

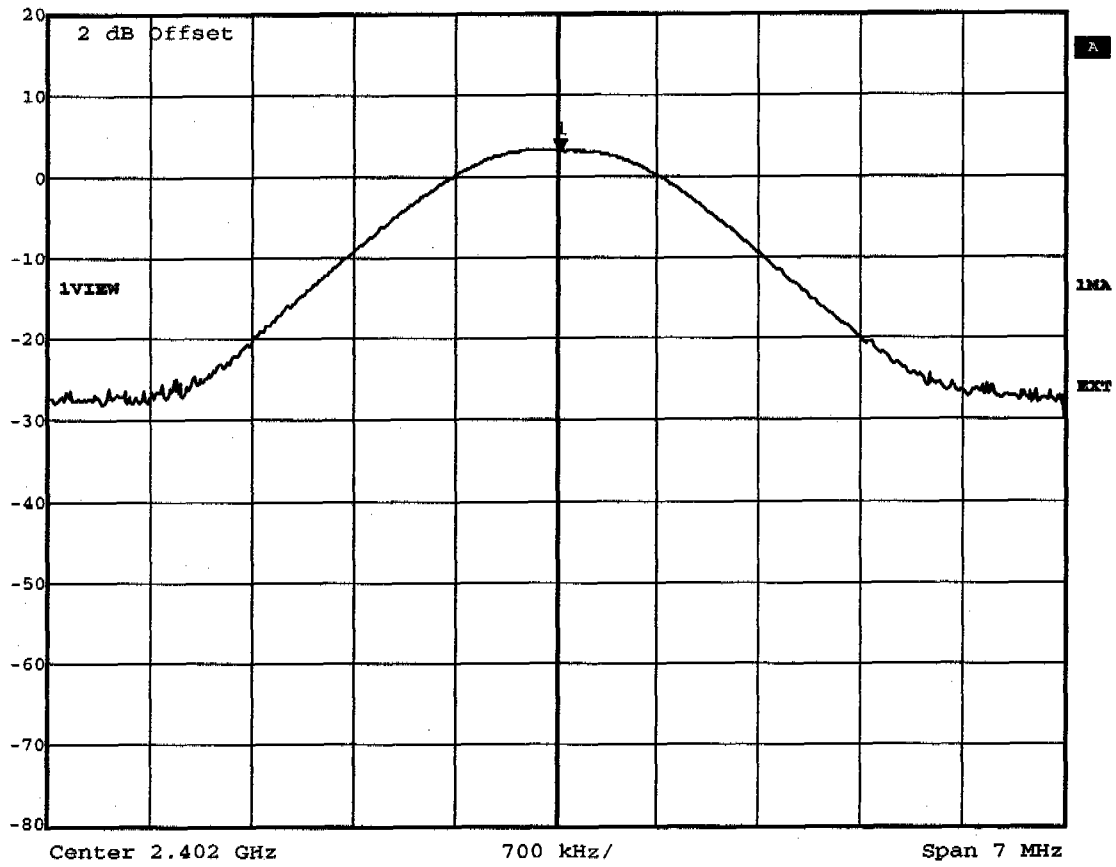


Appendix B

Peak Output Power



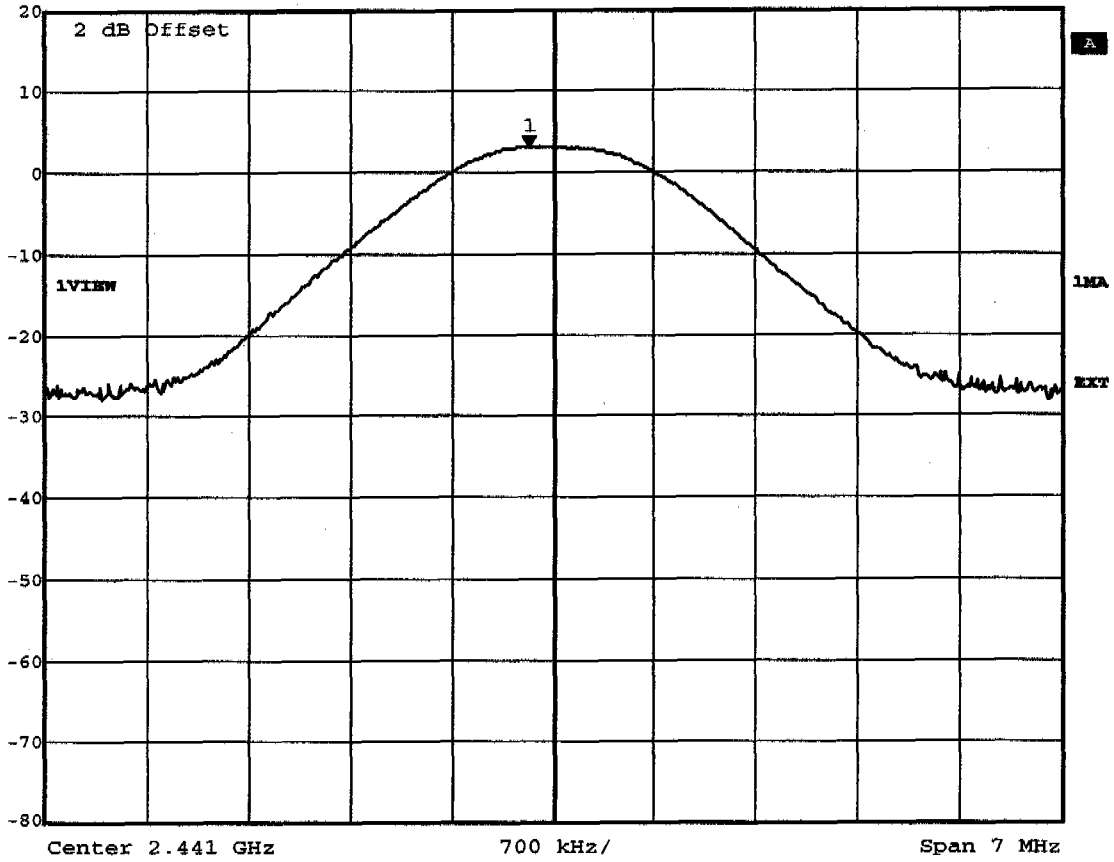
Marker 1 [T1] RBW 1 MHz RF Att 40 dB
Ref Lvl 3.18 dBm VBW 1 MHz
20 dBm 2.40203507 GHz SWT 5 ms Unit dBm



Title: Peak Output Power conducted Ch.: 0
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 07:50:24



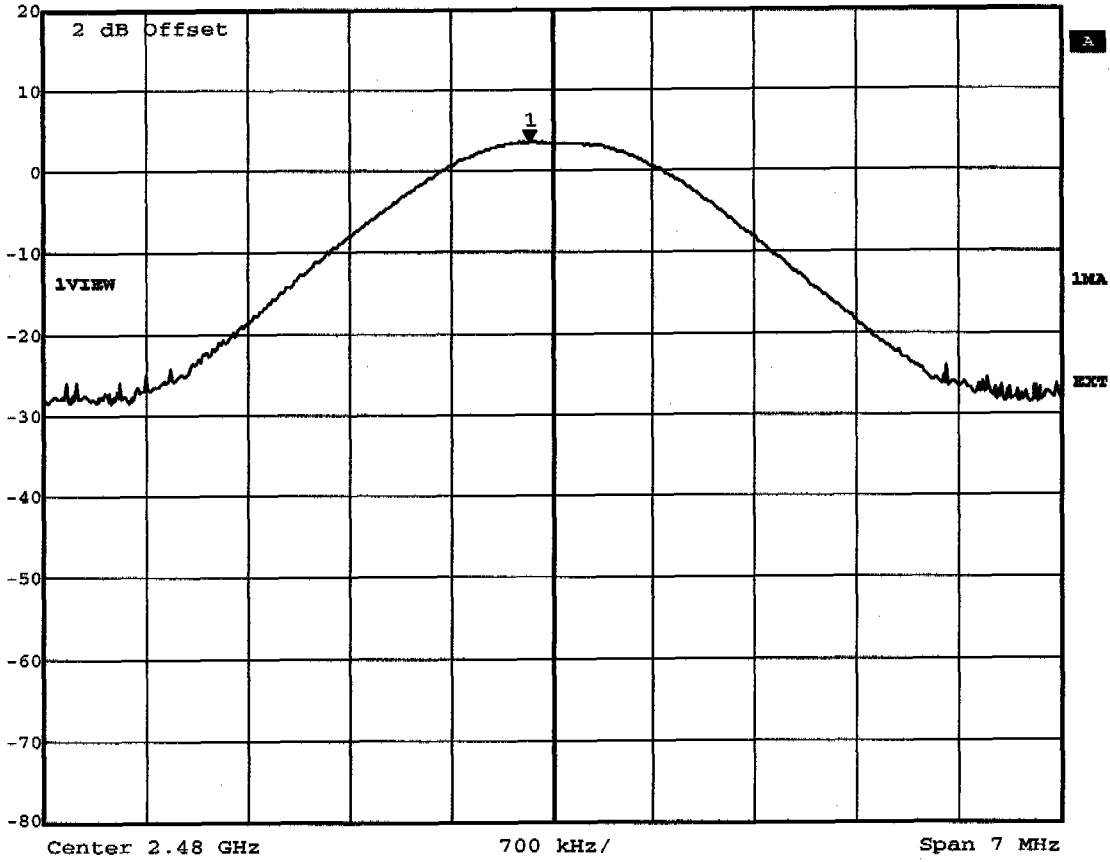
Ref Lvl	20 dBm	Marker 1 [T1]	2.93 dBm	RBW	1 MHz	RF Att	40 dB
			2.44083868 GHz	VBW	1 MHz		
				SWT	5 ms	Unit	dBm



Title: Peak Output Power conducted Ch.: 39
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 07:49:16



Marker 1 [T1] RBW 1 MHz RF Att 40 dB
Ref Lvl 3.30 dBm VBW 1 MHz
20 dBm 2.47985271 GHz SWT 5 ms Unit dBm

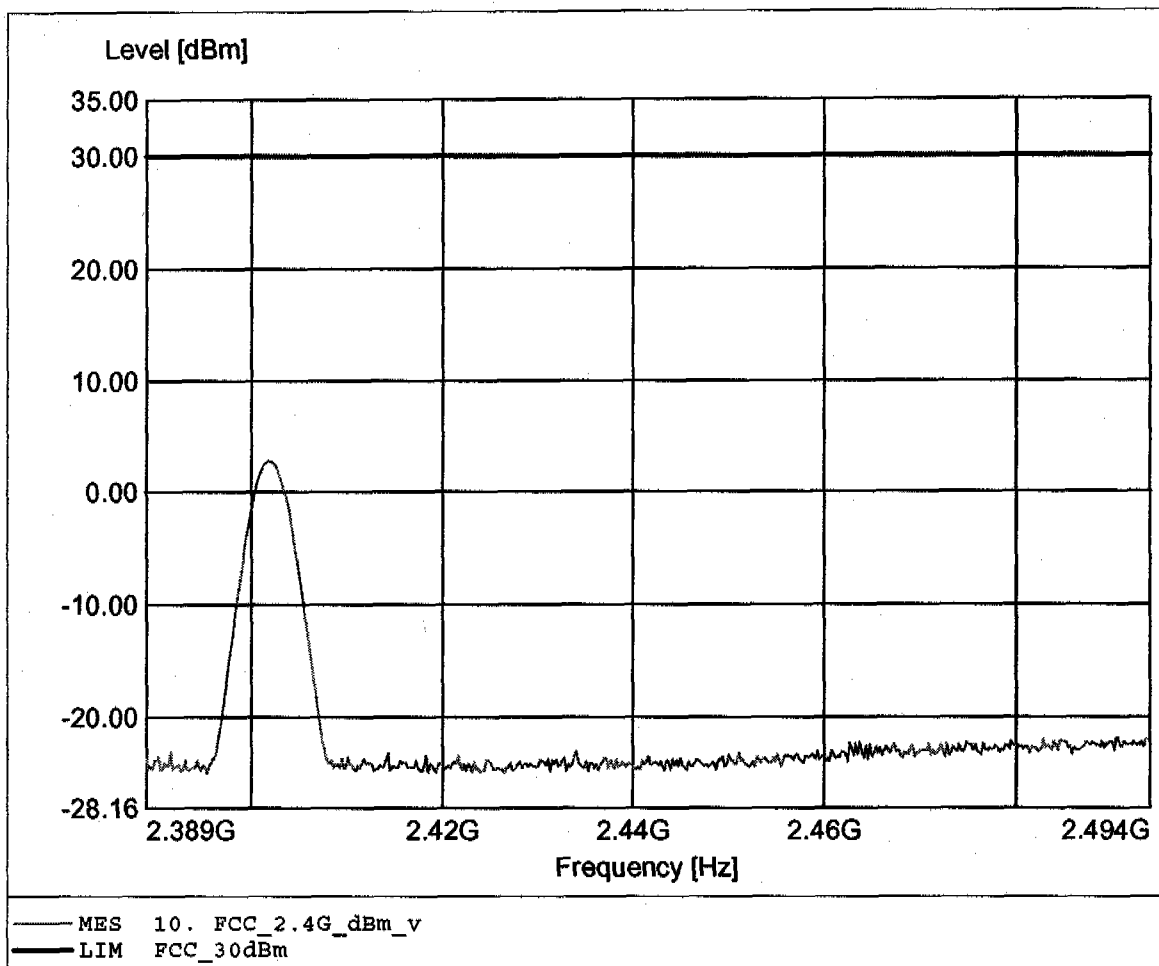


Title: Peak Output Power conducted Ch.: 78
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 07:52:19

Carrier power (dBm)

FCC RULES PART 15, SUBPART C

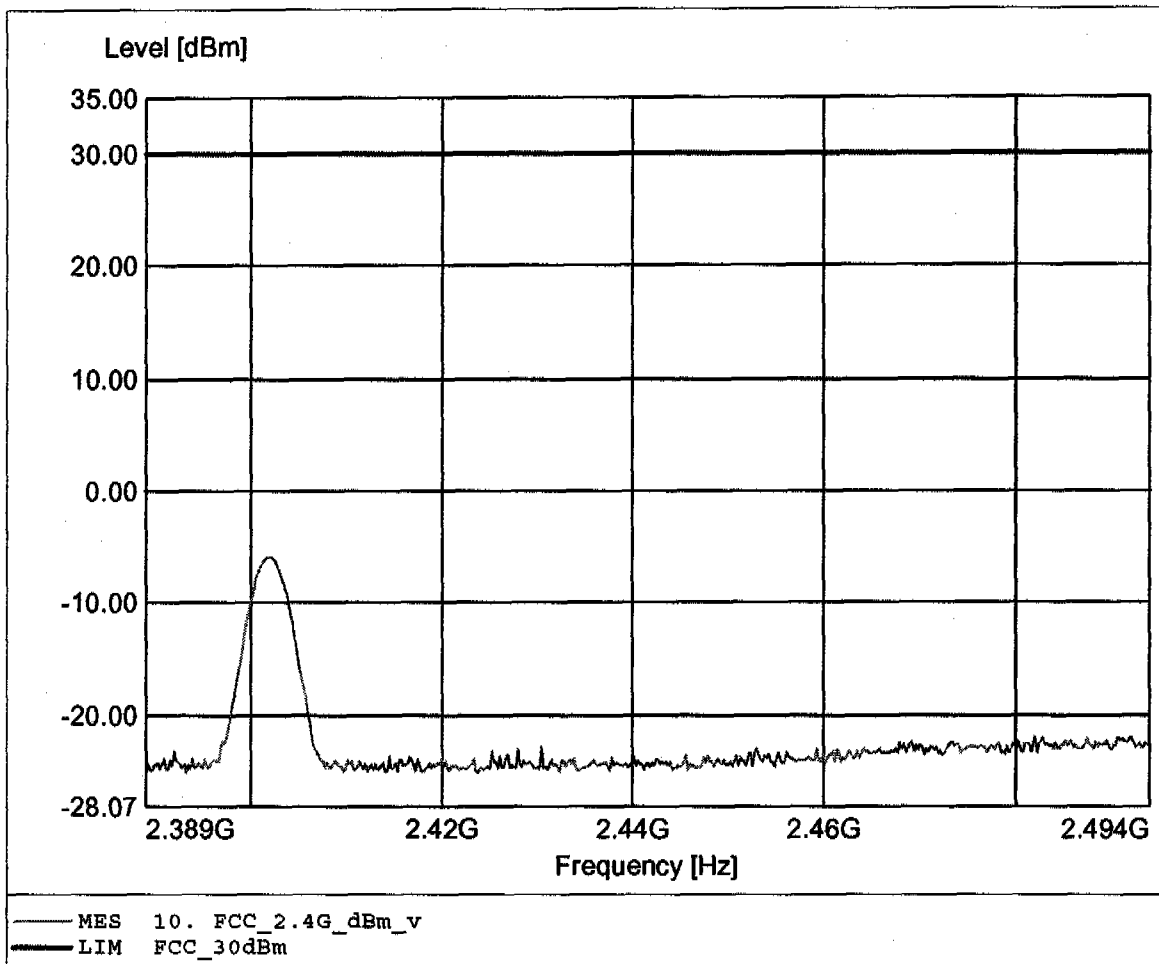
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: BBHA9120D
Comment 2: Freq: 2.402GHz, Pmax: 2.77dBm, RBW: 5MHz



Carrier power (dBm)

FCC RULES PART 15, SUBPART C

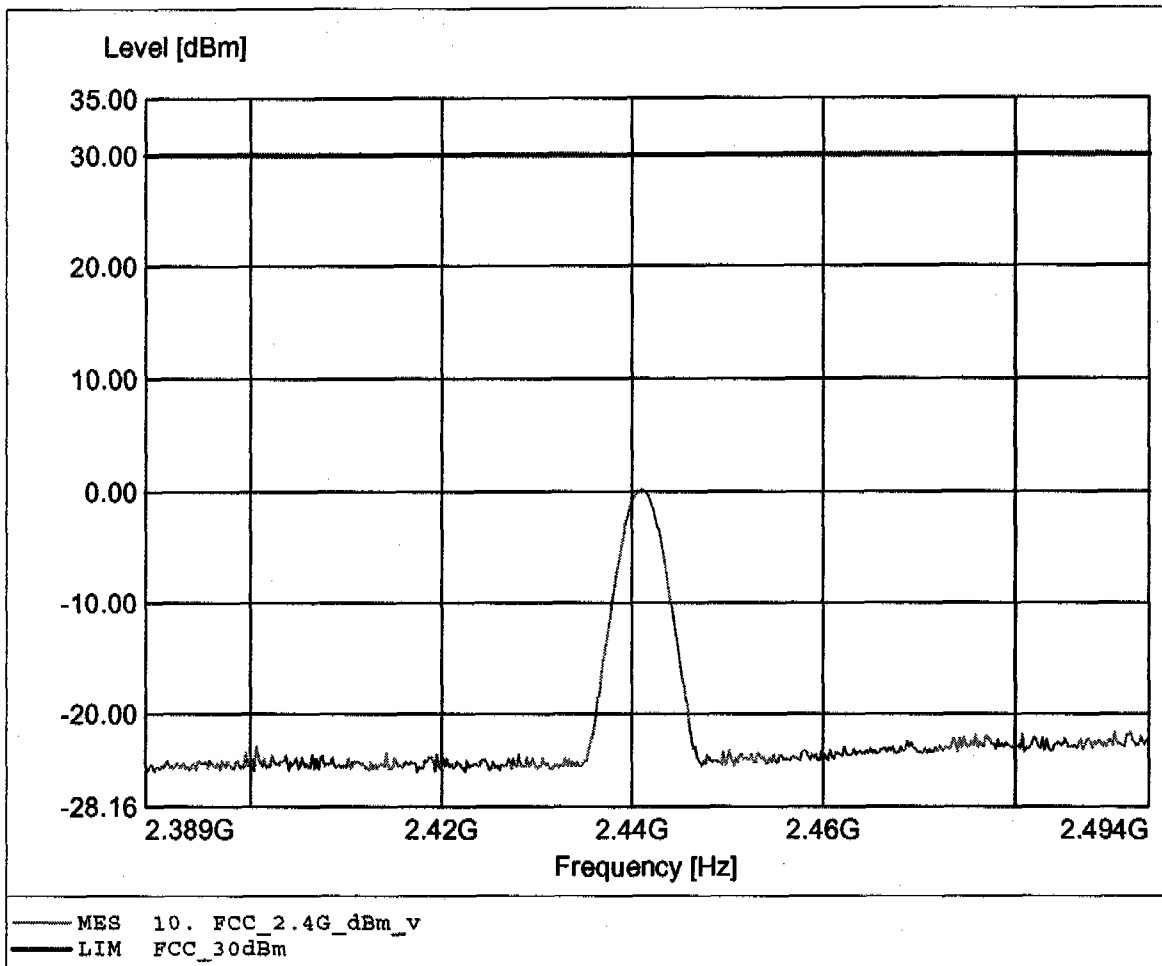
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: BBHA9120D
Comment 2: Freq: 2.402GHz, Pmax: -5.96dBm, RBW: 5MHz



Carrier power (dBm)

FCC RULES PART 15, SUBPART C

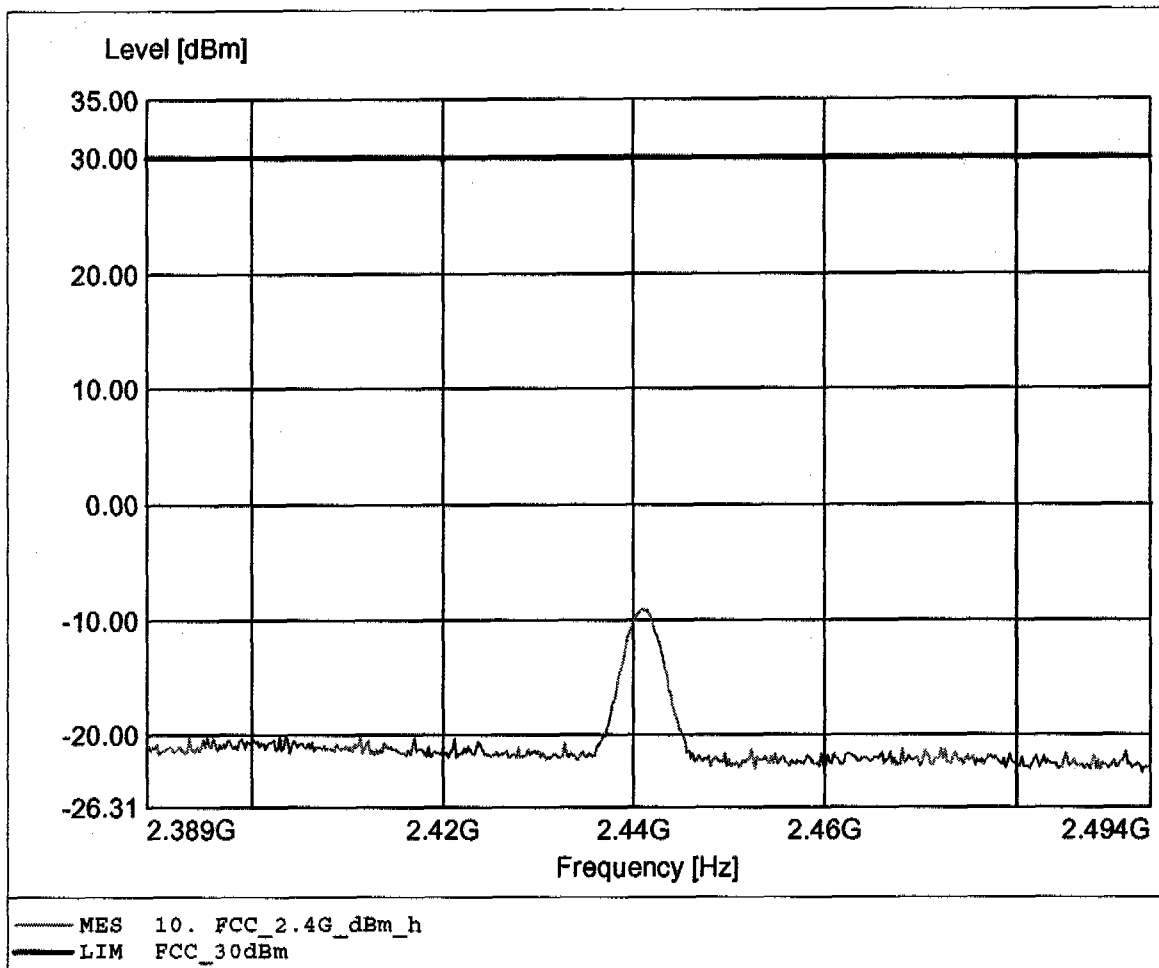
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: BBHA9120D
Comment 2: Freq: 2.441GHz, Pmax: 0.15dBm, RBW: 5MHz



Carrier power (dBm)

FCC RULES PART 15, SUBPART C

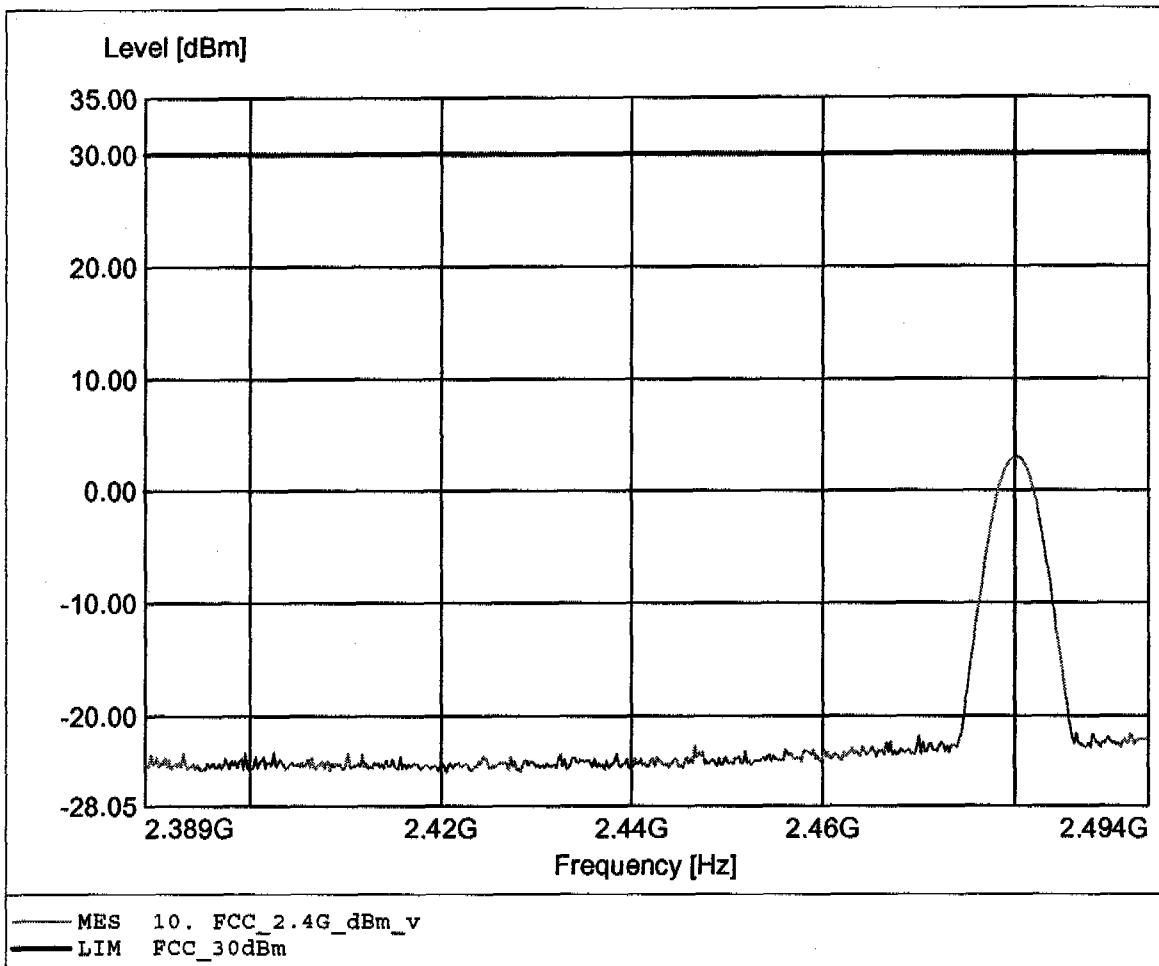
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: BBHA9120D
Comment 2: Freq: 2.441GHz, Pmax: -9.00dBm, RBW: 5MHz



Carrier power (dBm)

FCC RULES PART 15, SUBPART C

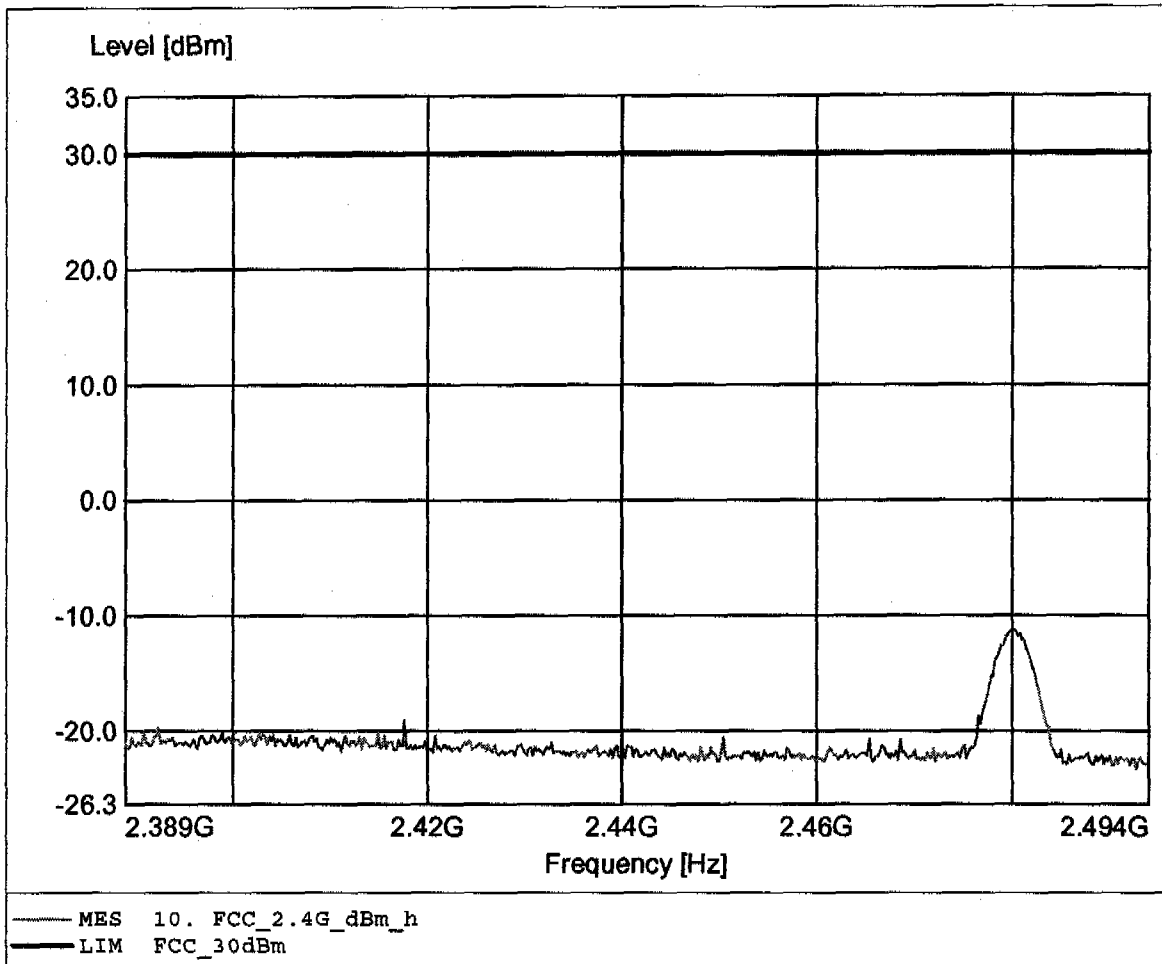
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: BBHA9120D
Comment 2: Freq: 2.480GHz, Pmax: 2.94dBm, RBW: 5MHz



Carrier power (dBm)

FCC RULES PART 15, SUBPART C

Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: BBHA9120D
Comment 2: Freq: 2.480GHz, Pmax: -11.21dBm, RBW: 5MHz





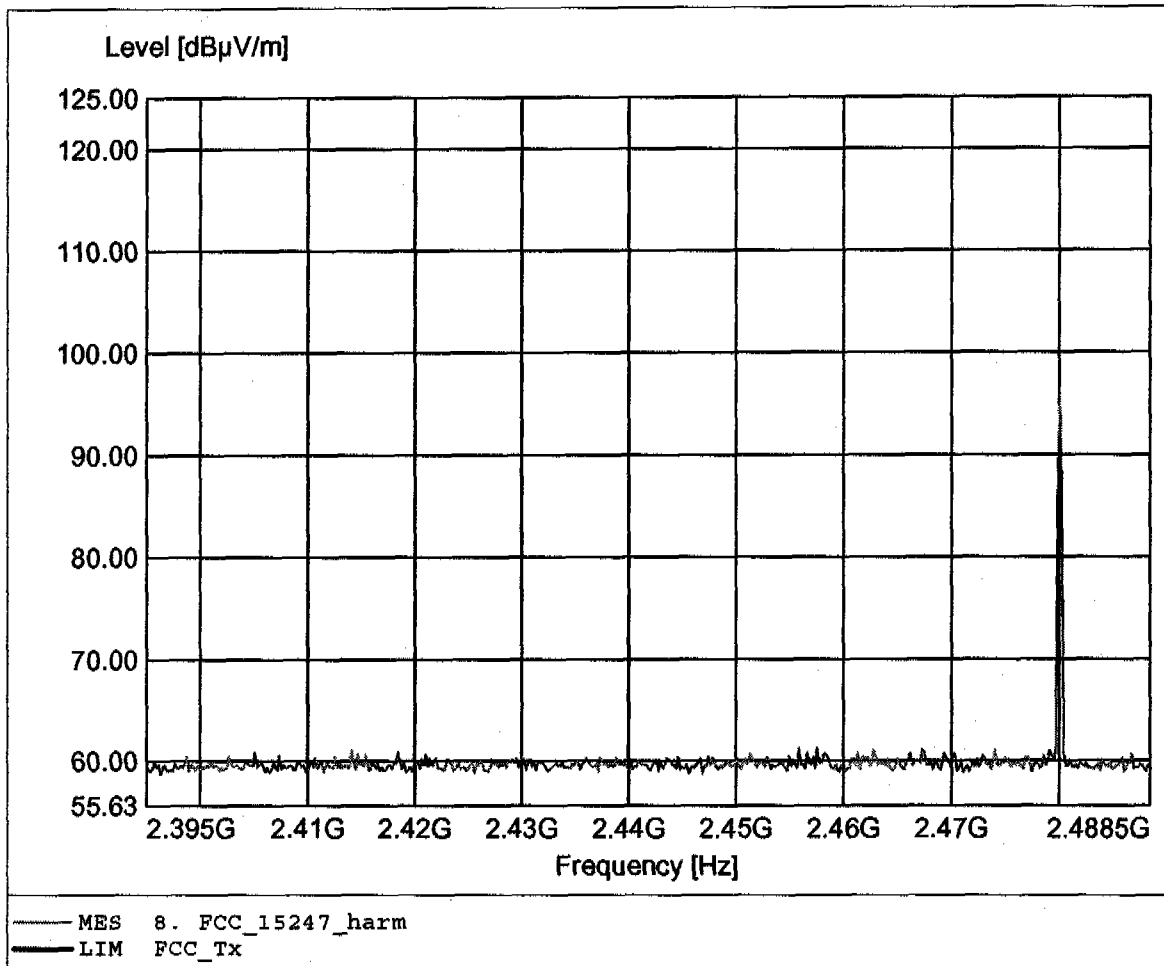
Appendix C

Spurious Emissions radiated - Transmitter operating

Carrier power (Field Strength)

FCC RULES PART 15, SUBPART C

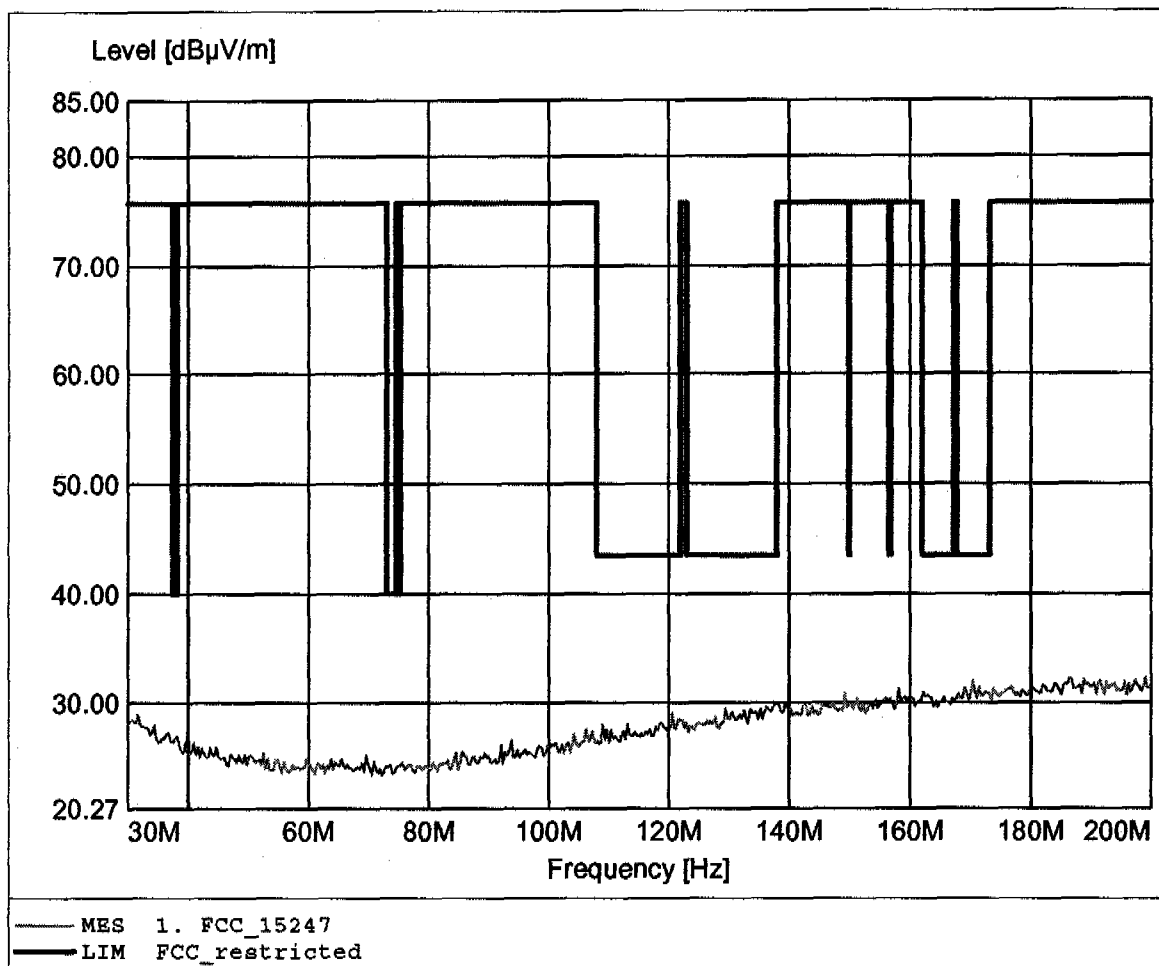
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: BBHA9120D
Comment 2: Freq: 2.480GHz, Emax: 95.78dBµV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

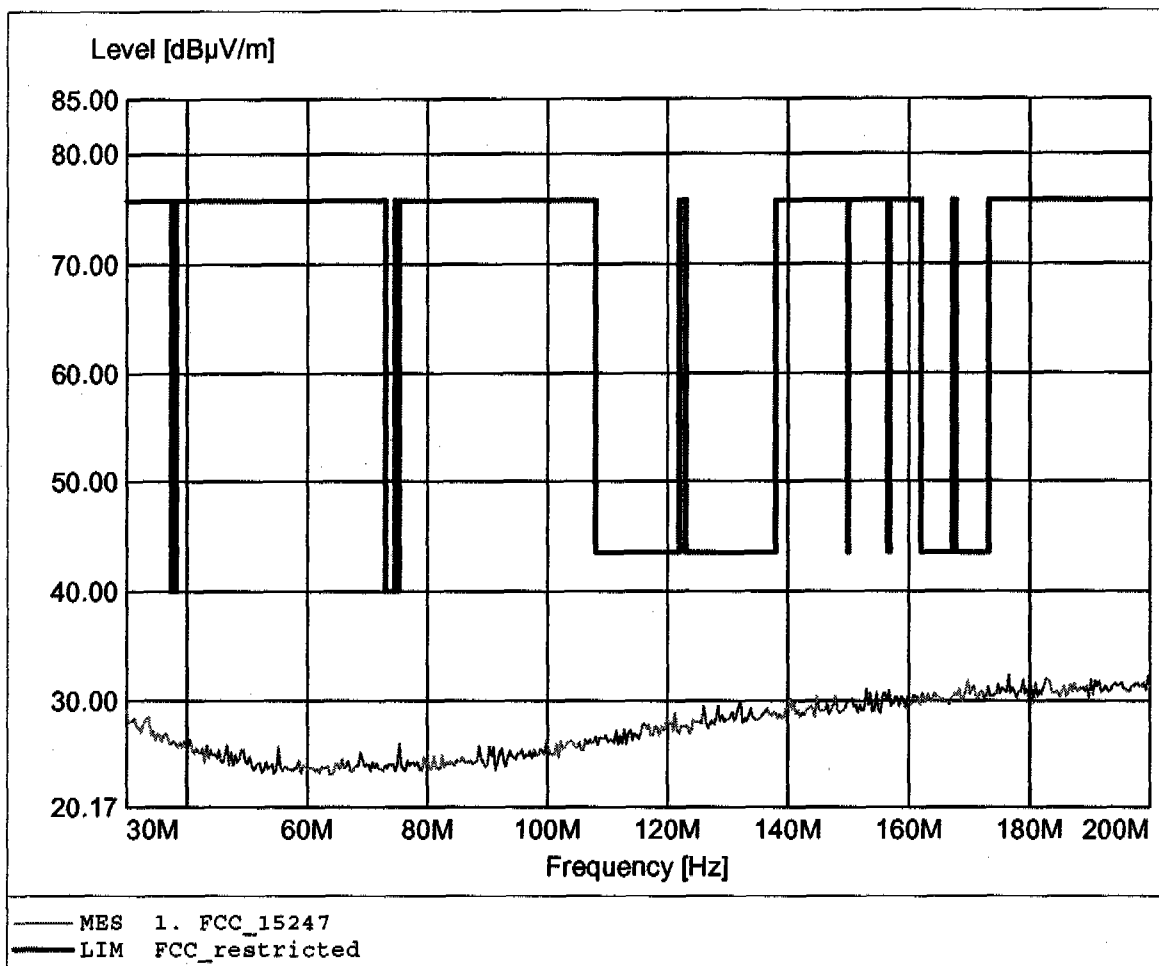
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HK 116
Comment 2: Freq: 198.978MHz, Emax: 32.29dBµV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

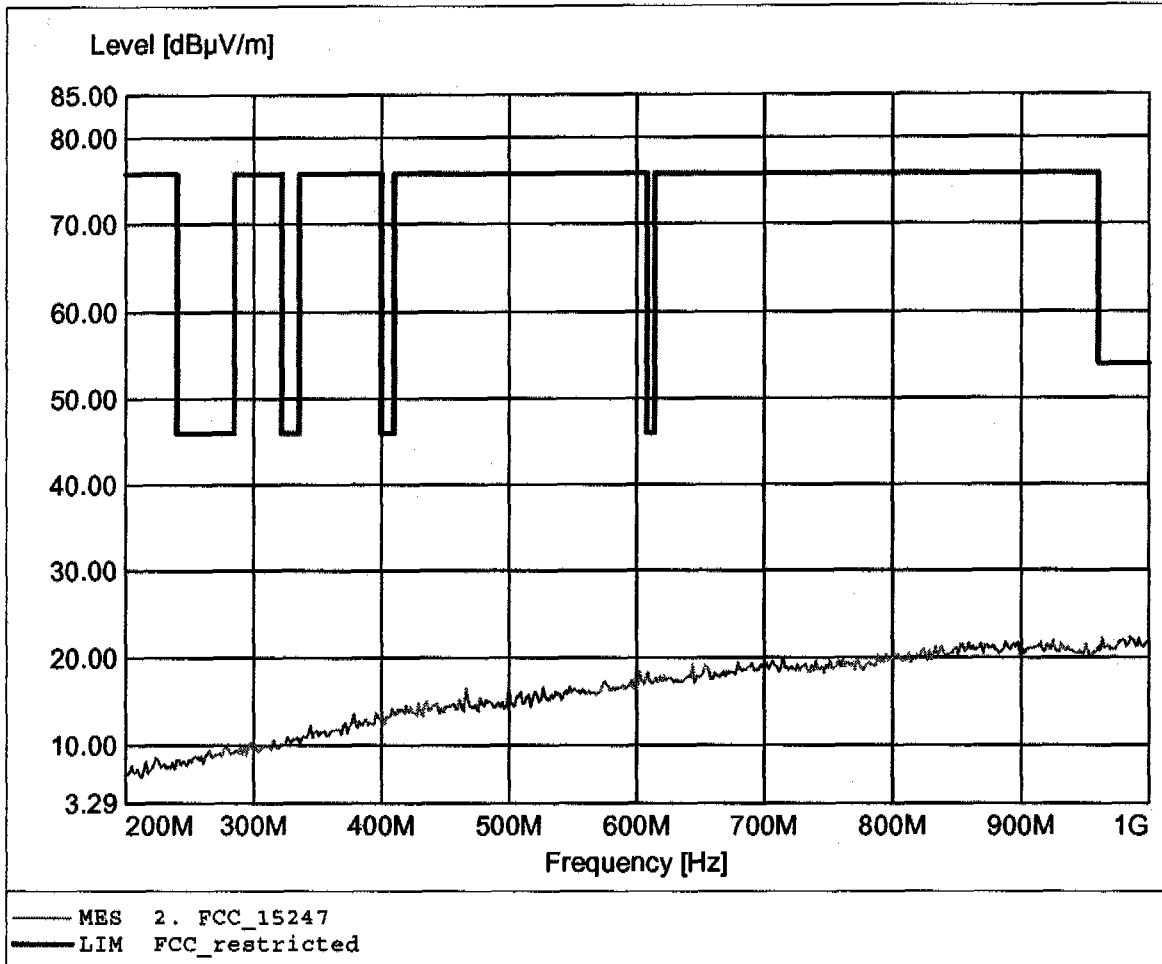
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HK 116
Comment 2: Freq: 176.493MHz, Emax: 32.37dBuV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

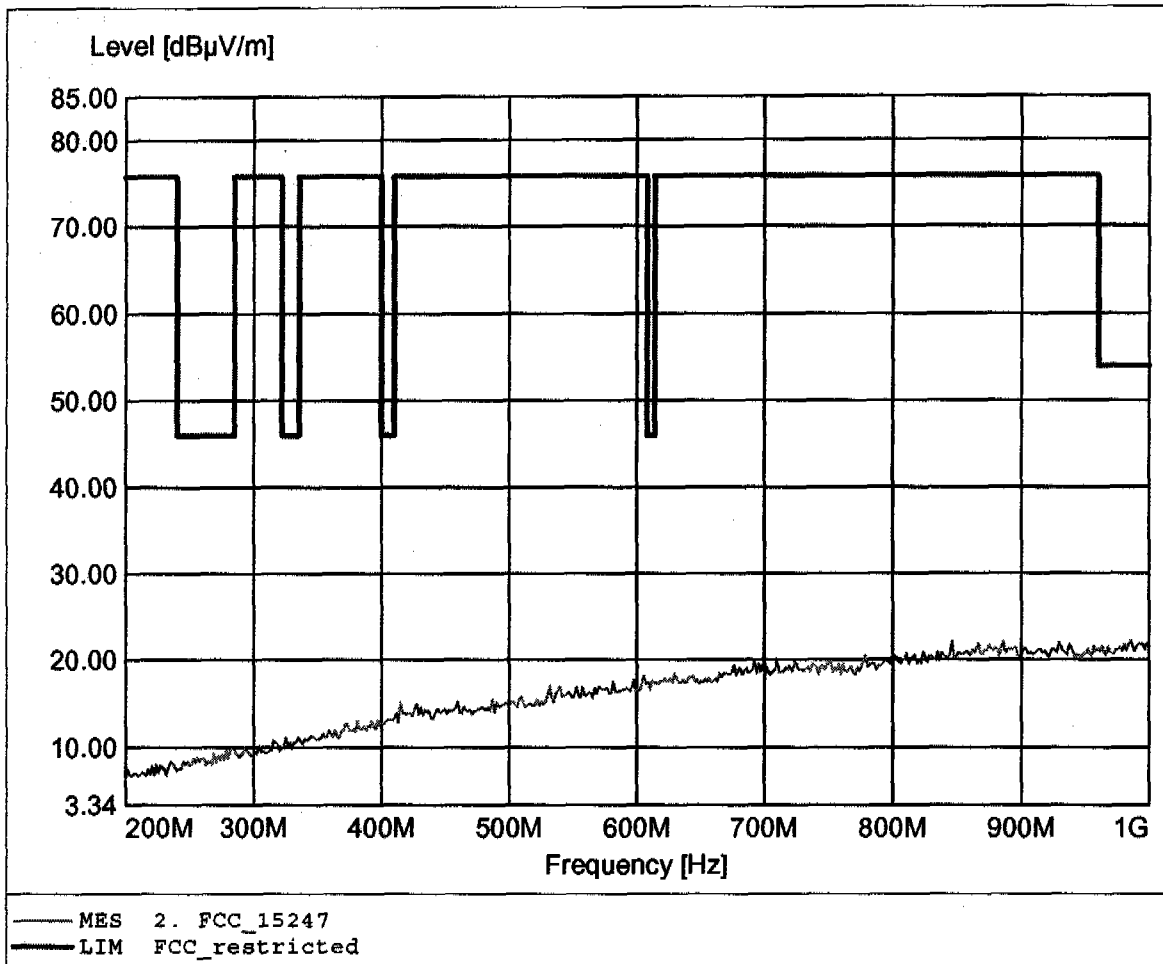
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HL 223, amplif.
Comment 2: Freq: 985.571MHz, Emax: 22.36dBµV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

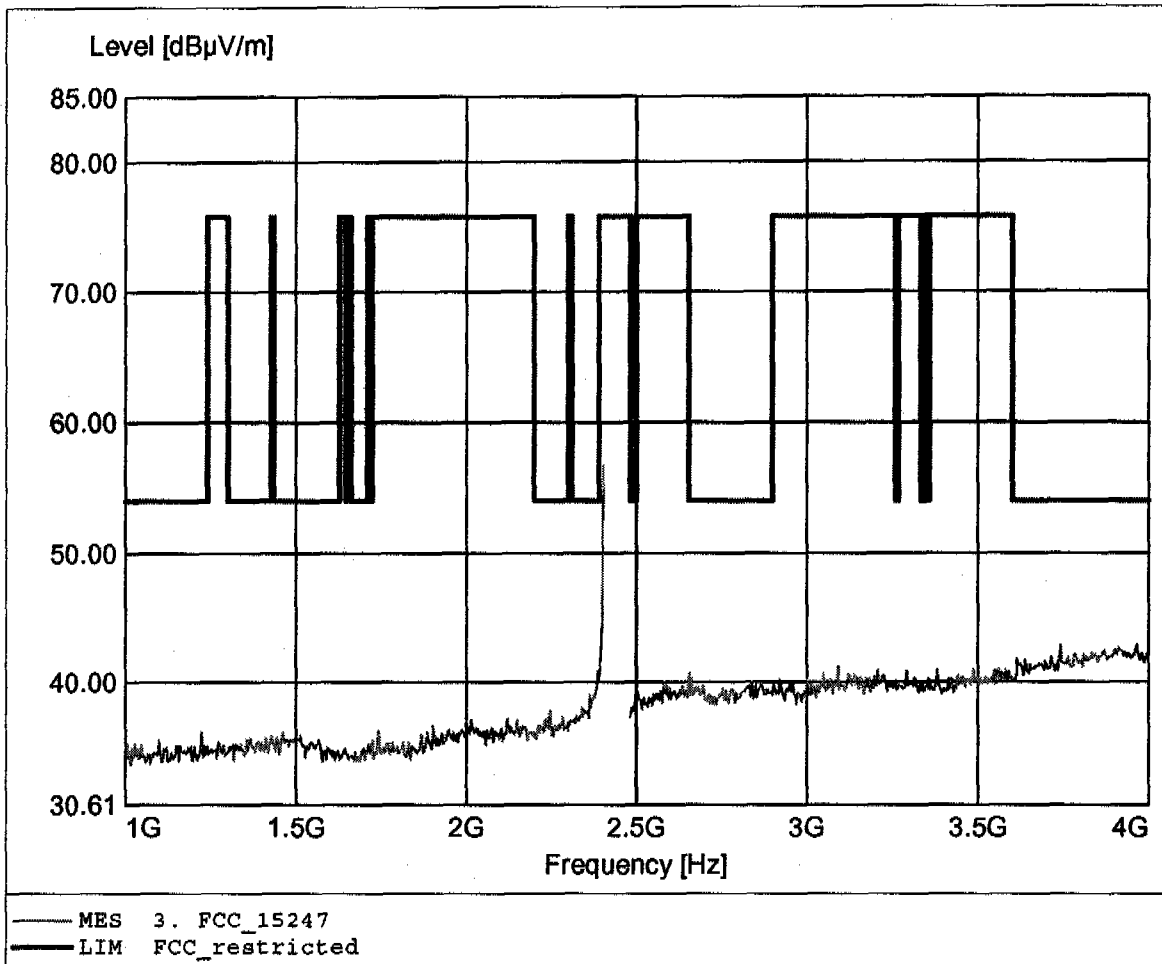
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cerovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HL 223, amplif.
Comment 2: Freq: 985.571MHz, Emax: 22.17dBuV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

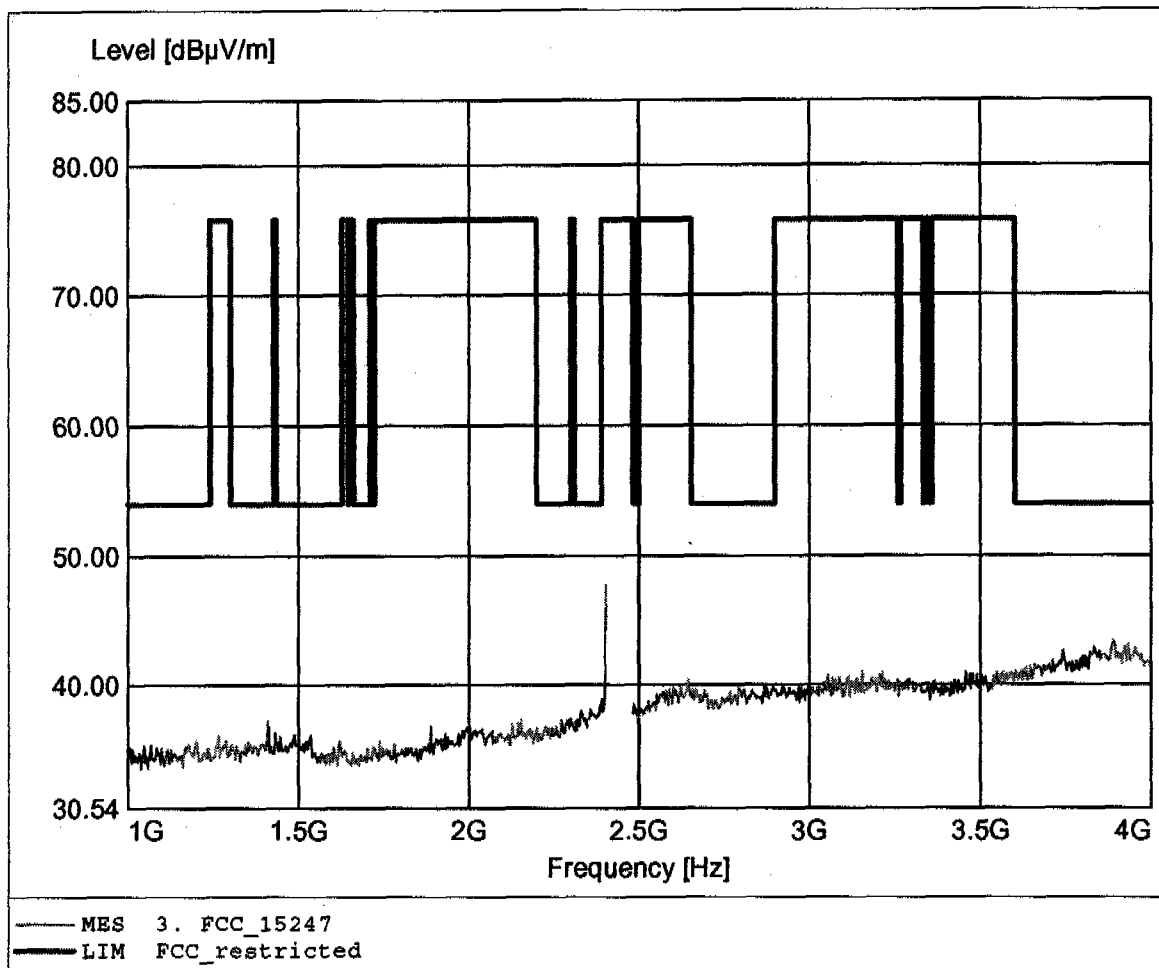
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, amplif.
Comment 2: Freq: 2.403GHz, Emax: 56.72dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

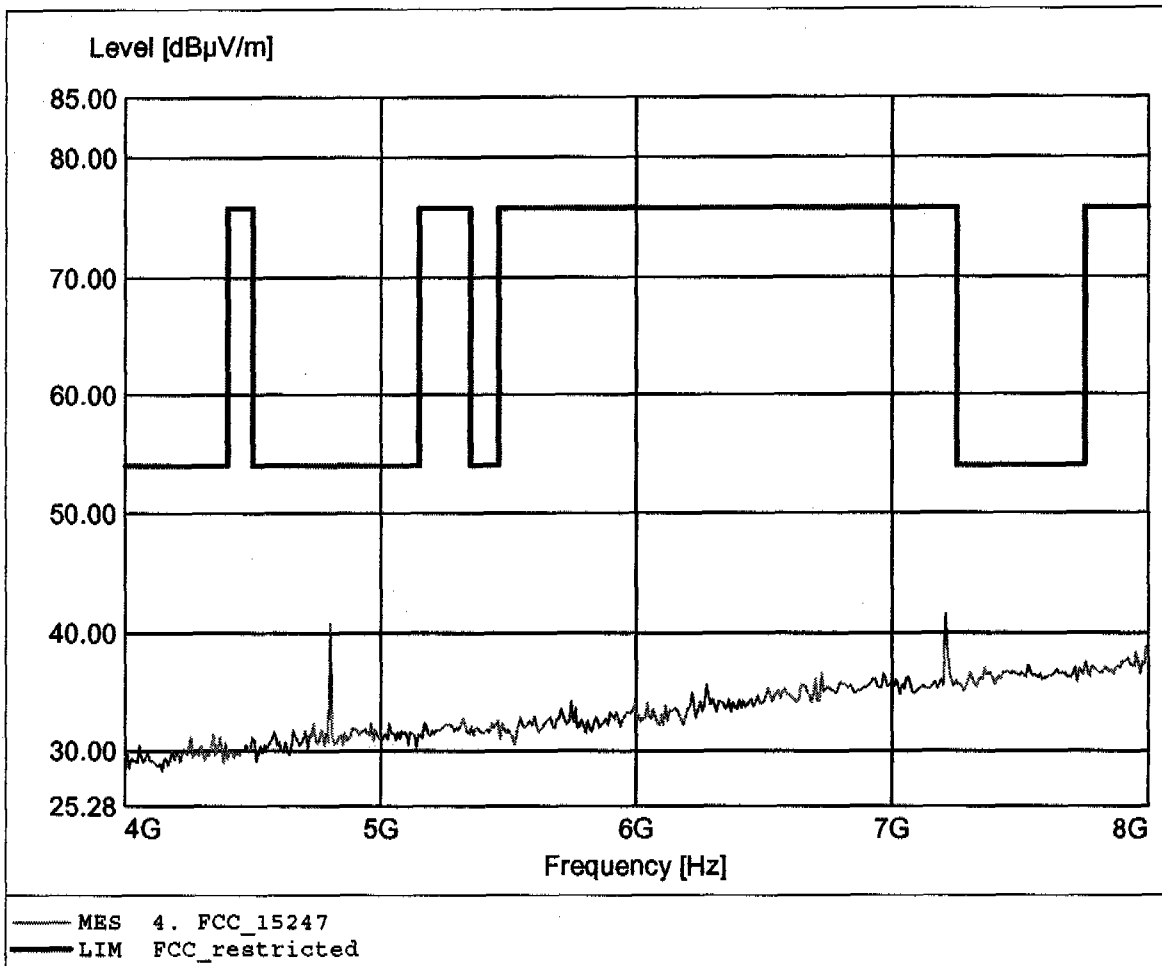
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cerovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, amplif.
Comment 2: Freq: 2.403GHz, Emax: 47.71dBµV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

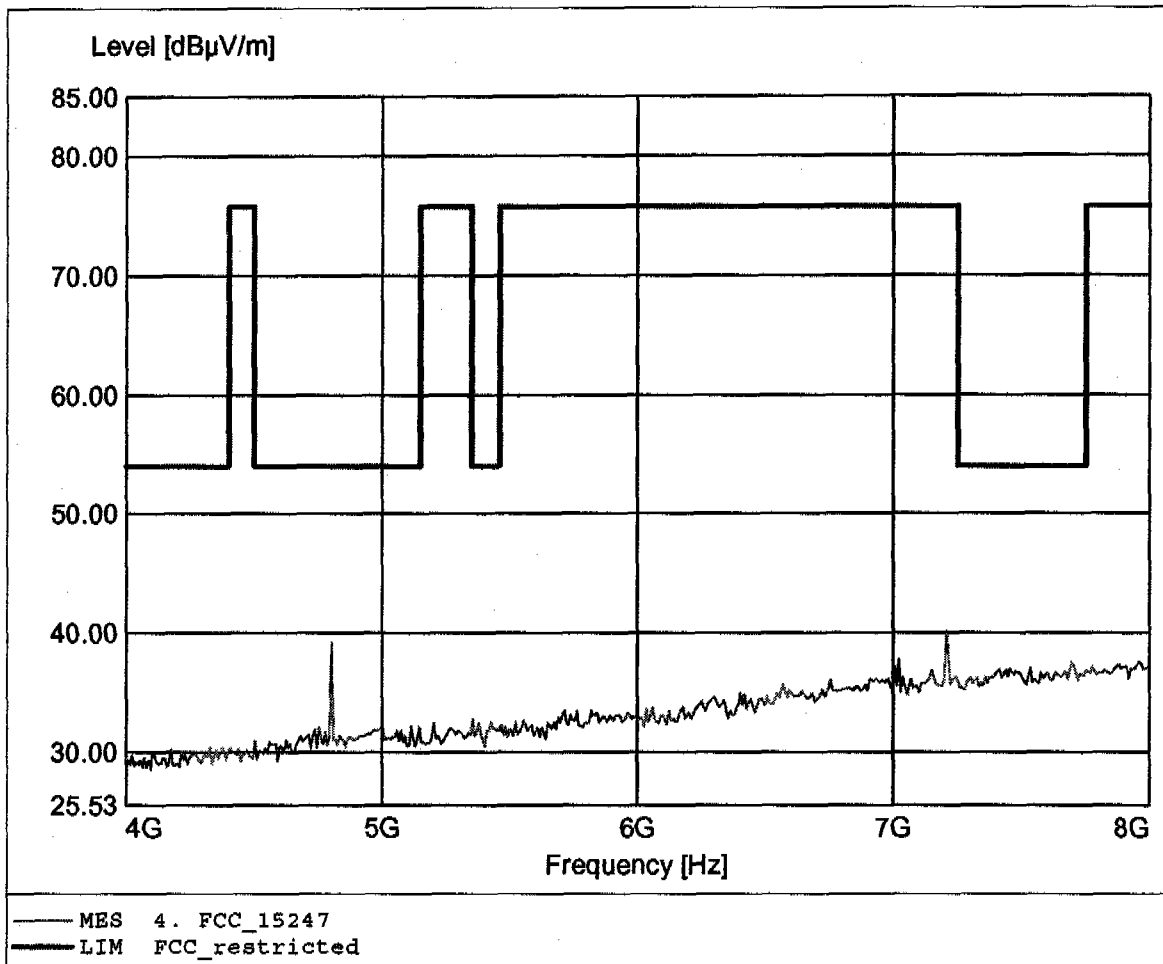
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 7.206GHz, Emax: 41.61dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

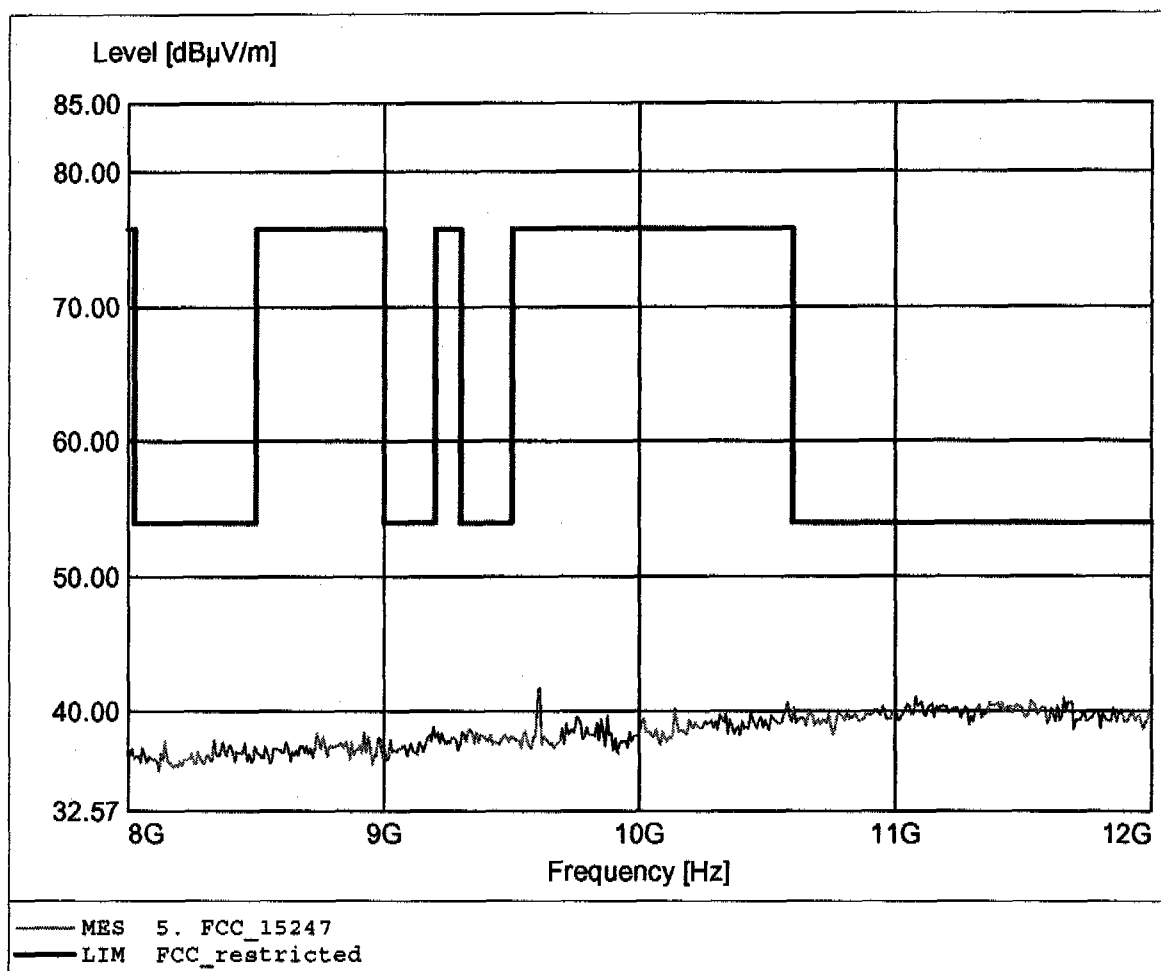
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 7.206GHz, Emax: 40.16dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

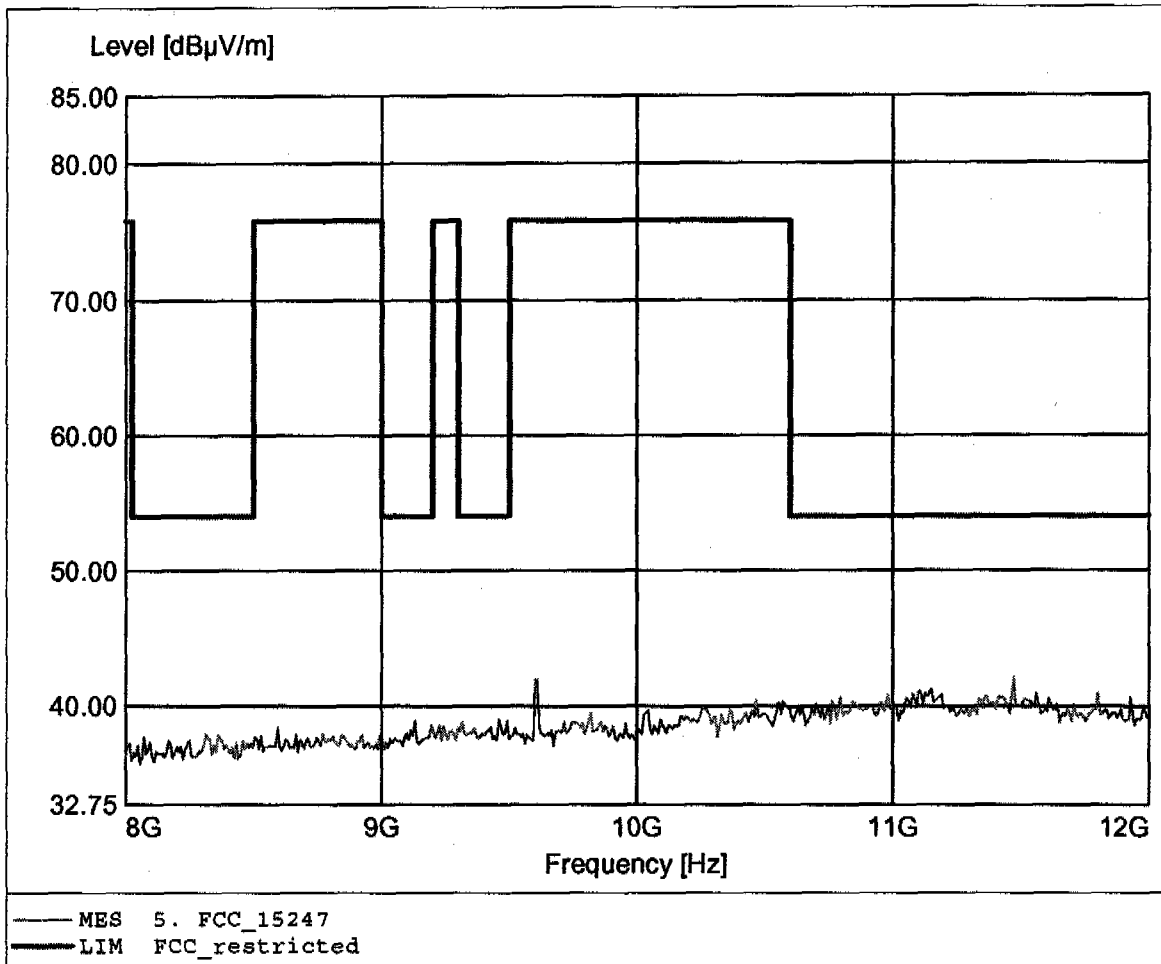
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 9.611GHz, Emax: 41.75dBµV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

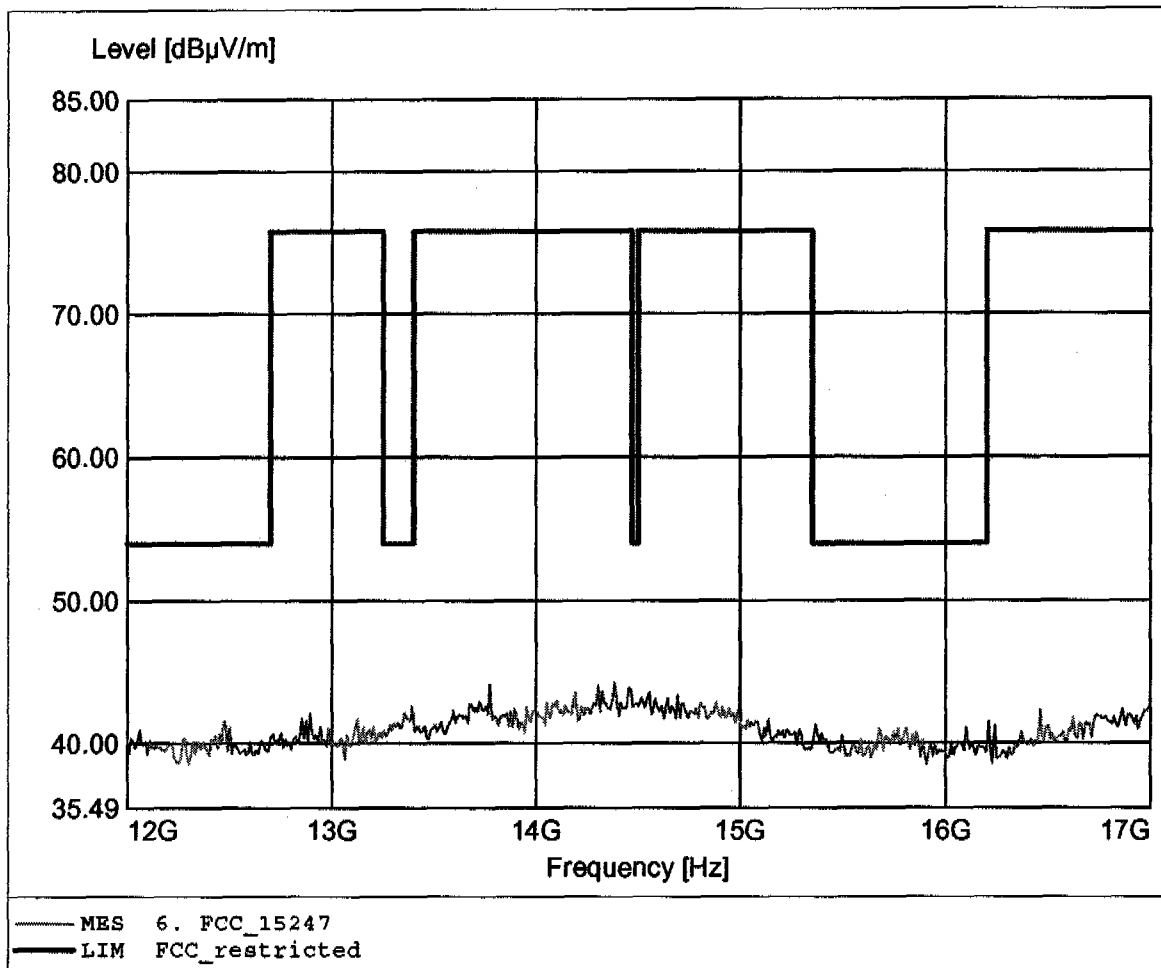
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150D BE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 11.471GHz, Emax: 42.11dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

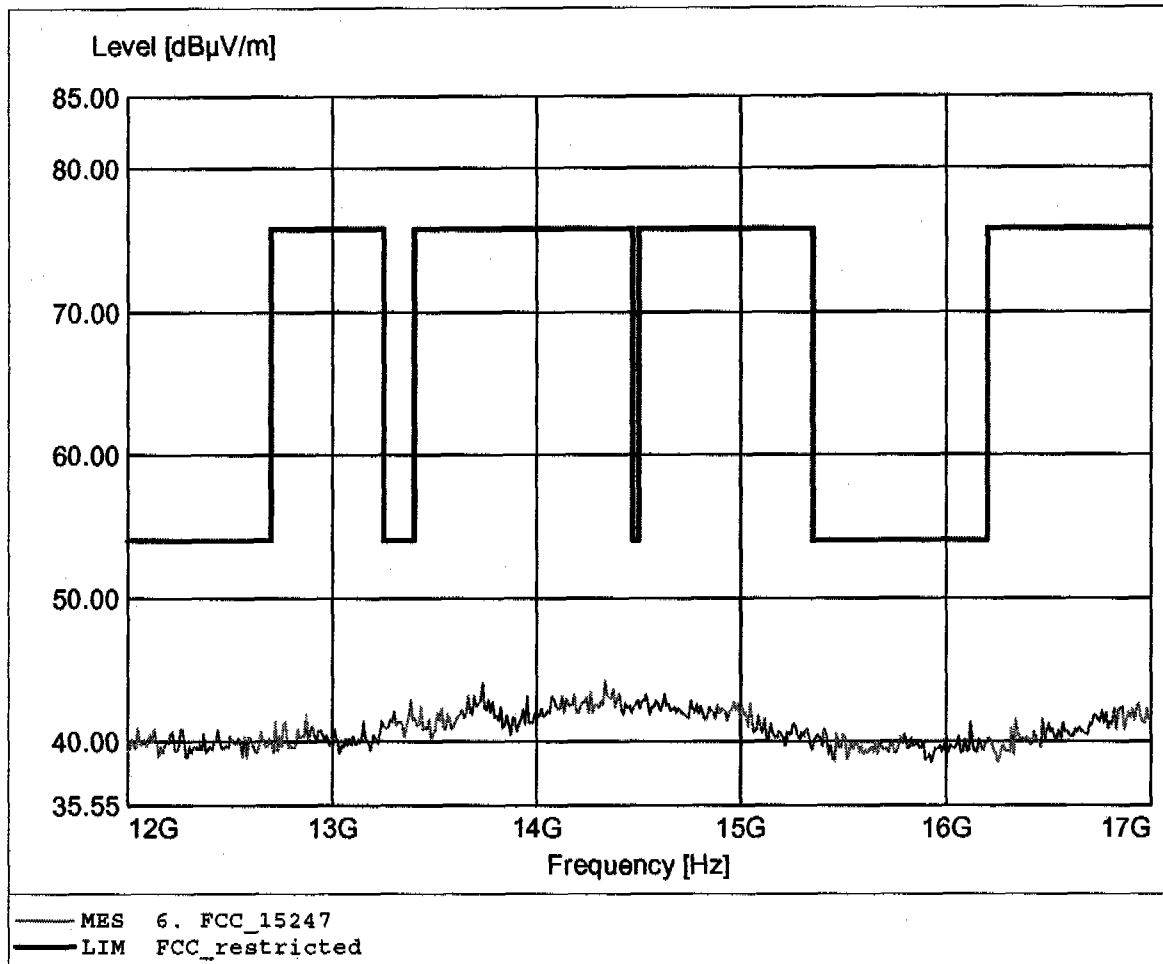
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 14.385GHz, Emax: 44.23dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

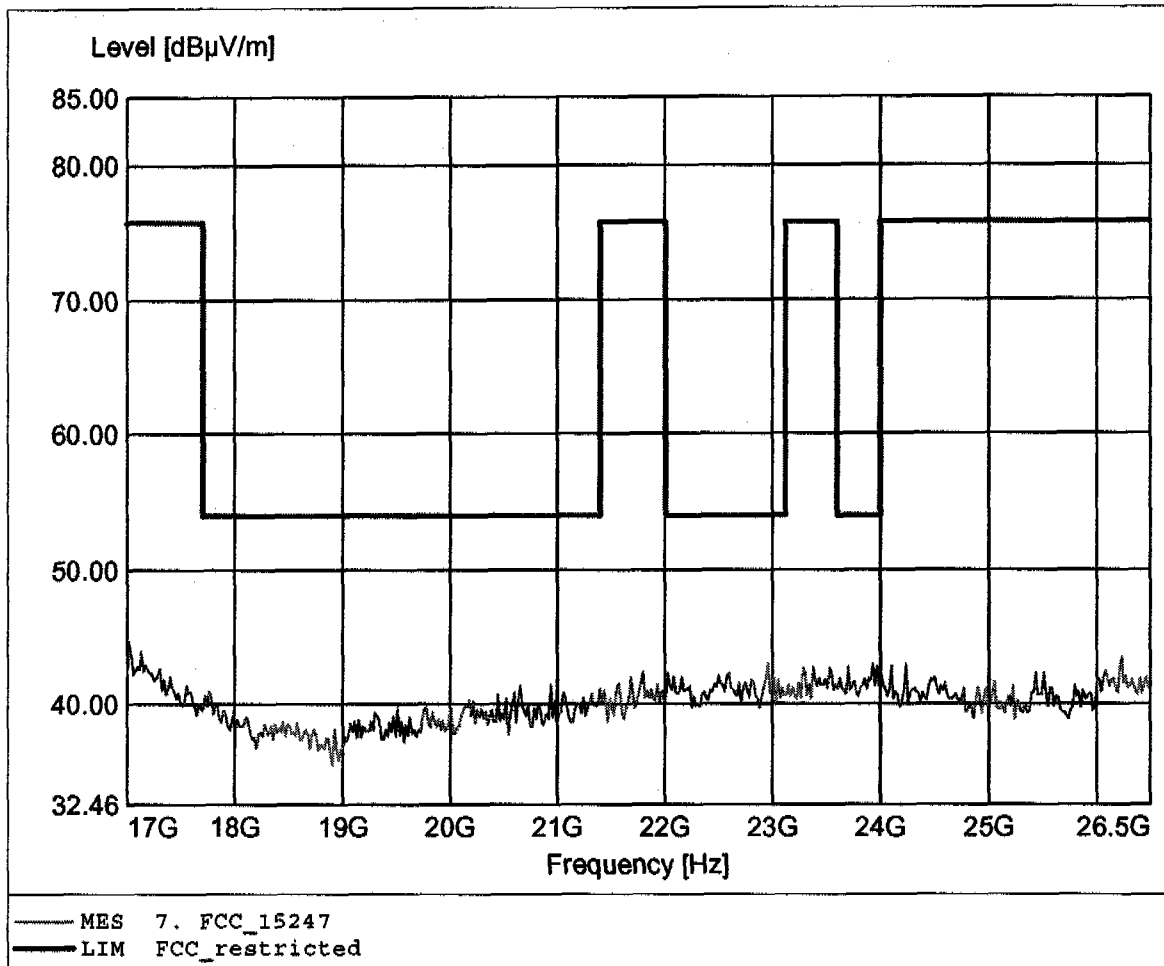
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 14.335GHz, Emax: 44.26dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

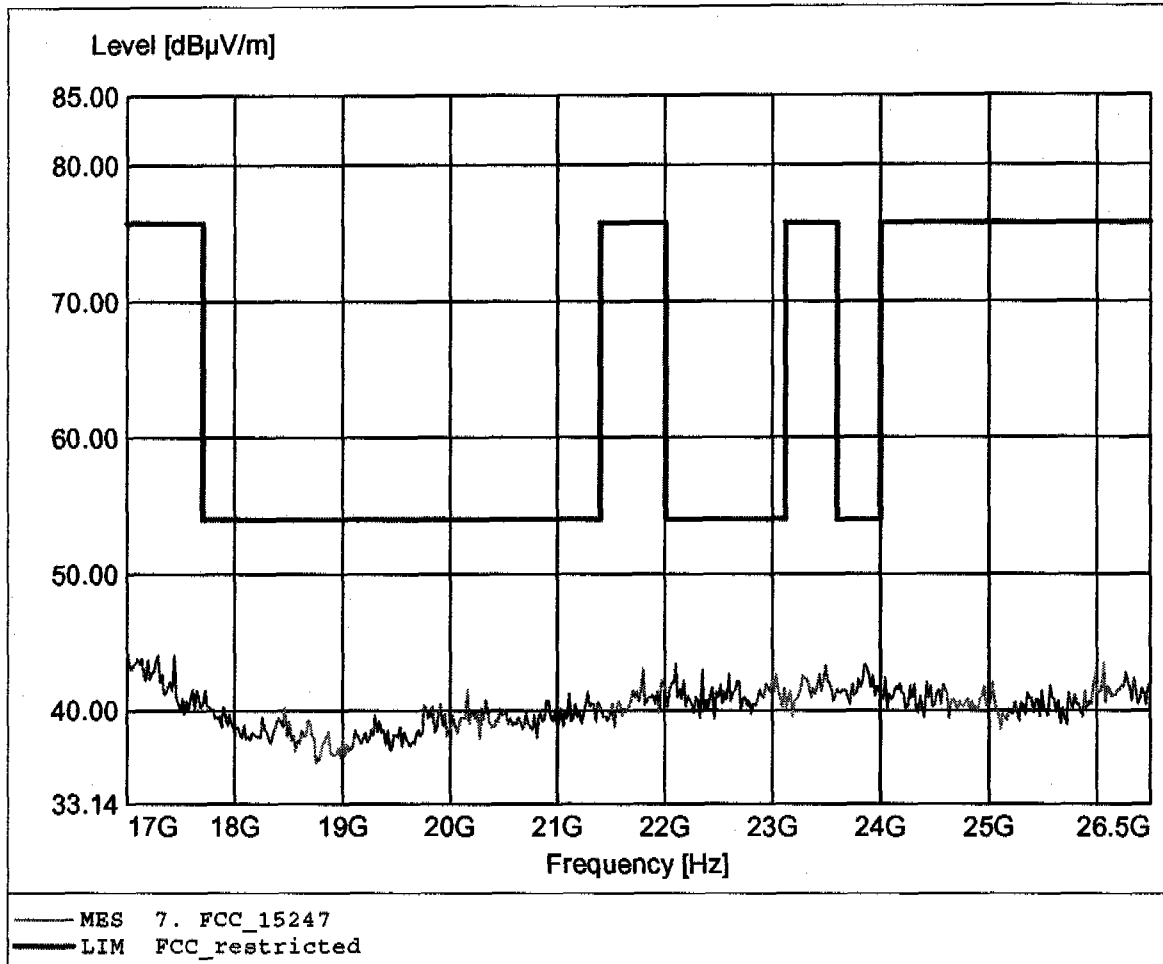
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: HL025, amplif.
Comment 2: Freq: 17.019GHZ, Emax: 44.74dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

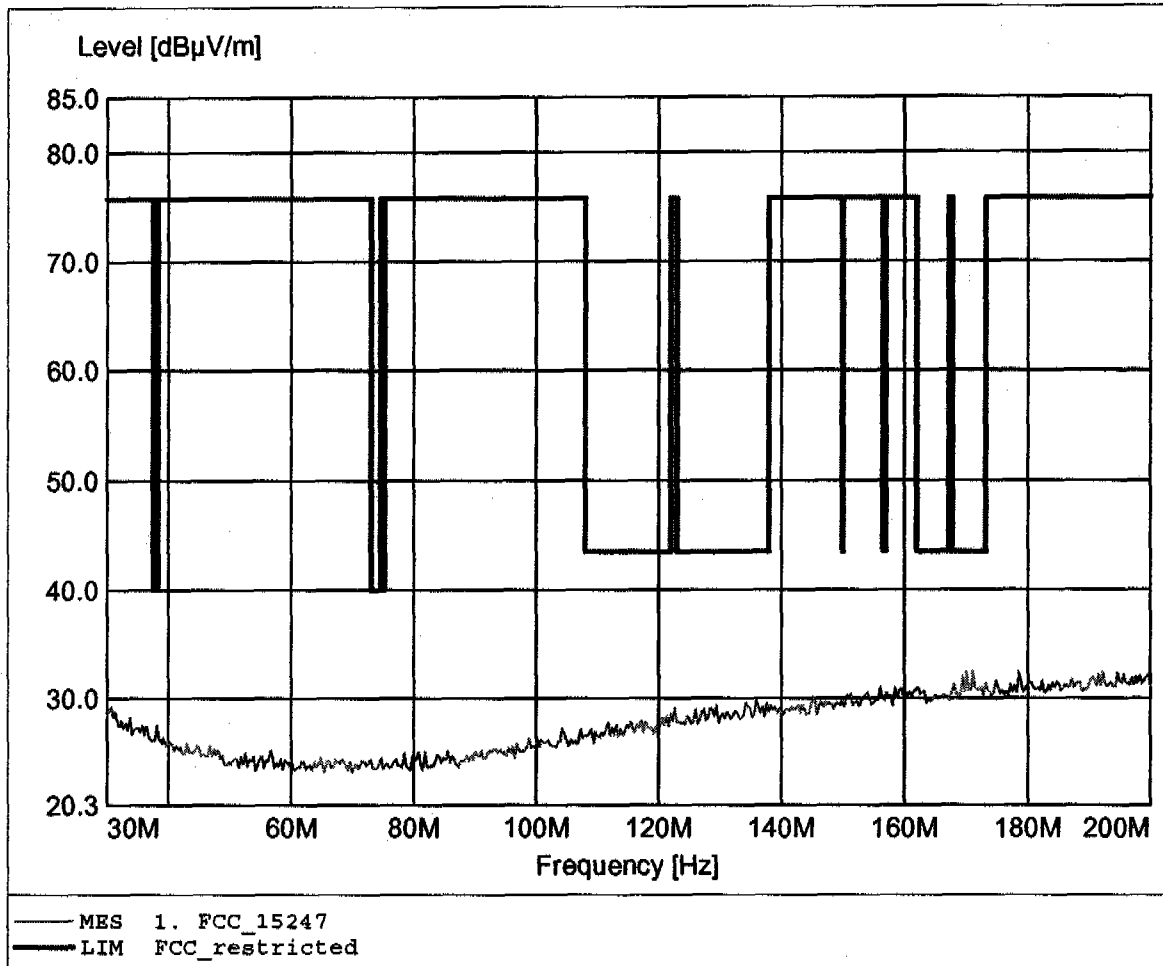
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2402 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: HL025, amplif.
Comment 2: Freq: 17.000GHz, Emax: 44.39dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

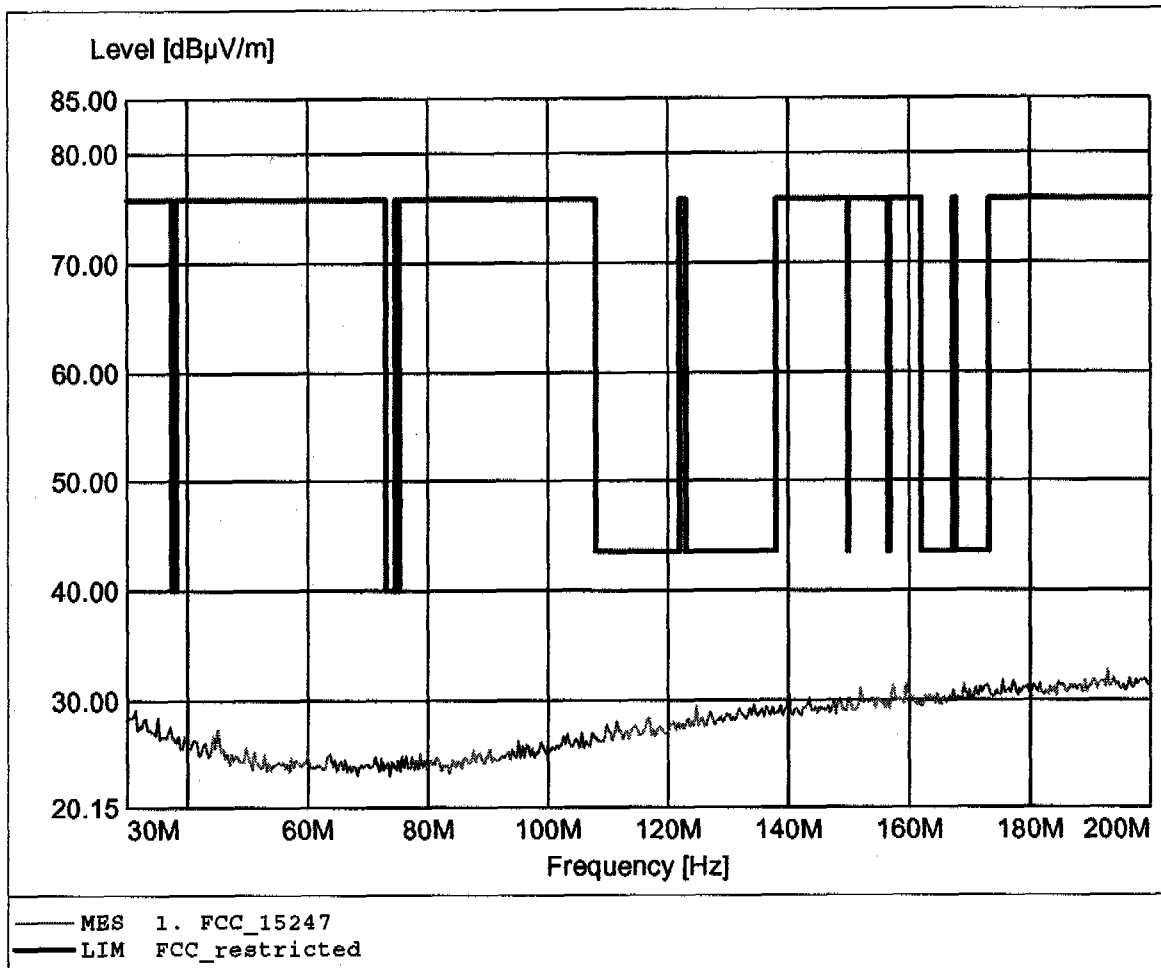
Approval Holder: GN Netcom A/S
EUT: Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HK 116
Comment 2: Freq: 171.042MHz, Emax: 32.49dBµV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

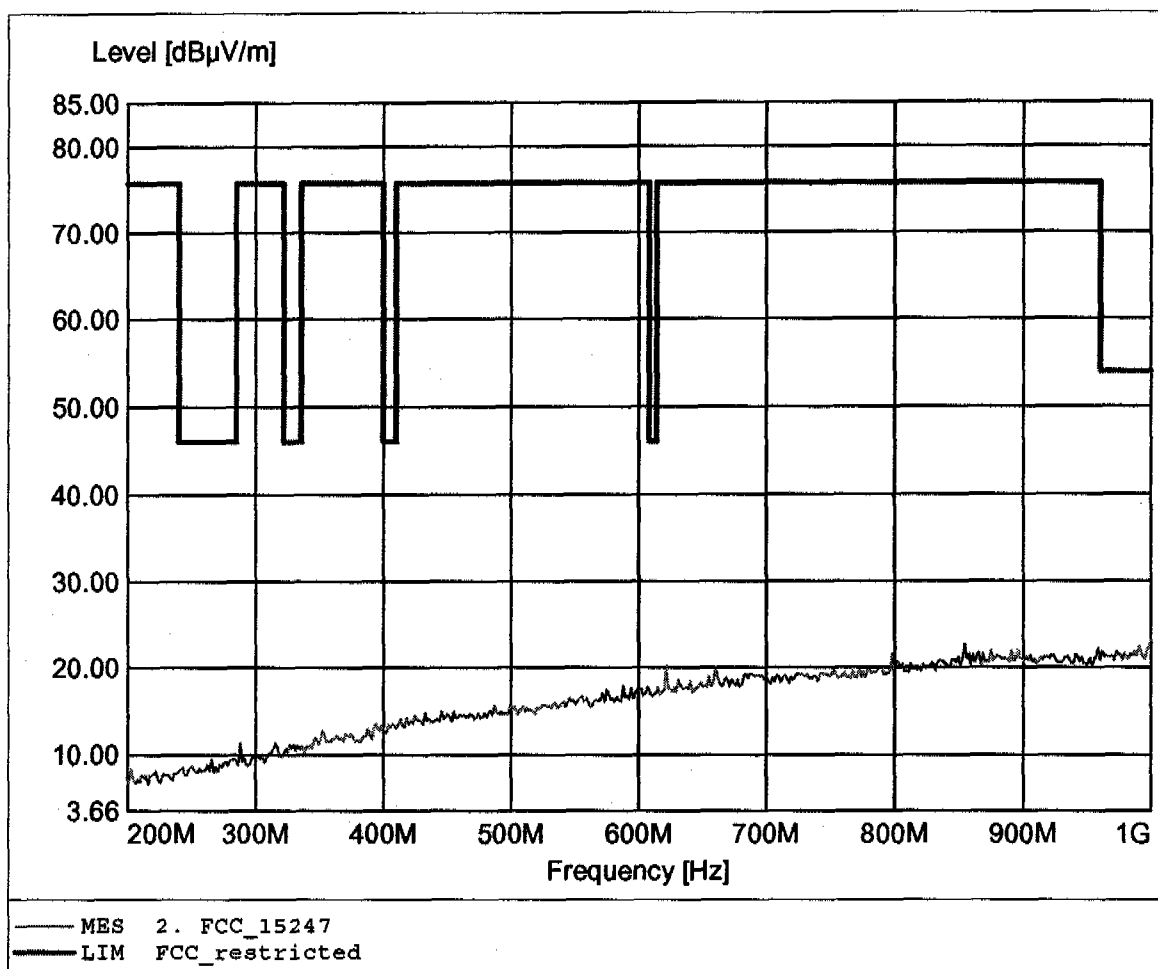
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HK 116
Comment 2: Freq: 192.846MHz, Emax: 32.68dBµV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

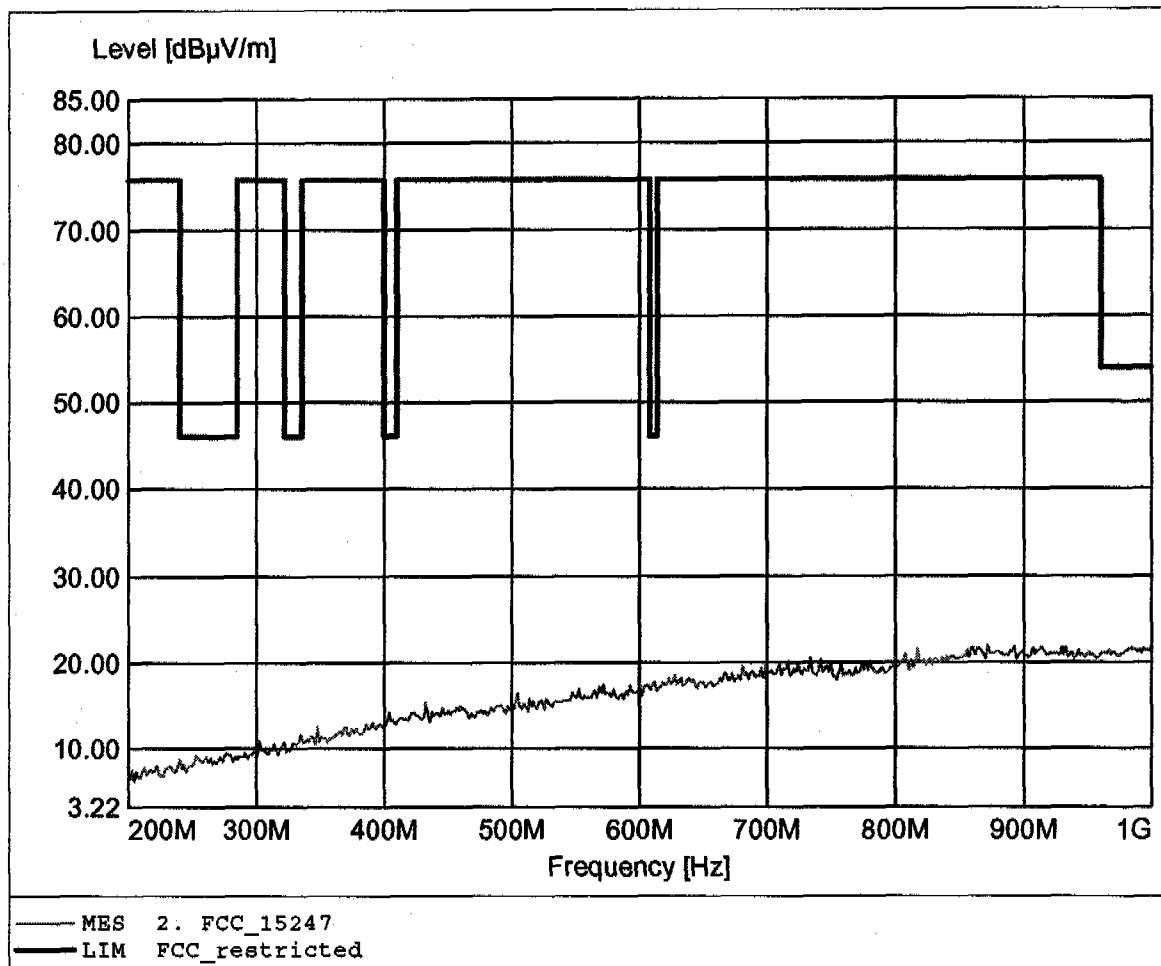
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HL 223, amplif.
Comment 2: Freq: 1.000GHz, Emax: 23.11dBµV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

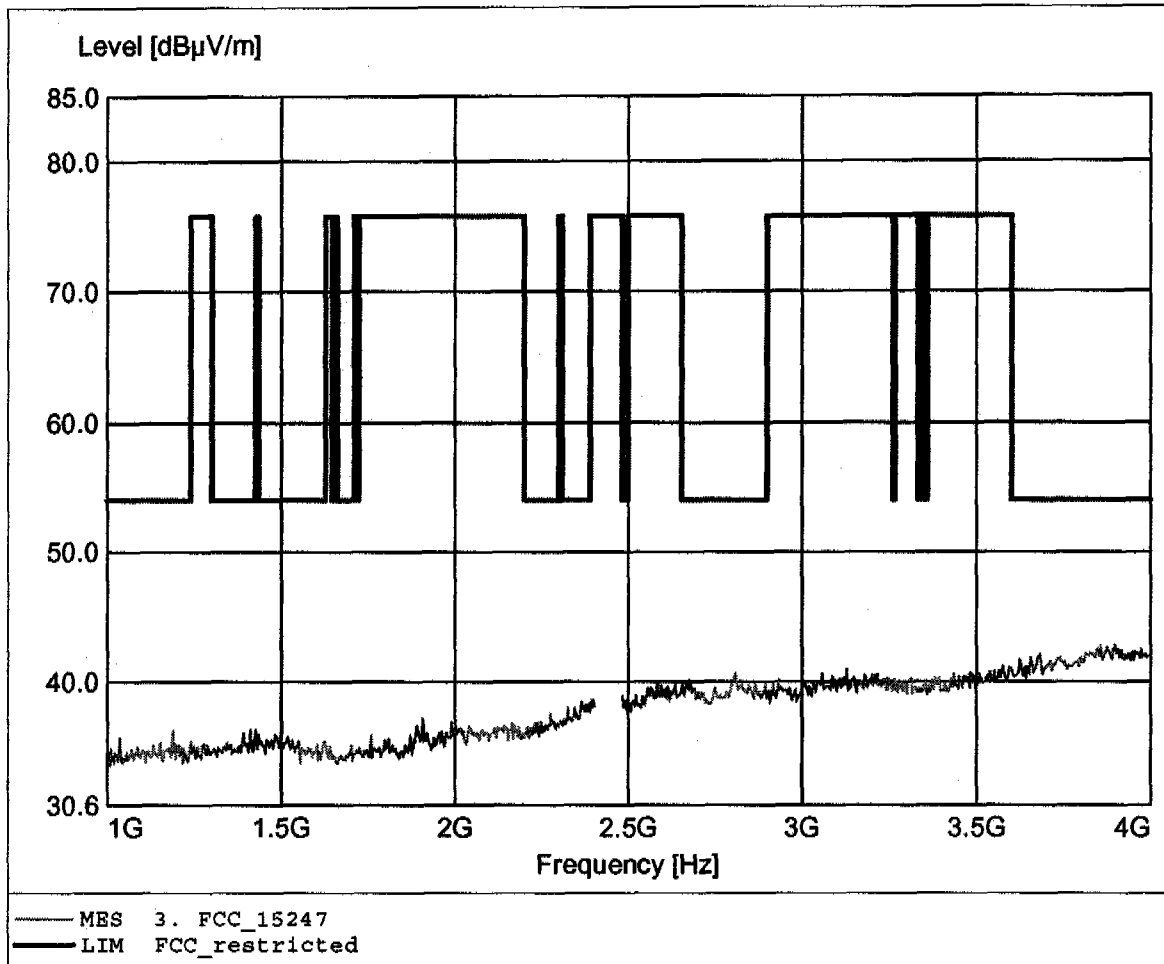
Approval Holder: GN Netcom A/S
EUT: Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HL 223, amplif.
Comment 2: Freq: 1.000GHz, Emax: 22.12dBµV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

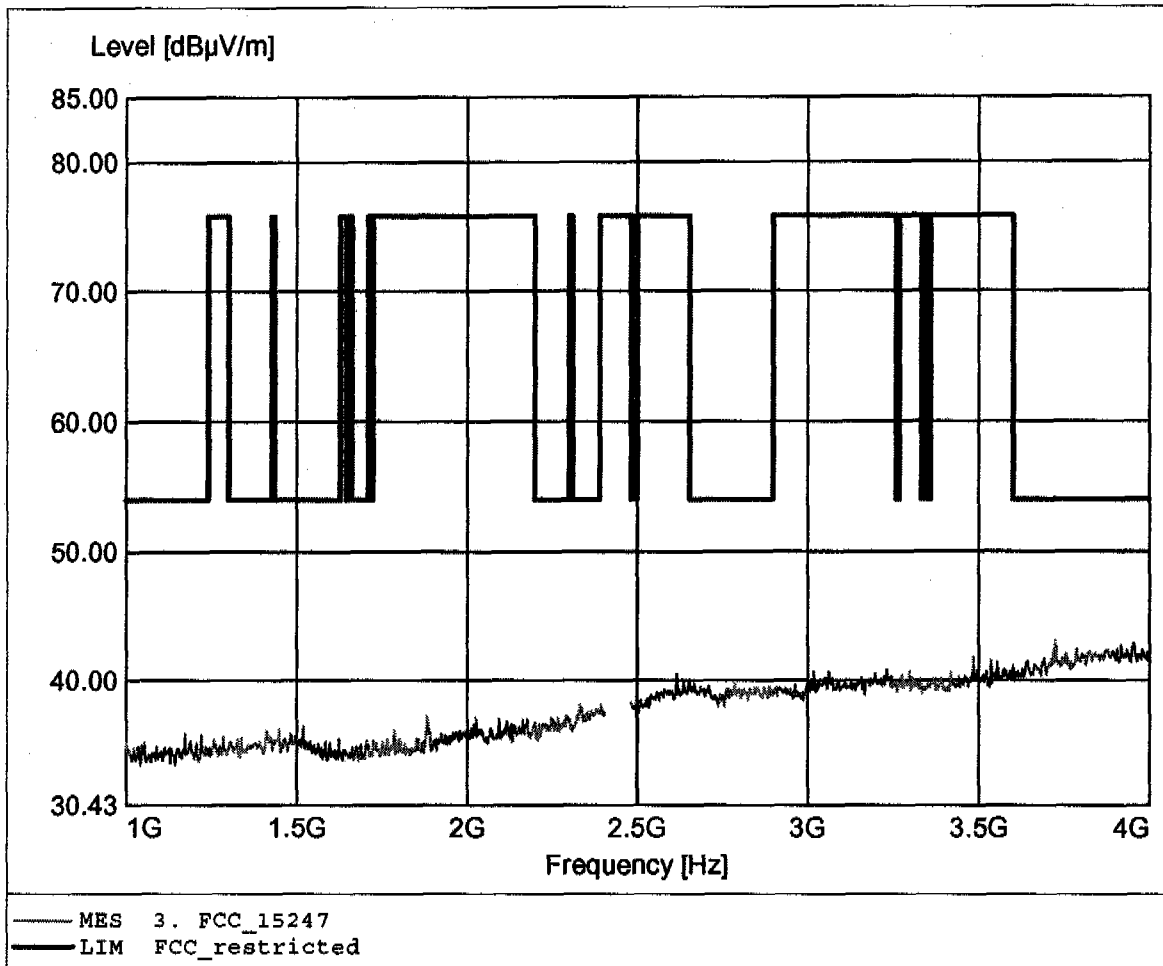
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, amplif.
Comment 2: Freq: 3.897GHz, Emax: 42.78dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

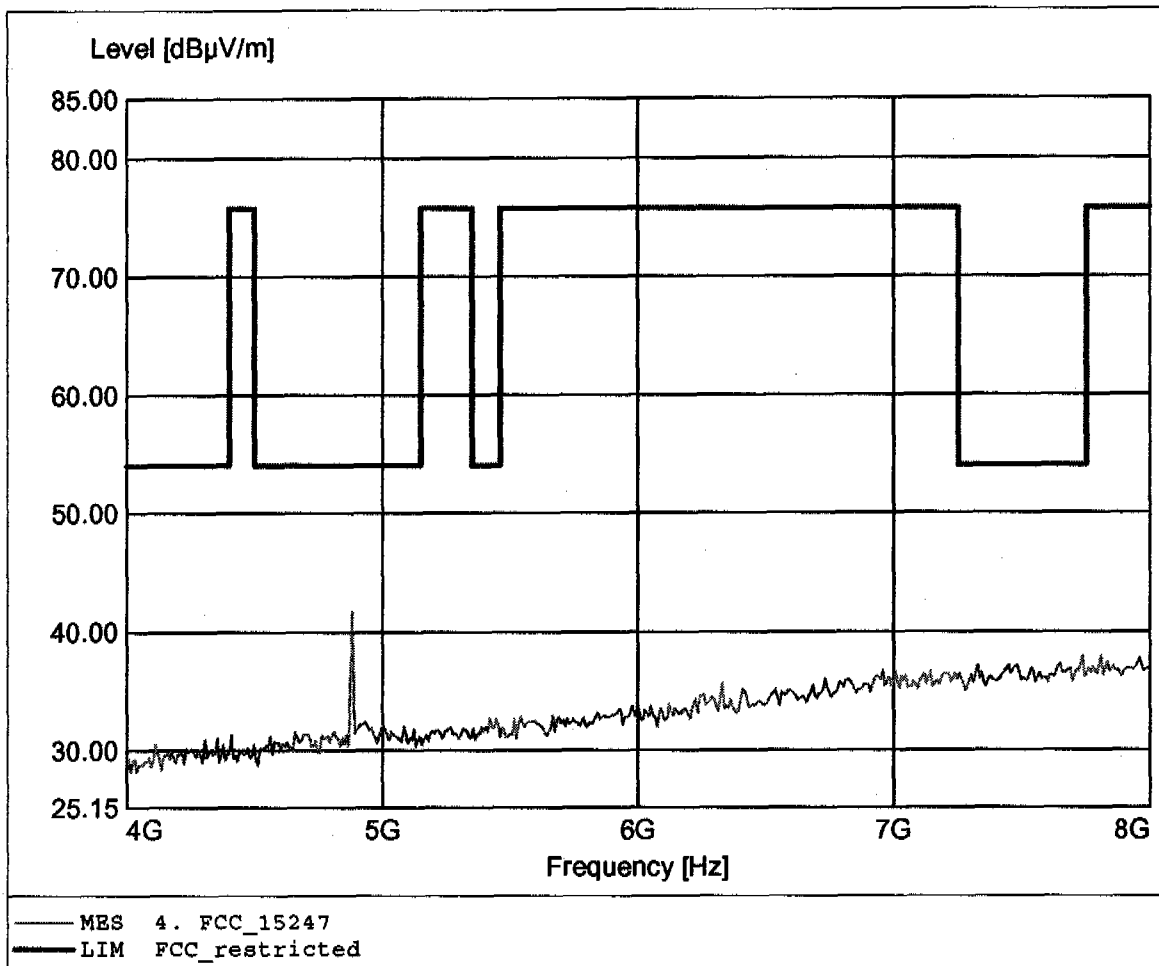
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, amplif.
Comment 2: Freq: 3.723GHz, Emax: 43.11dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

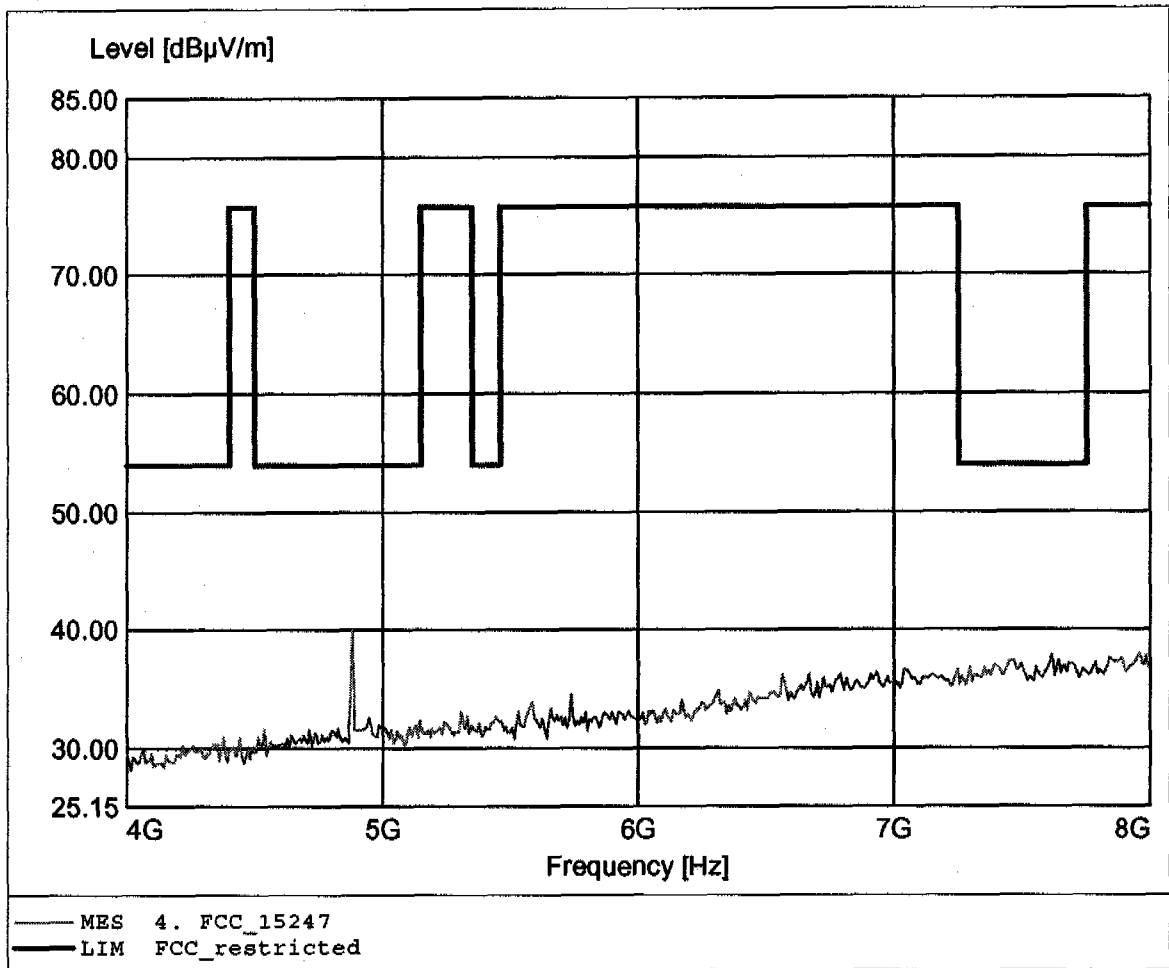
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 4.882GHz, Emax: 41.81dBµV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

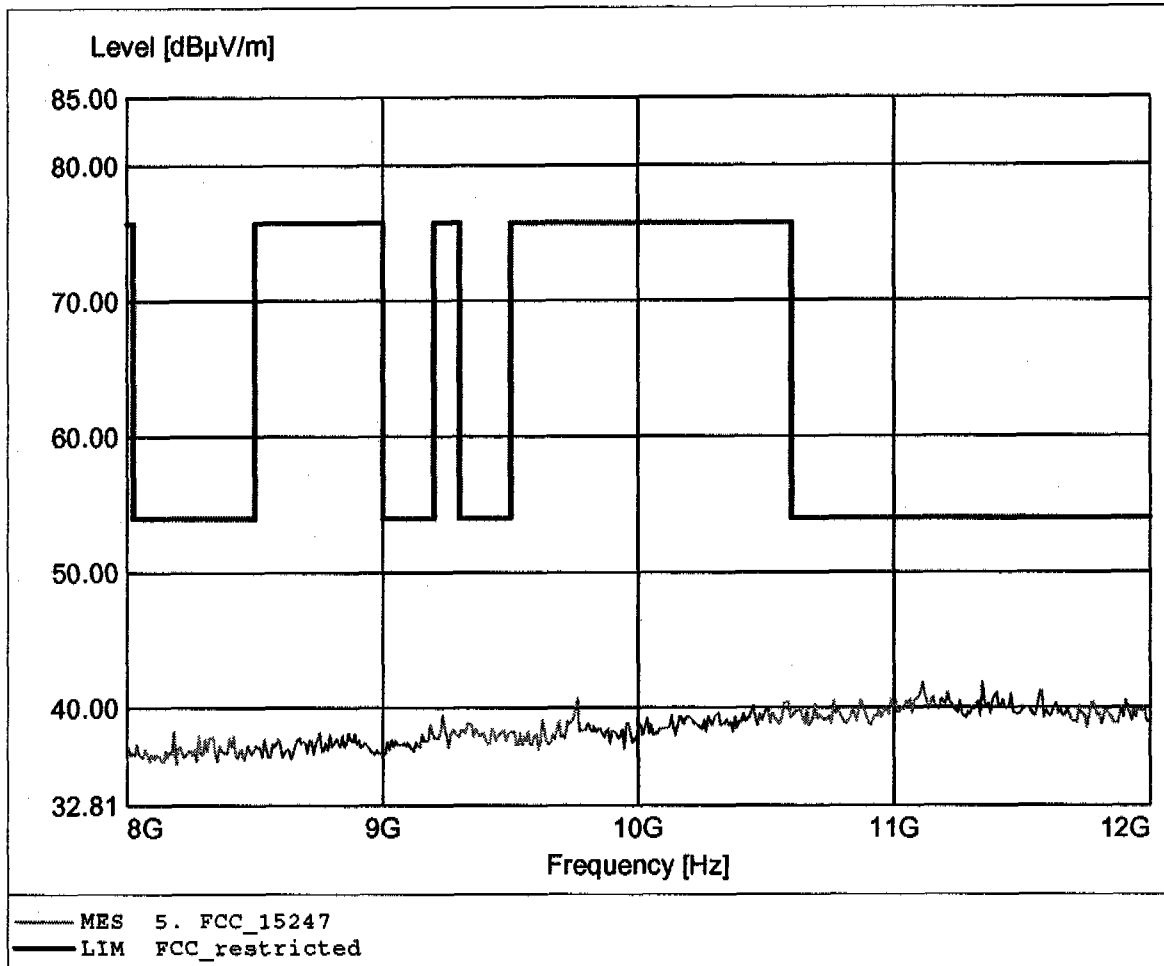
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 4.882GHz, Emax: 40.07dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

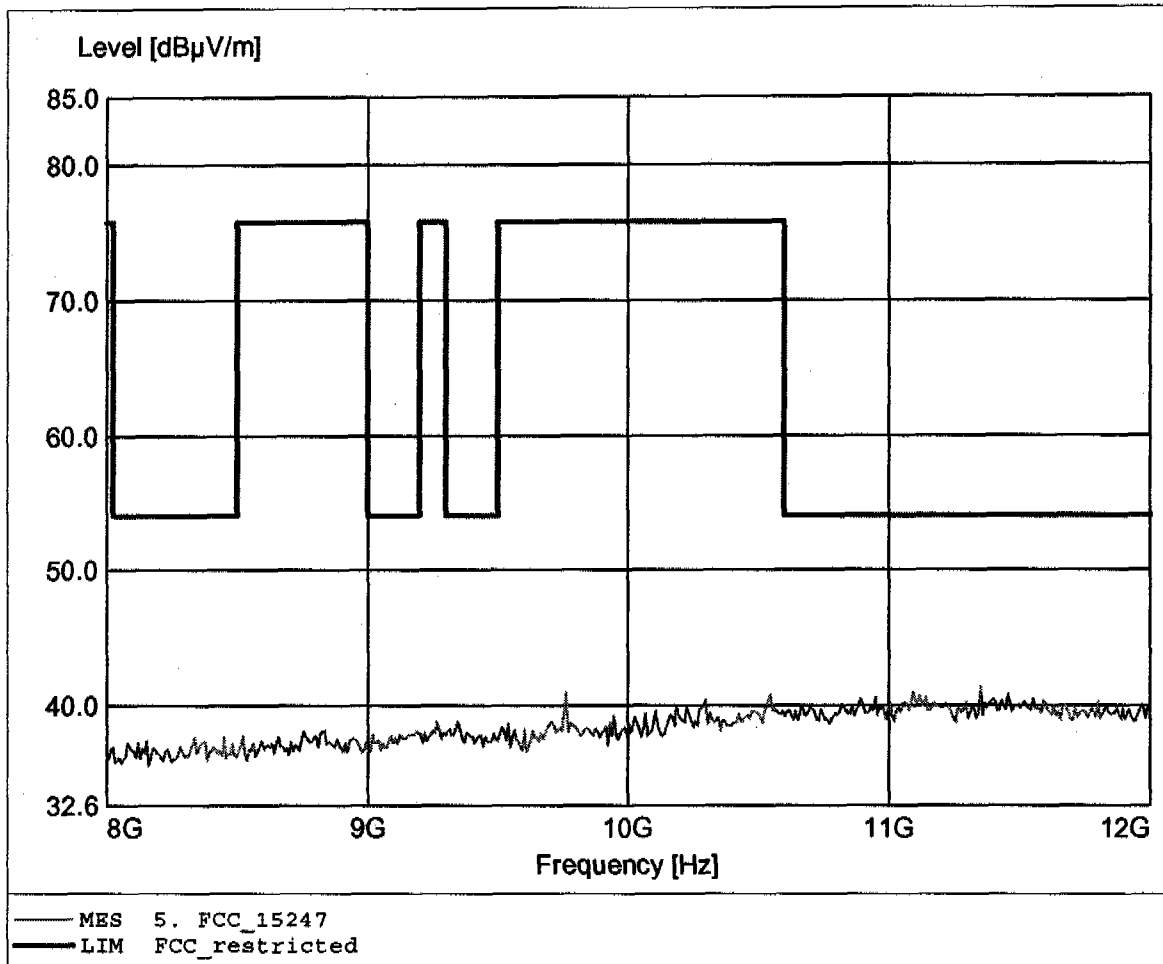
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 11.343GHz, Emax: 41.85dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

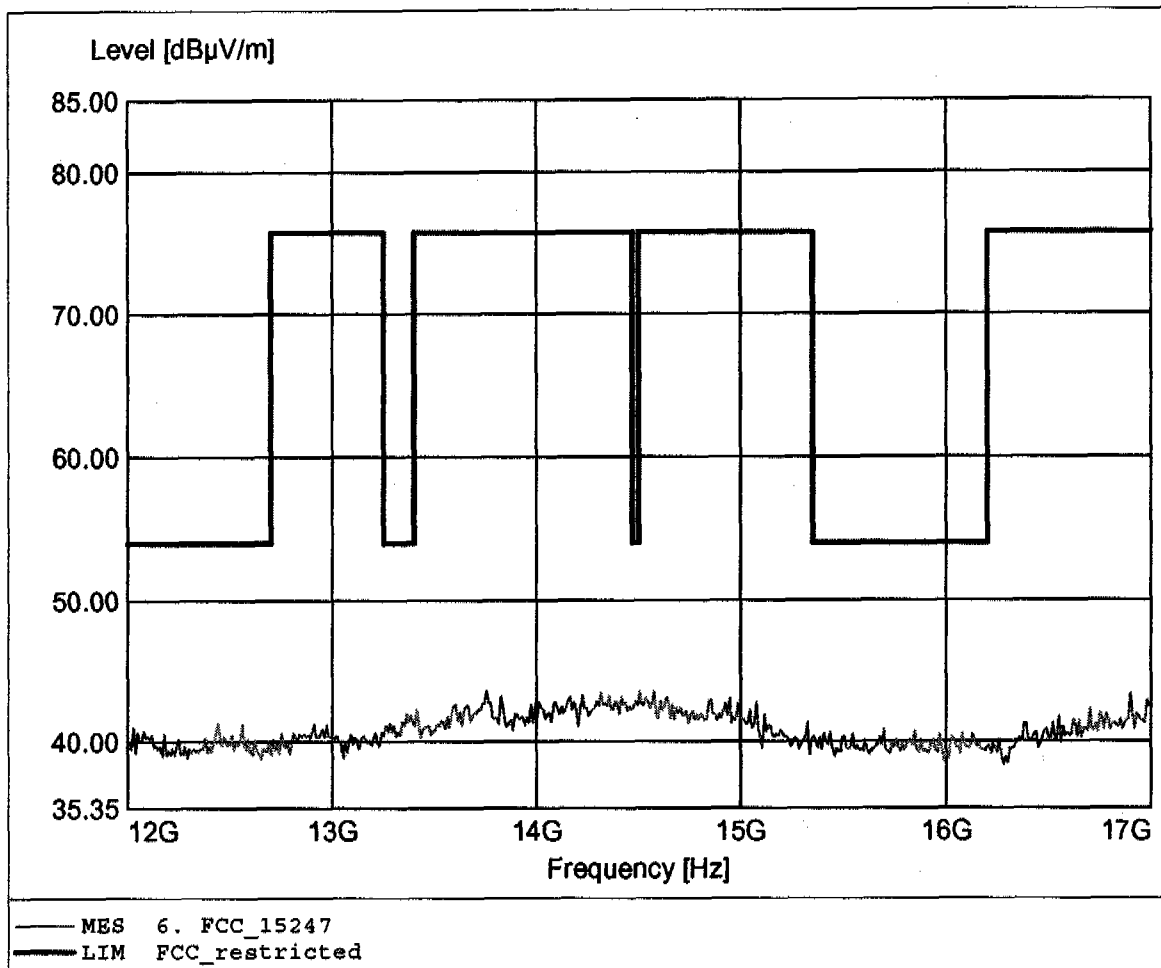
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150D BE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 11.351GHz, Emax: 41.36dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

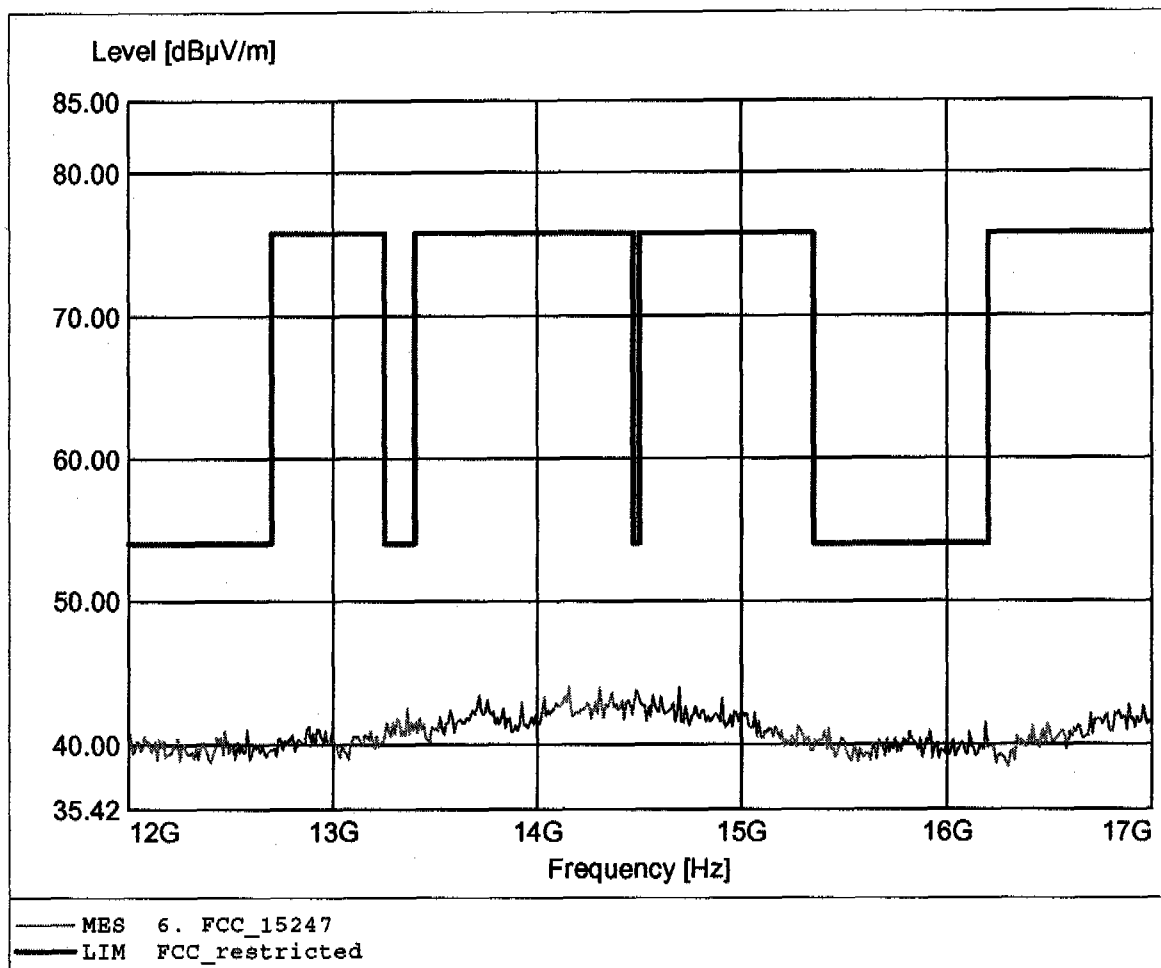
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 13.754GHz, Emax: 43.60dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

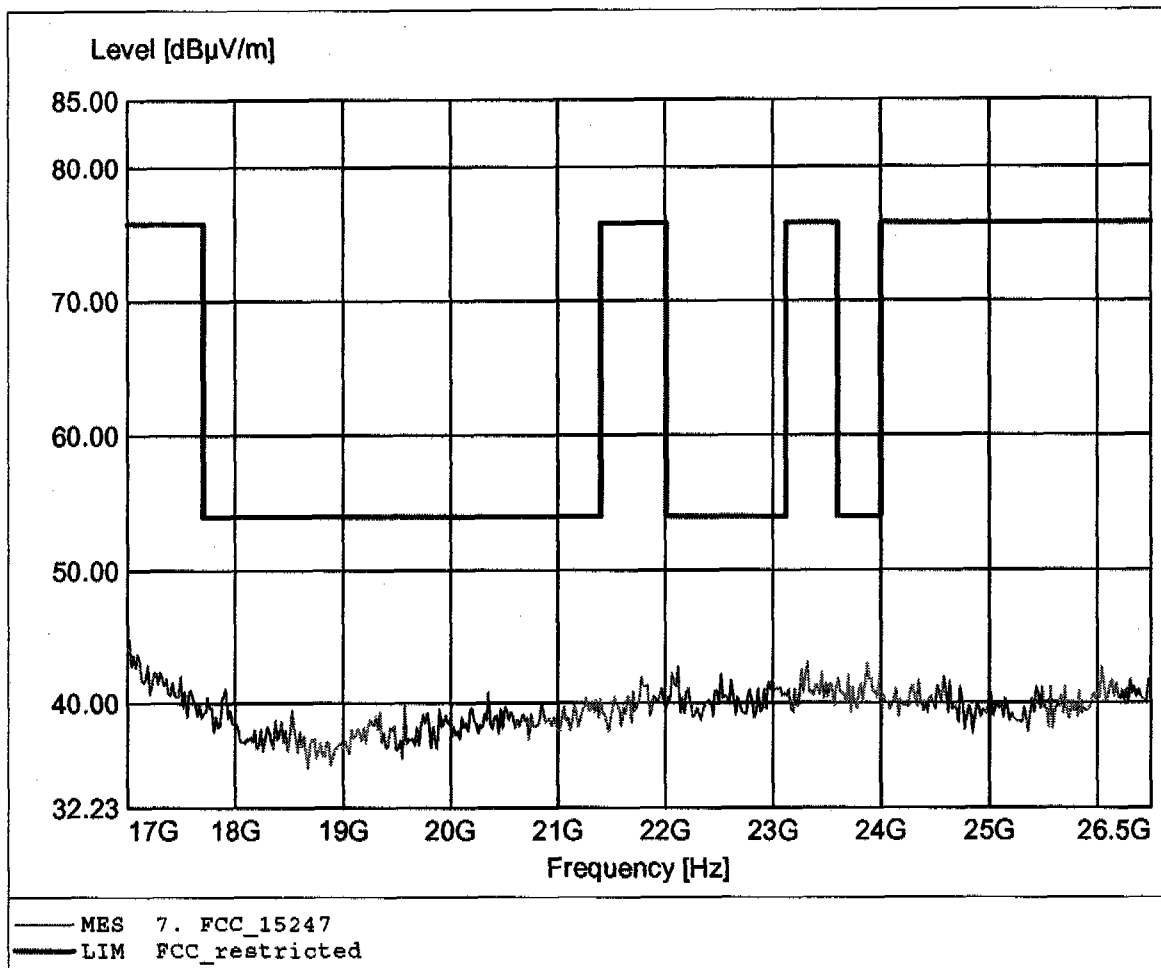
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cerovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 14.154GHz, Emax: 44.04dBµV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

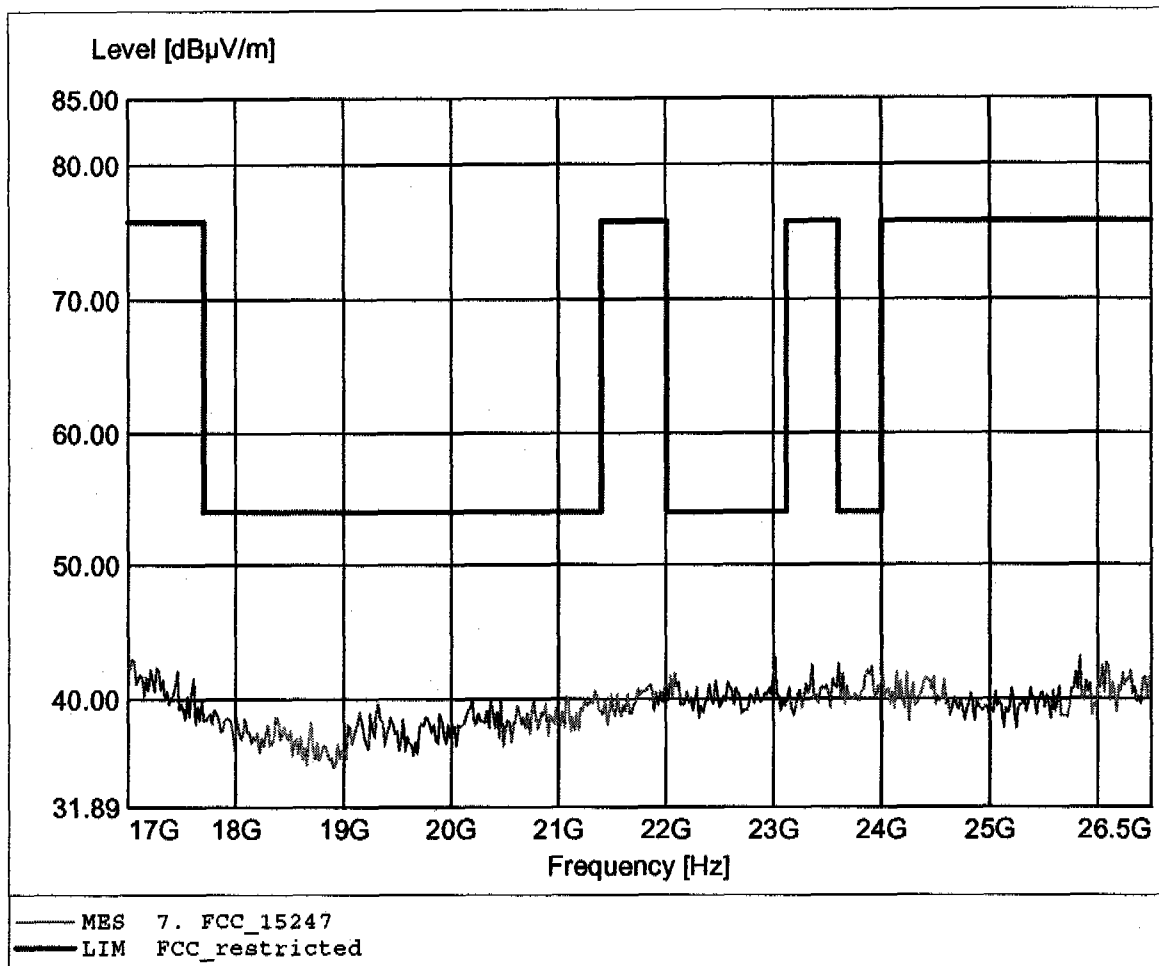
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: HL025, amplif.
Comment 2: Freq: 17.019GHz, Emax: 44.84dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

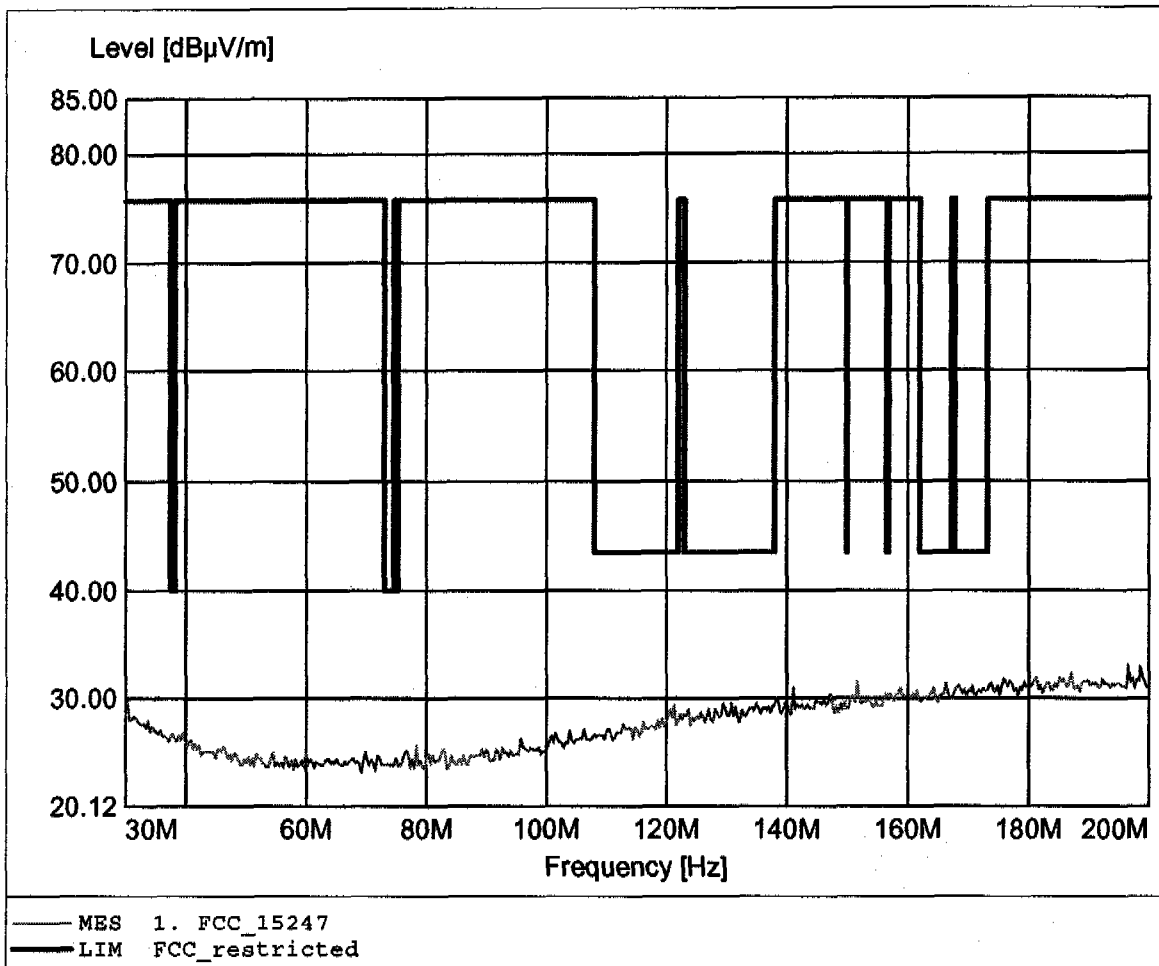
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2441 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: HL025, amplif.
Comment 2: Freq: 25.834GHz, Emax: 43.19dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

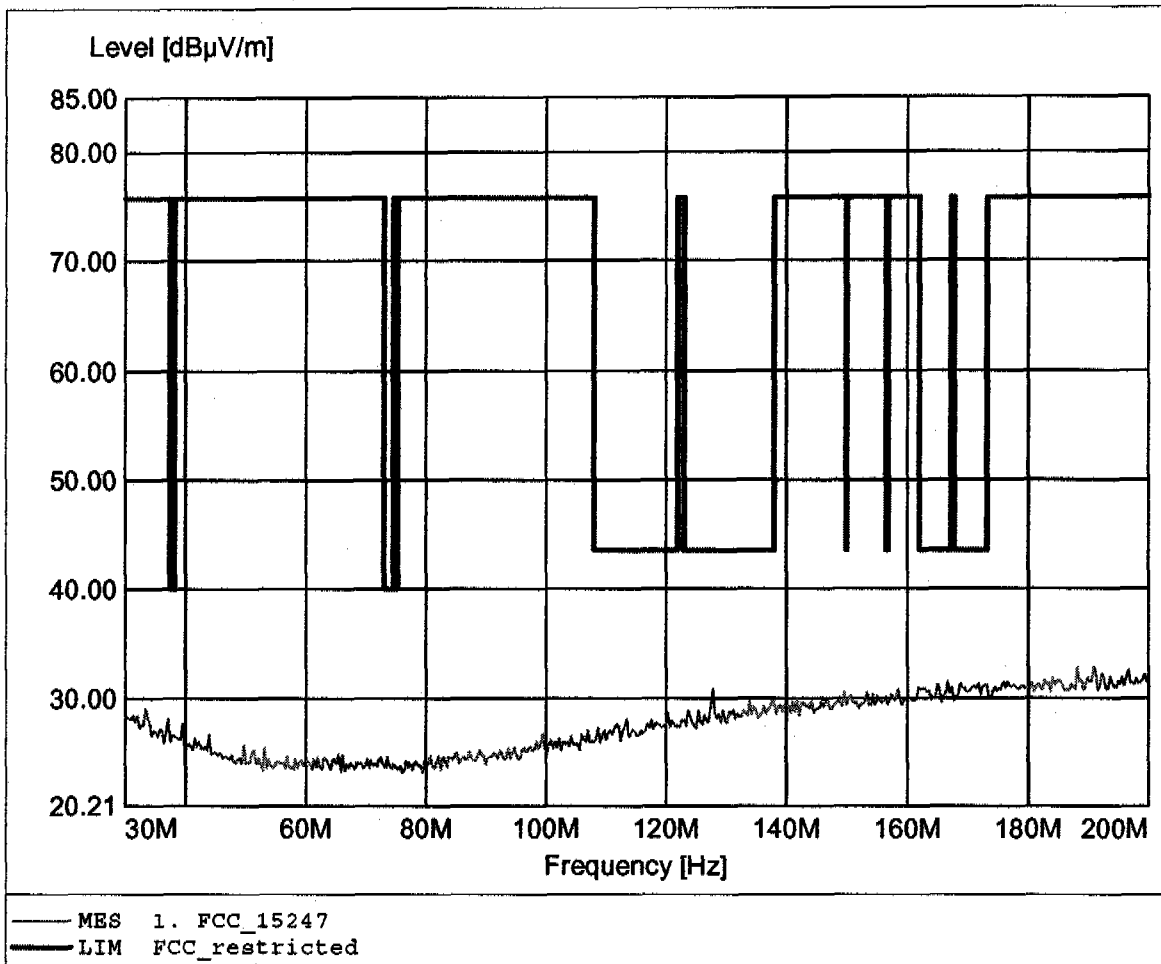
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HK 116
Comment 2: Freq: 196.593MHz, Emax: 33.08dBuV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

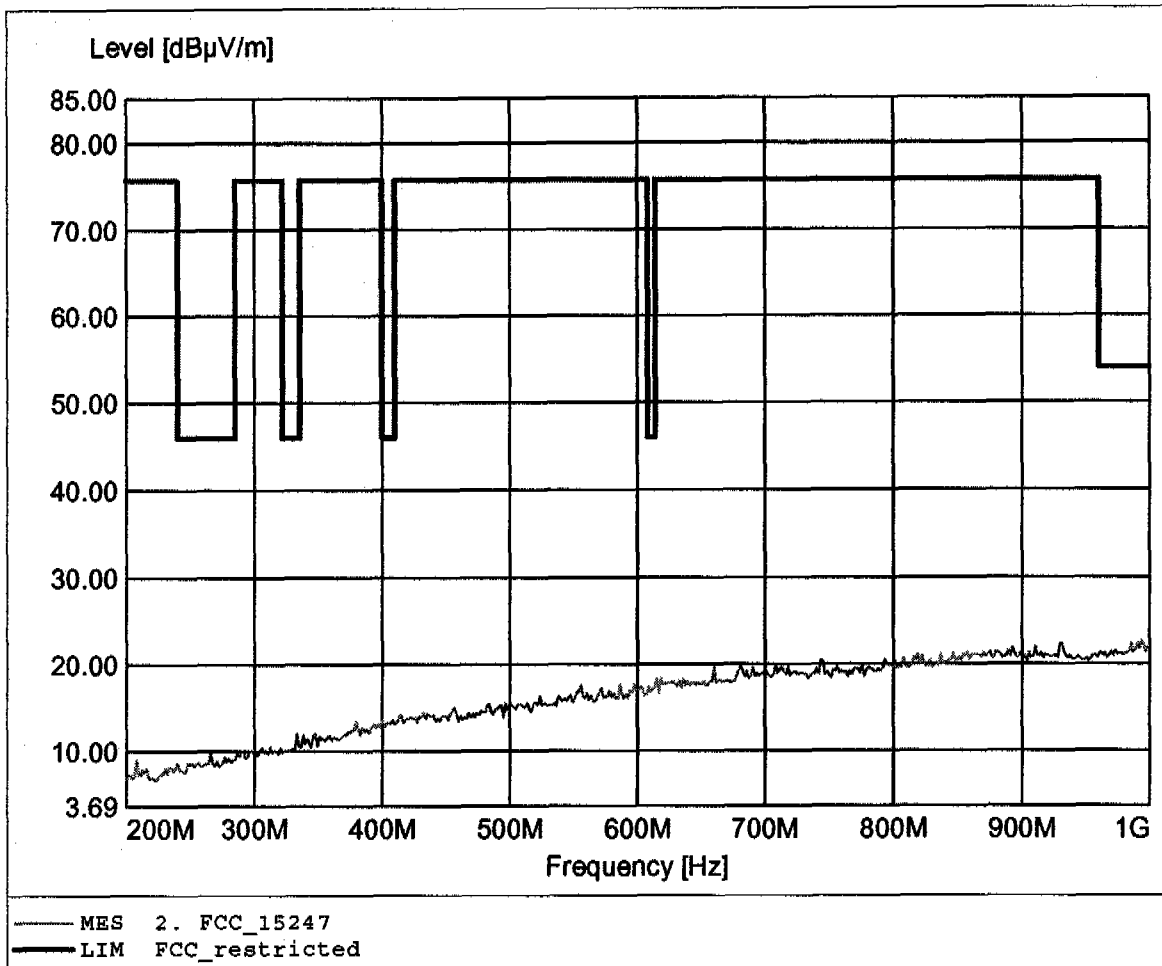
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HK 116
Comment 2: Freq: 188.076MHz, Emax: 32.86dBuV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

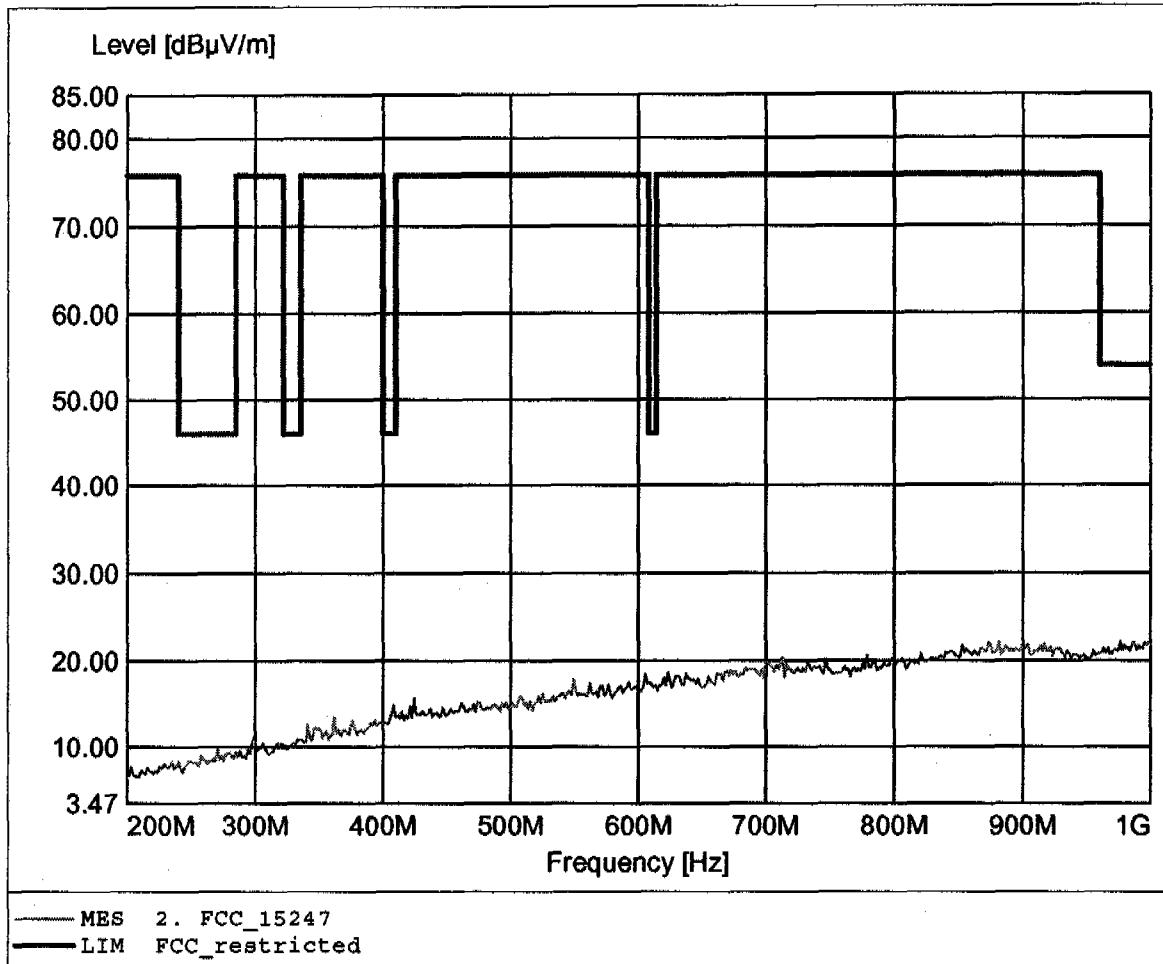
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HL 223, amplif.
Comment 2: Freq: 993.587MHz, Emax: 22.69dBuV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

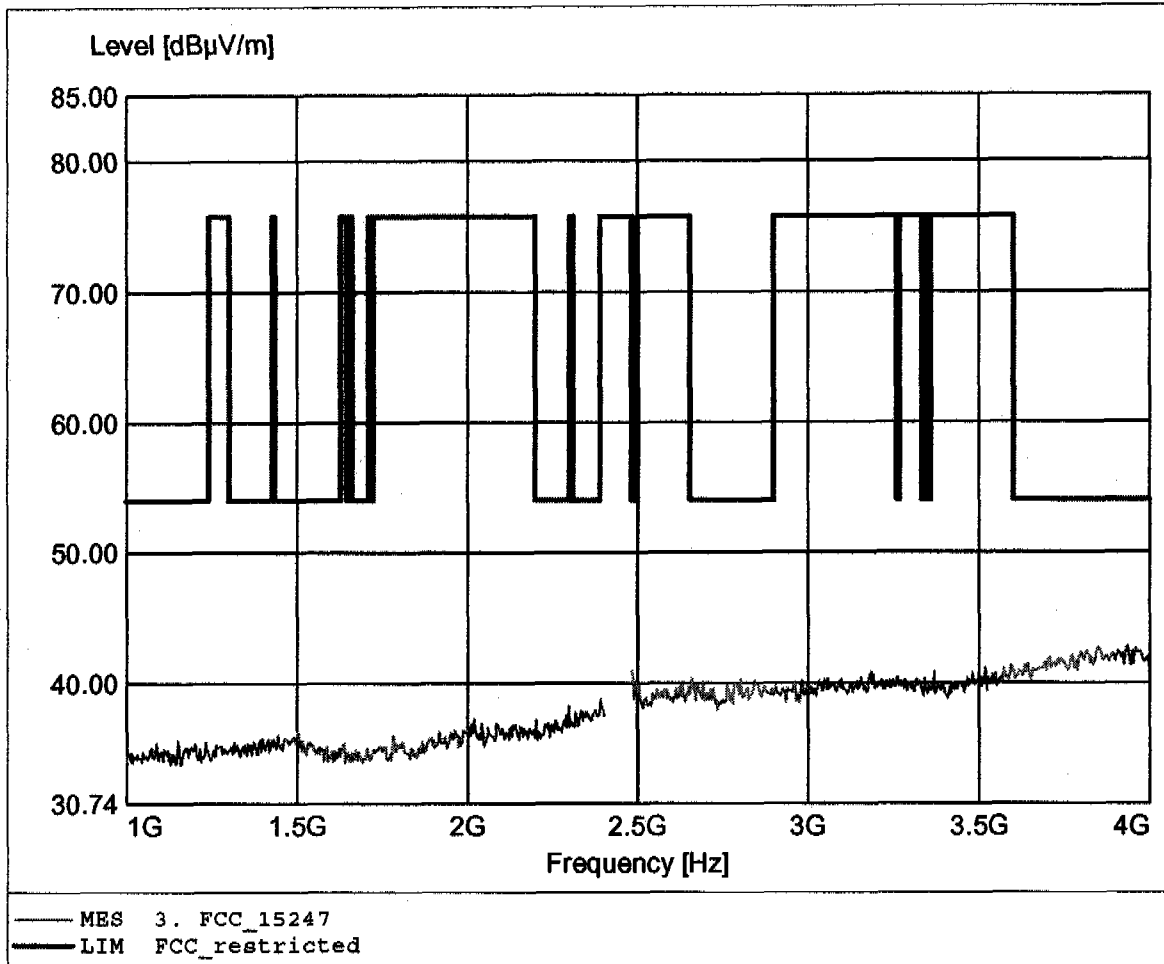
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247
Comment 1: Dist.: 3m, Ant.: HL 223, amplif.
Comment 2: Freq: 975.952MHz, Emax: 22.26dBµV/m, RBW: 100kHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

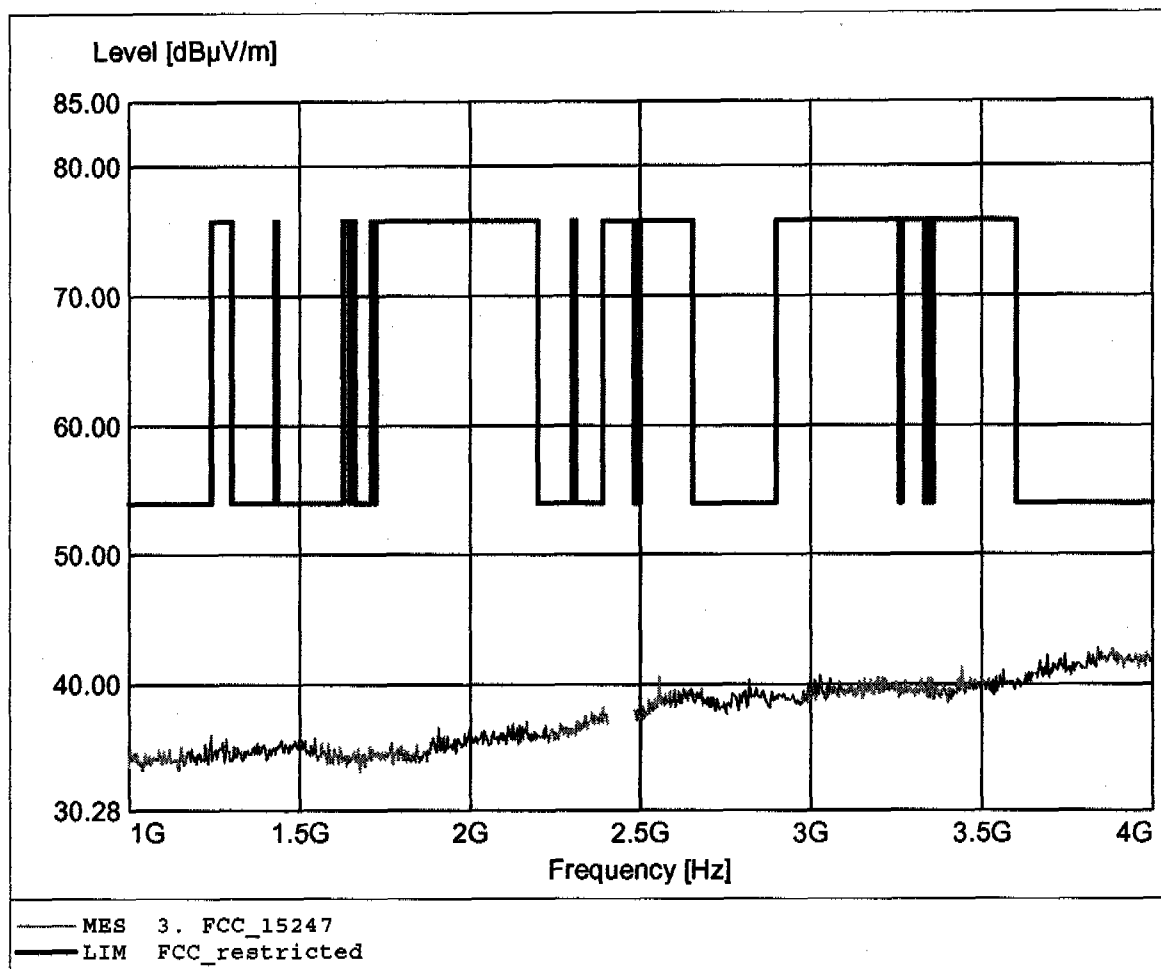
Approval Holder: GN Netcom A/S
EUT: Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, amplif.
Comment 2: Freq: 3.933GHz, Emax: 42.87dBµV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

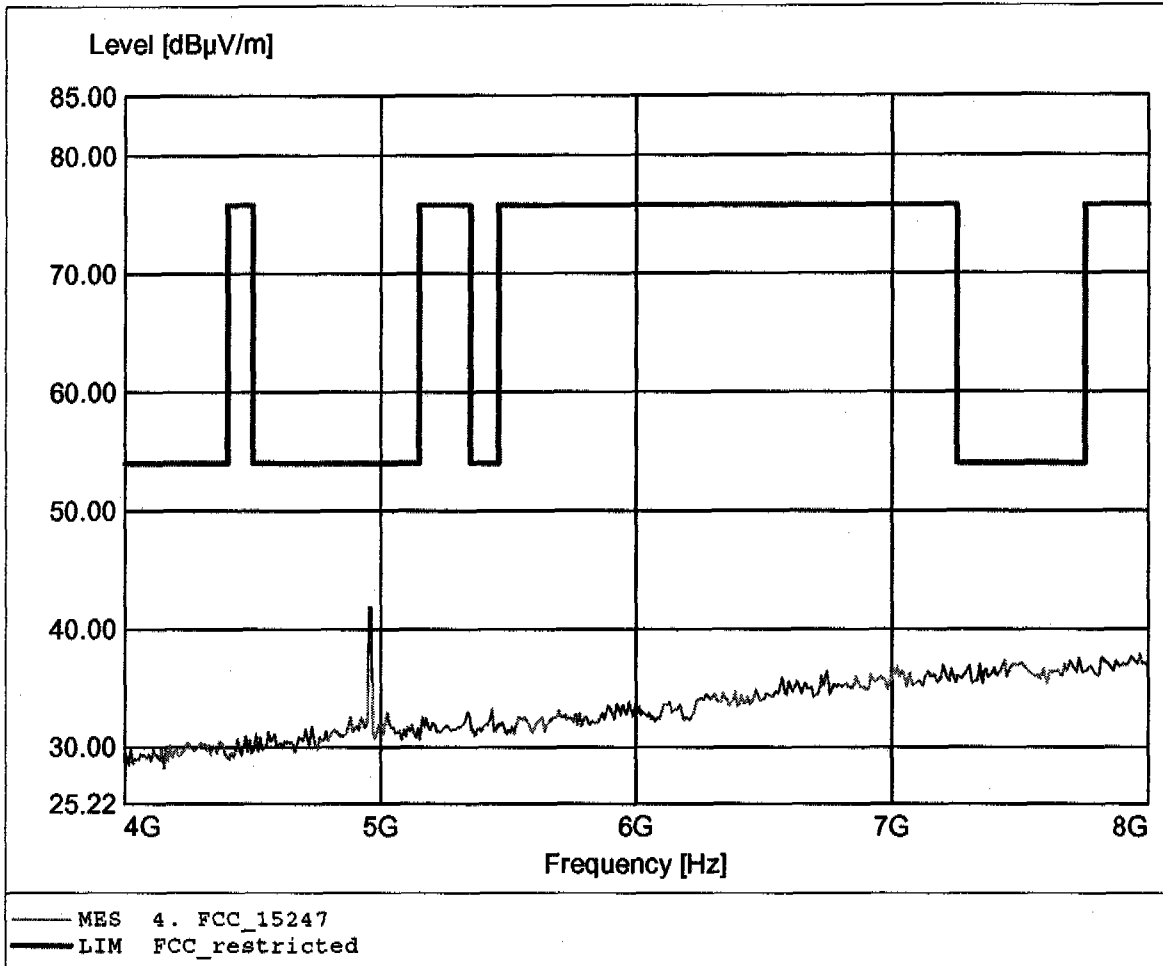
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cerovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, amplif.
Comment 2: Freq: 3.839GHz, Emax: 42.77dBµV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

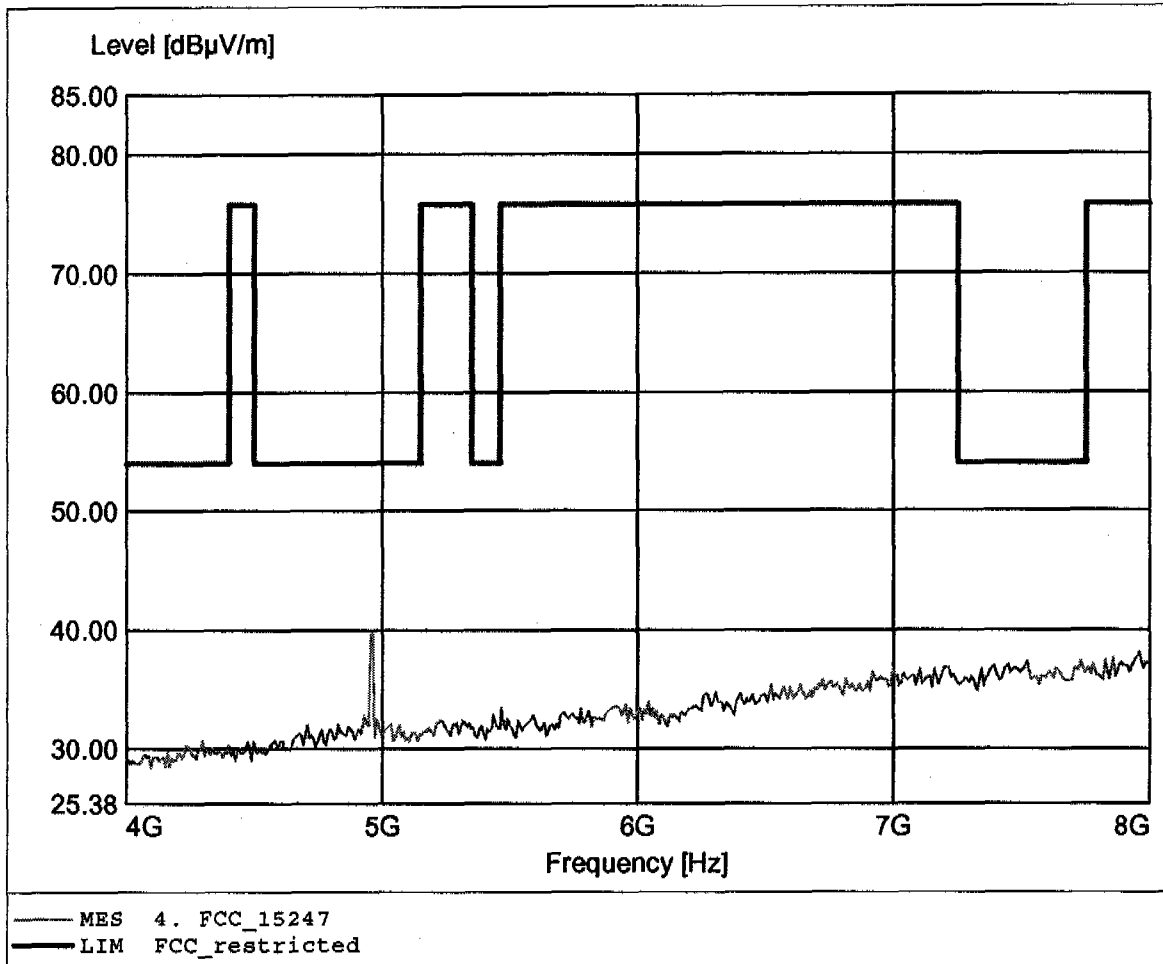
Approval Holder: GN Netcom A/S
EUT: Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 4.954GHz, Emax: 41.85dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

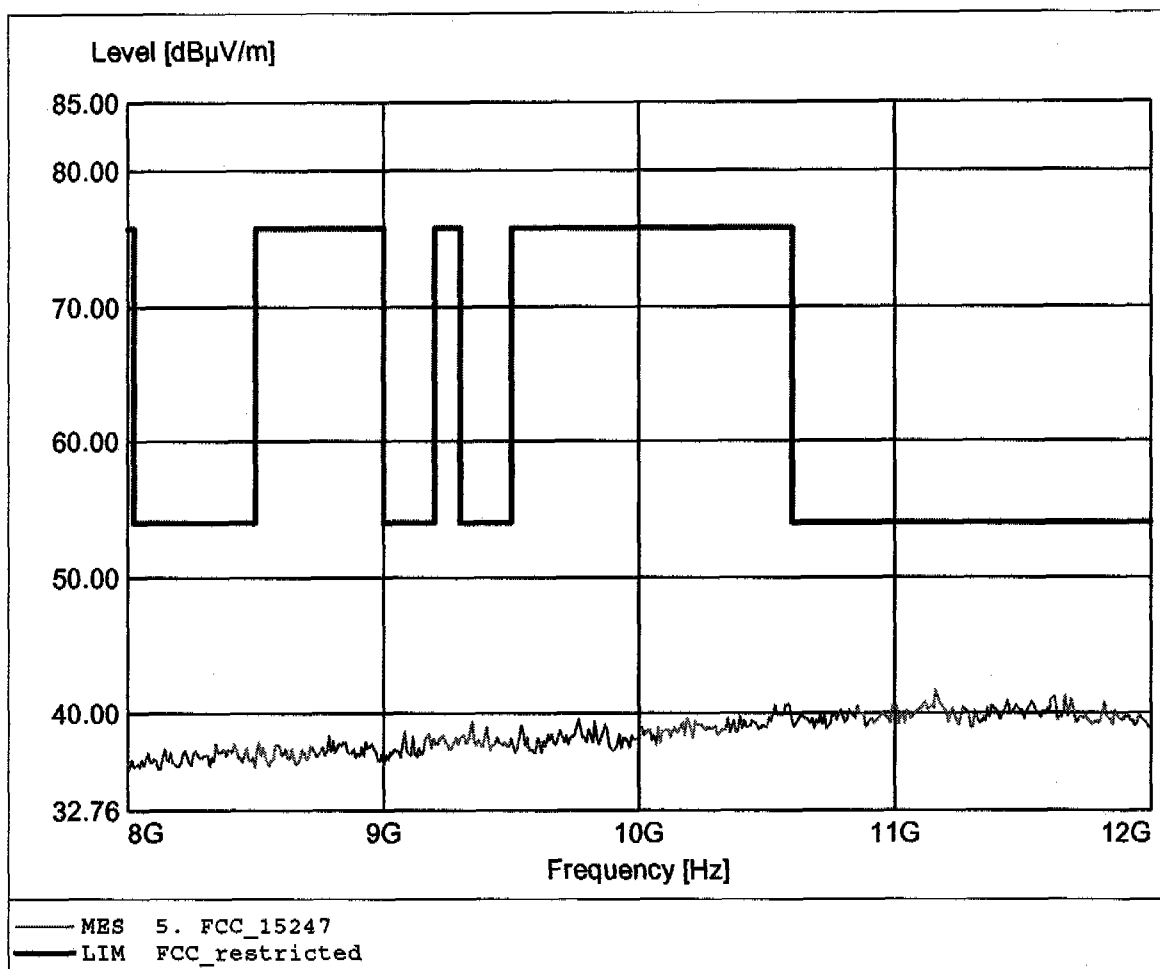
Approval Holder: GN Netcom A/S
EUT: Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 4.962GHz, Emax: 39.74dBµV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

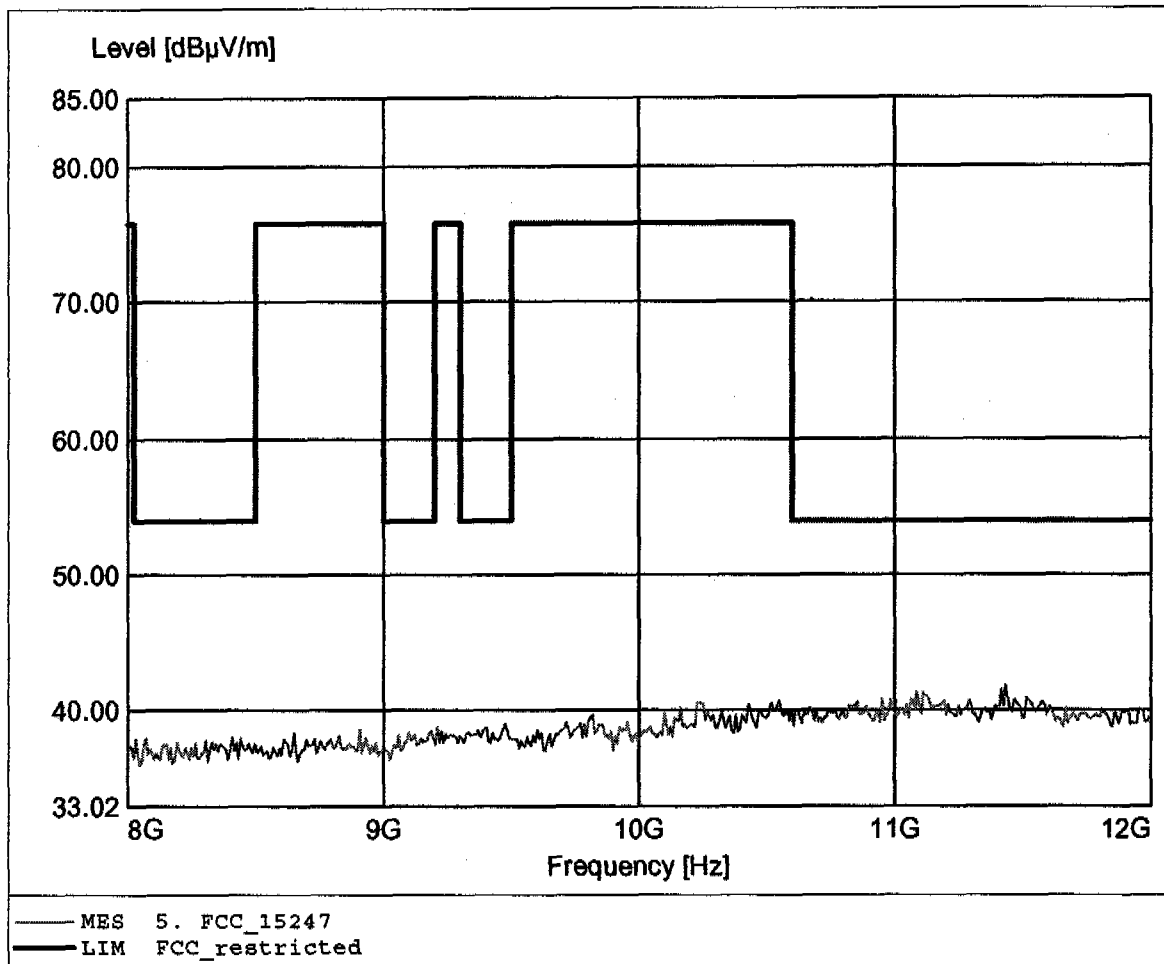
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 11.158GHz, Emax: 41.73dBµV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

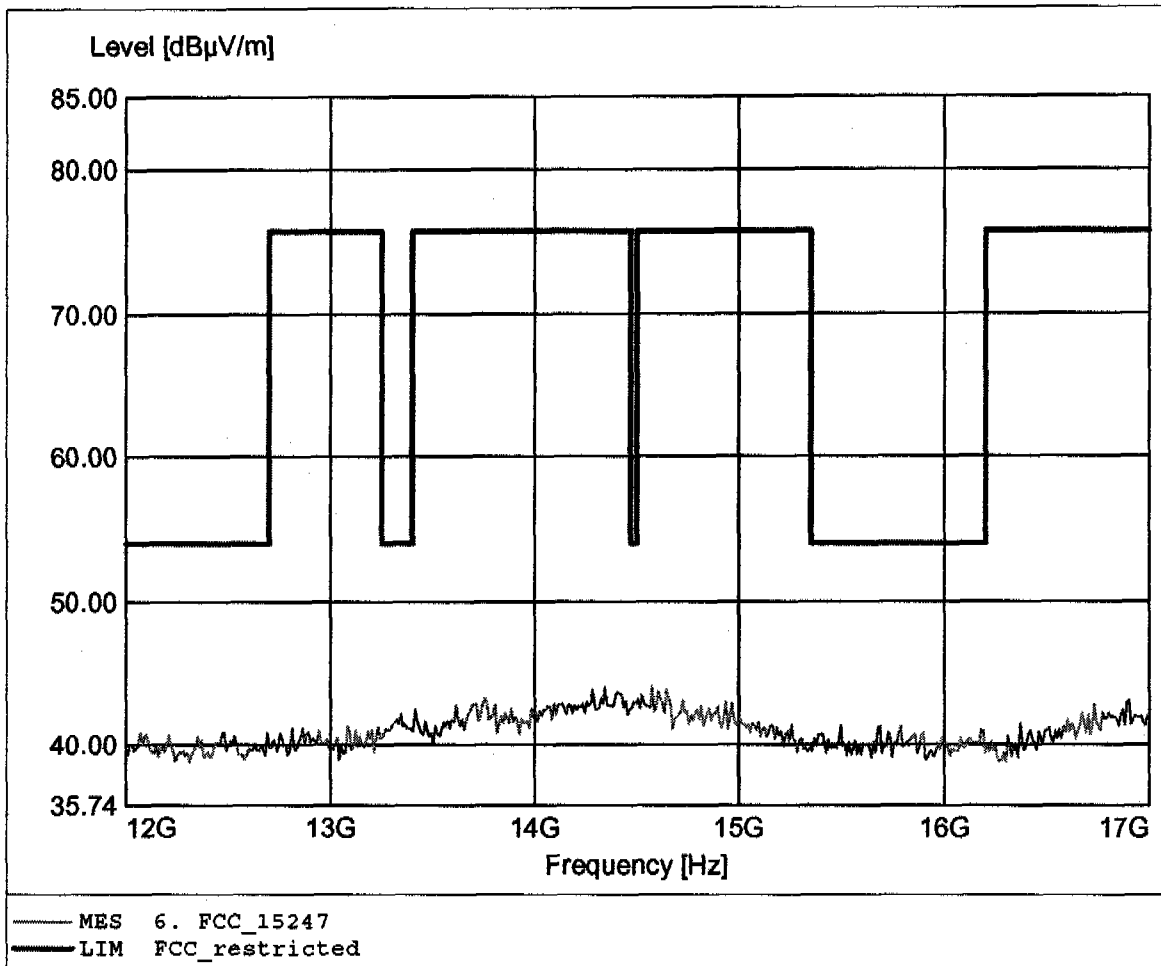
Approval Holder: GN Netcom A/S
EUT: Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 11.431GHz, Emax: 41.89dBµV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

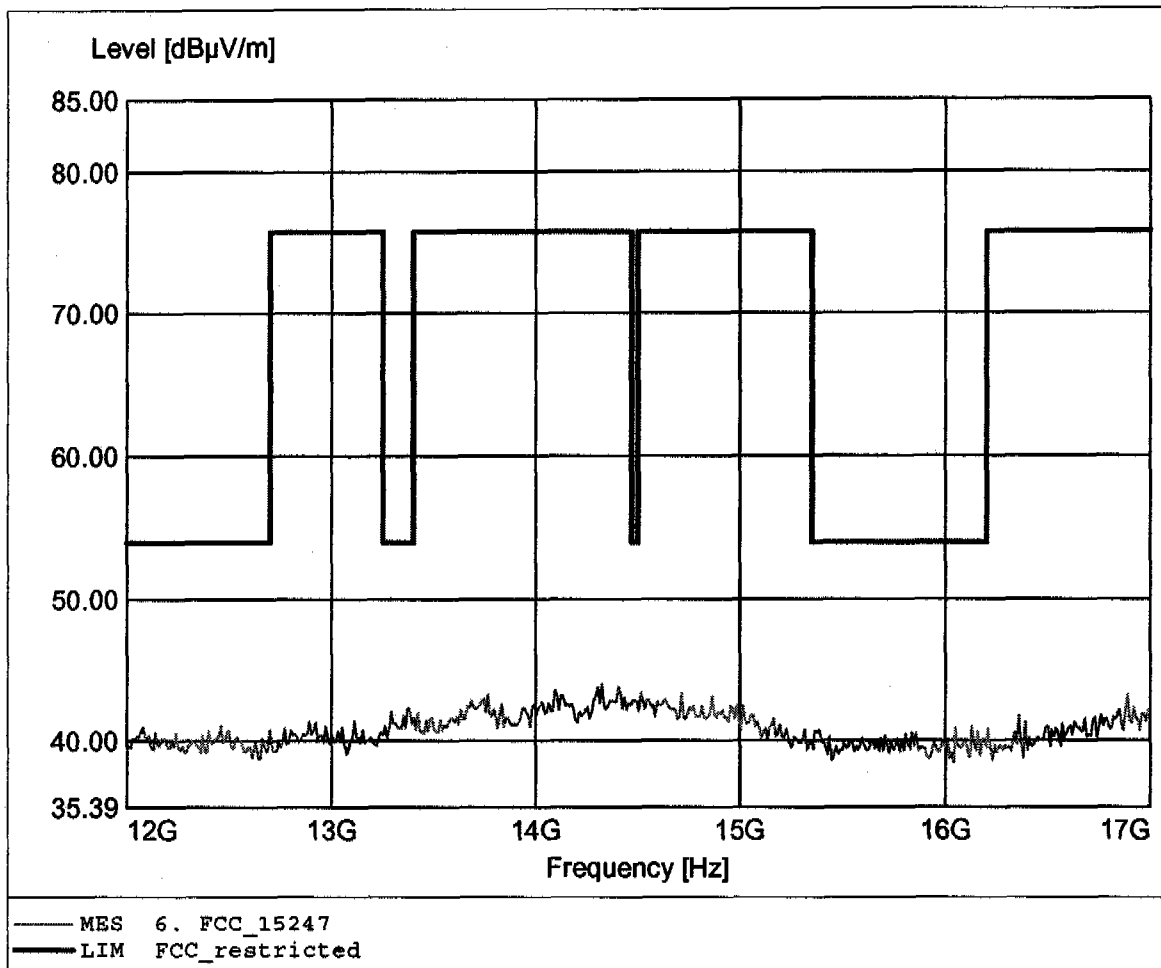
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 14.575GHz, Emax: 44.13dBµV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

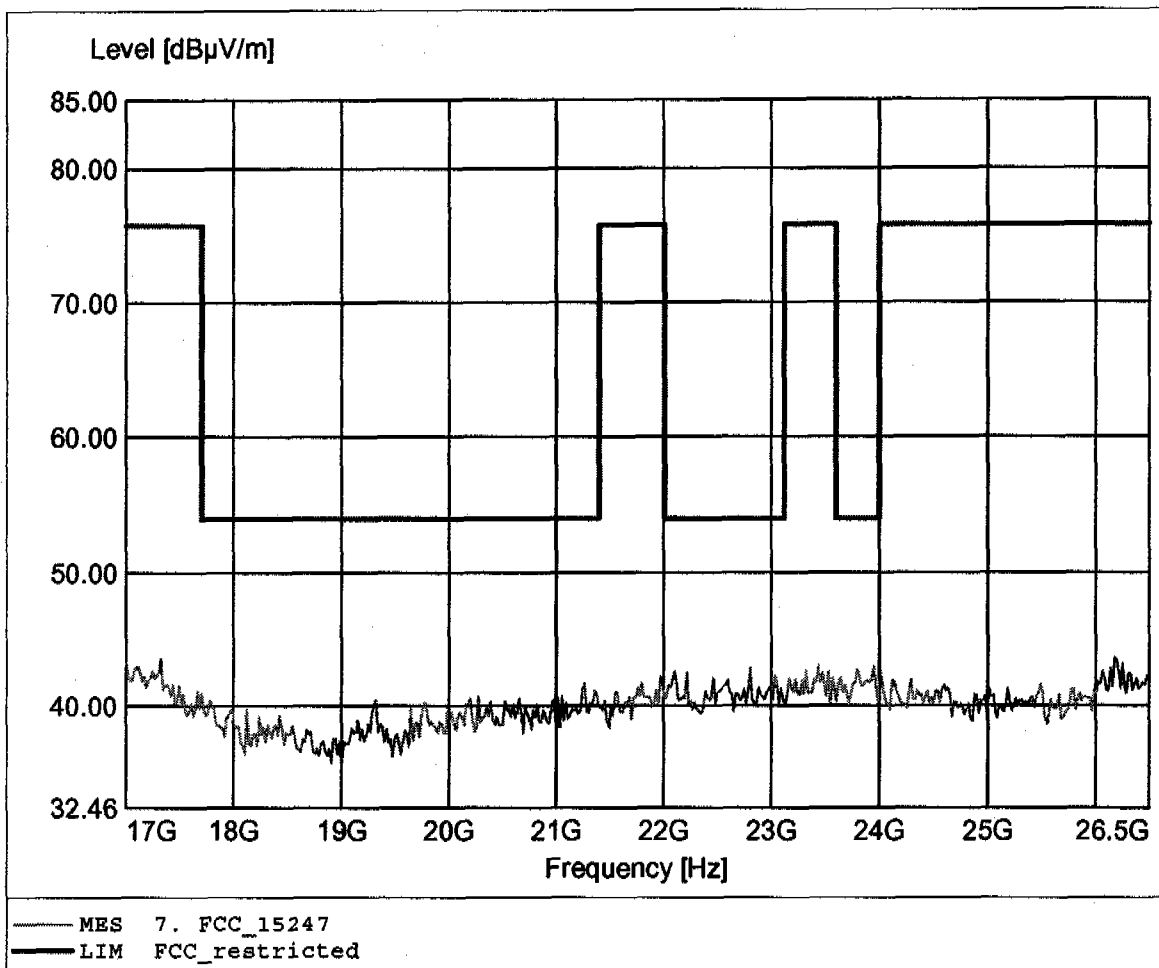
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: BBHA9120D, ampl.+HP.
Comment 2: Freq: 14.325GHz, Emax: 44.00dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

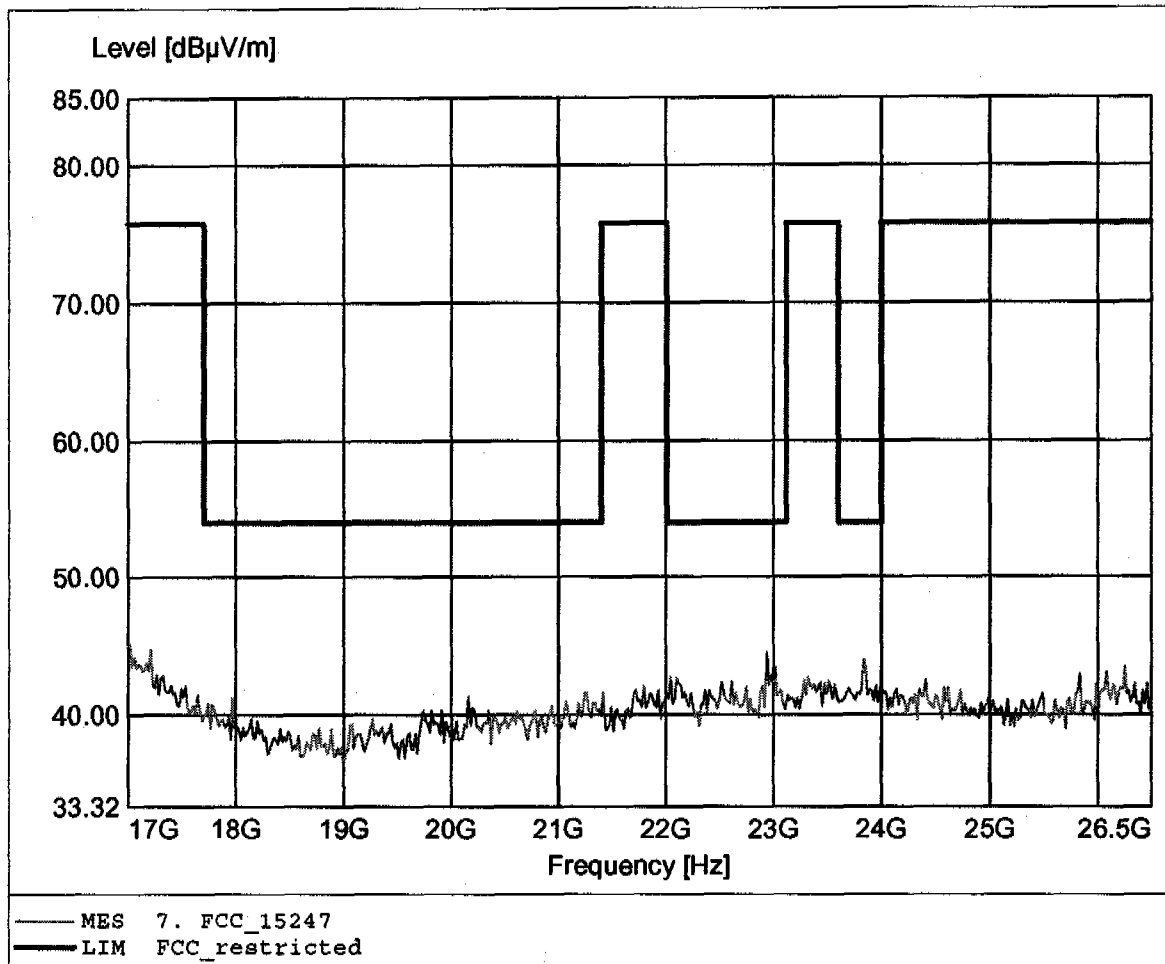
Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: HL025, amplif.
Comment 2: Freq: 26.176GHz, Emax: 43.63dBuV/m, RBW: 1MHz



Spurious emissions Field Strength

FCC RULES PART 15, SUBPART C

Approval Holder: GN Netcom A/S
EUT : Bluetooth headset
Model: Samsung WEP 150 DBE / 2480 MHz
Test Site / Operator: ETS / Mr. Cersovsky
Temperature/ Voltage: 25°C / Unom: 3,7 V DC
Test Specification: according to §15.247, peak detector
Comment 1: Dist.: 3m, Ant.: HL025, amplif.
Comment 2: Freq: 17.019GHz, Emax: 45.13dBuV/m, RBW: 1MHz





Appendix D

Spurious Emissions conducted - Transmitter operating

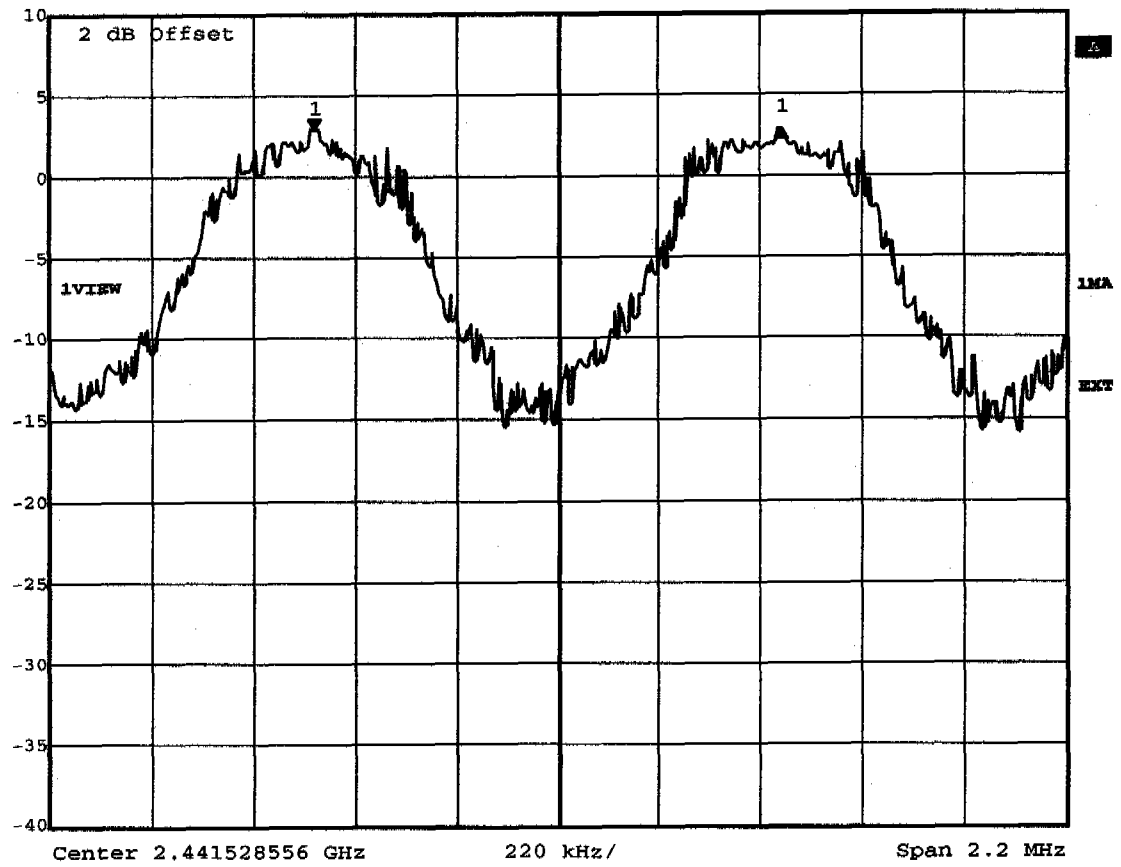


Appendix E

Carrier Frequency Separation



Delta 1 [T1] RBW 100 kHz RF Att 40 dB
Ref Lvl -0.07 dB VBW 100 kHz
10 dBm 1.01402806 MHz SWT 5 ms Unit dBm



Title: Carrier Frequency Separation
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 09:12:23



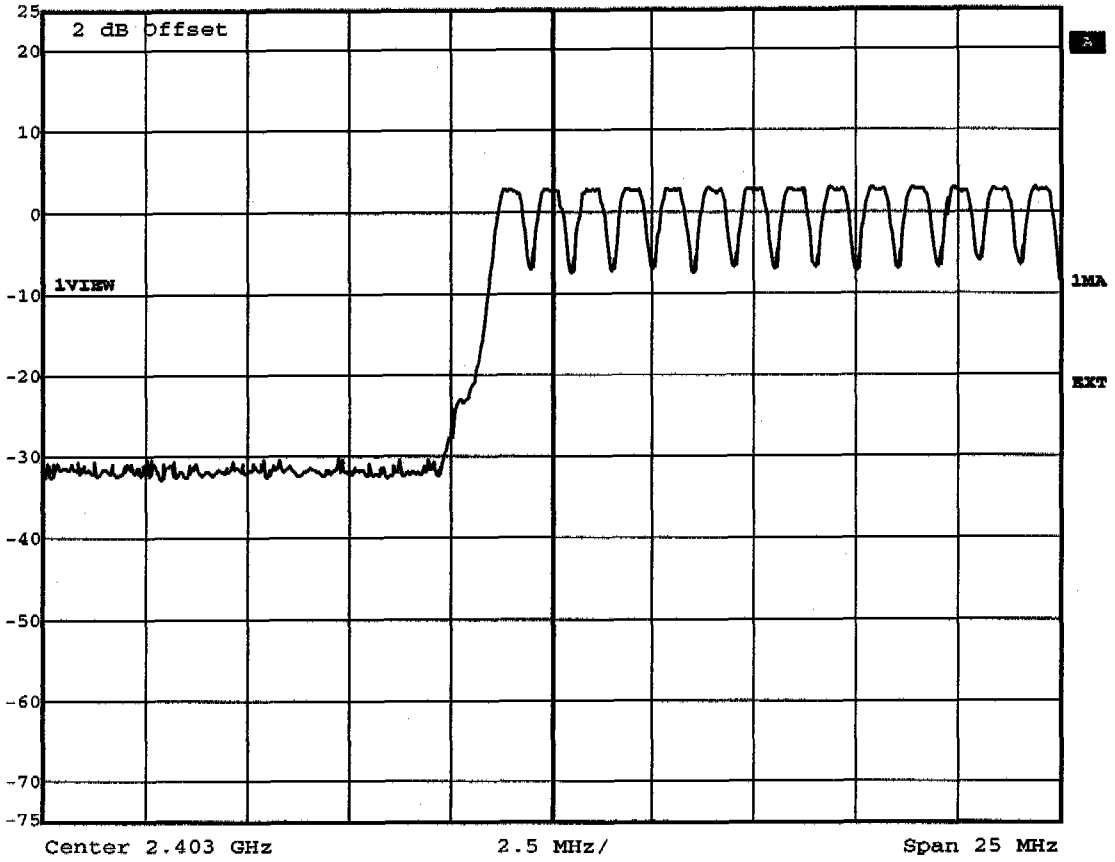
Appendix F

Number of Hopping Frequencies



Ref Lvl
25 dBm

RBW 300 kHz RF Att 50 dB
VBW 300 kHz
SWT 5 ms Unit dBm

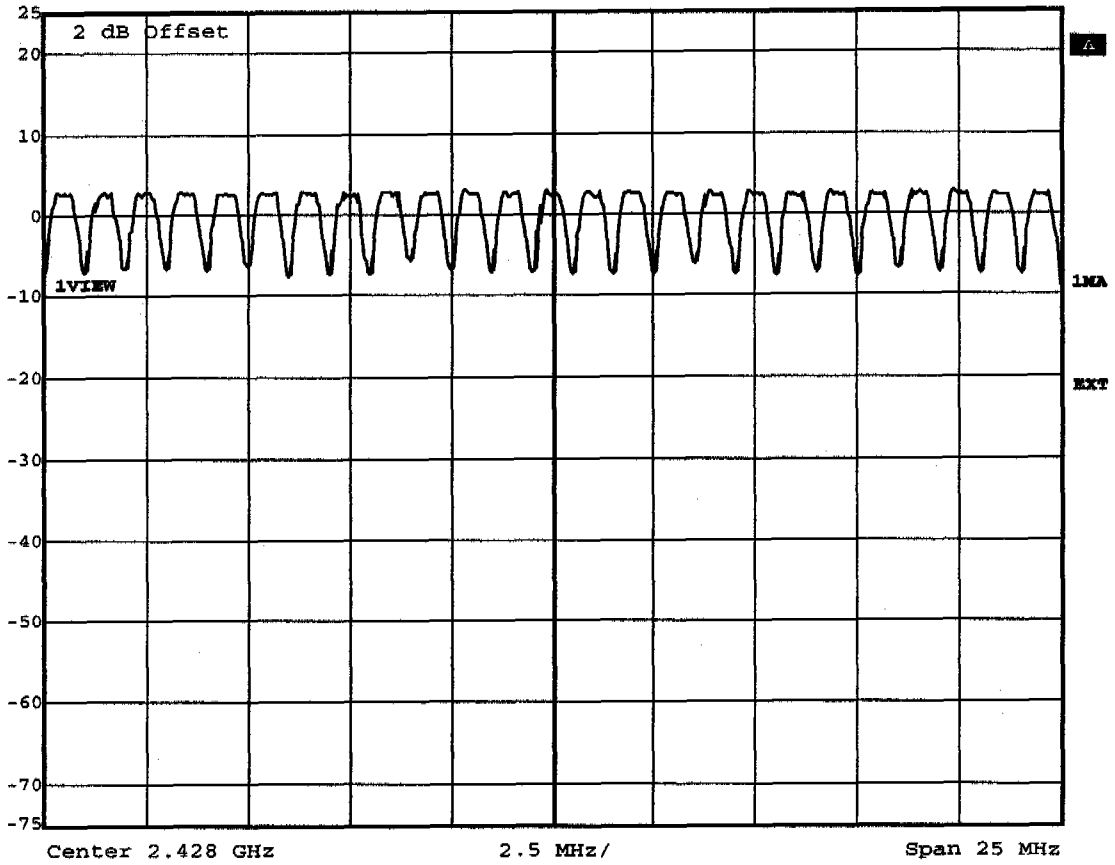


Title: Number of Hopping Frequencies Ch.: 0-13
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 09:15:54



Ref Lvl
25 dBm

RBW 300 kHz RF Att 50 dB
VBW 300 kHz
SWT 5 ms Unit dBm

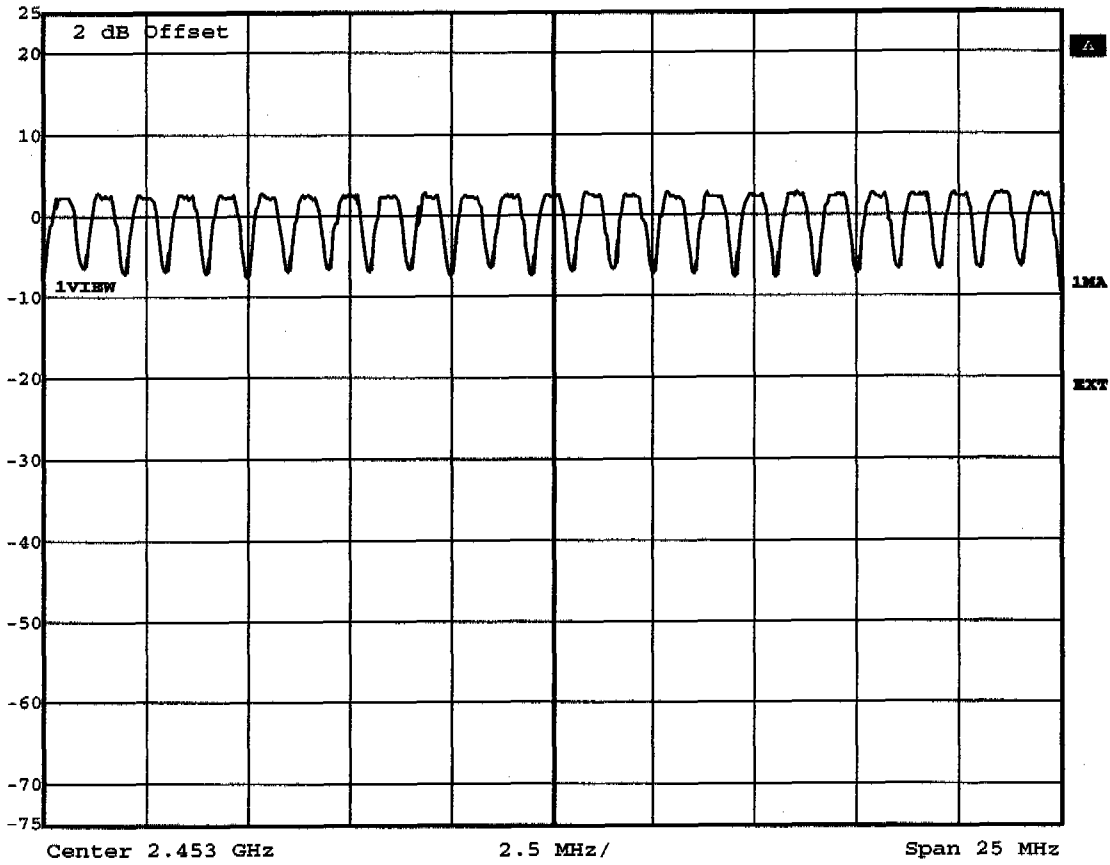


Title: Number of Hopping Frequencies Ch.: 14-38
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 09:17:23



Ref Lvl
25 dBm

RBW 300 kHz RF Att 50 dB
VBW 300 kHz
SWT 5 ms Unit dBm

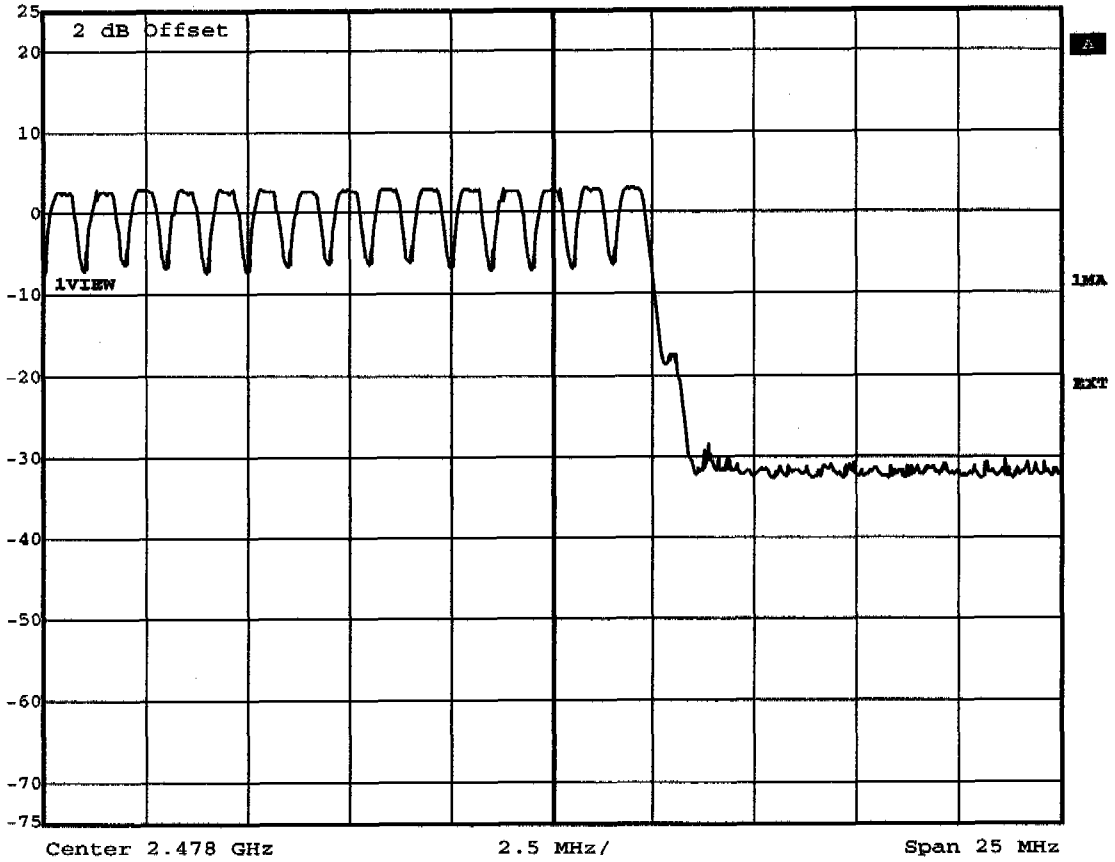


Title: Number of Hopping Frequencies Ch.: 39-63
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 09:18:38



Ref Lvl
25 dBm

RBW 300 kHz RF Att 50 dB
VBW 300 kHz
SWT 5 ms Unit dBm

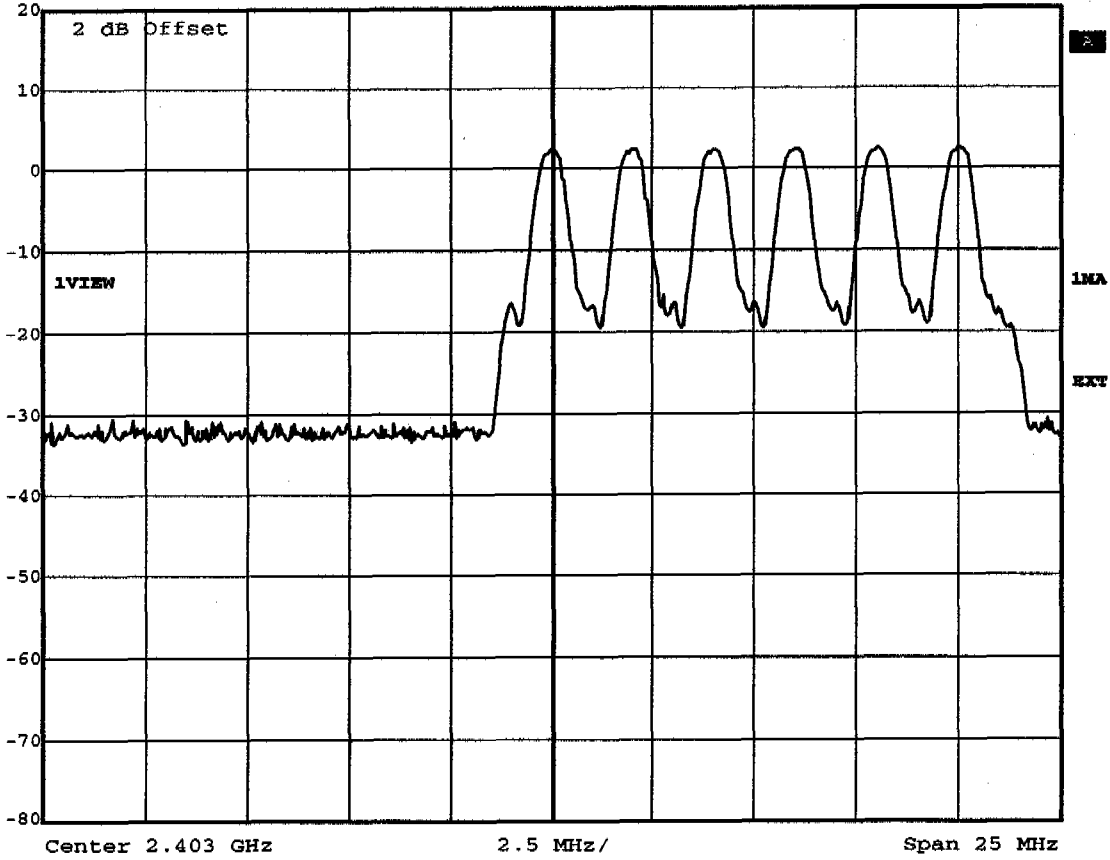


Title: Number of Hopping Frequencies Ch.: 64-78
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 09:20:21



Ref Lvl
20 dBm

RBW 300 kHz RF Att 40 dB
VBW 300 kHz
SWT 5 ms Unit dBm

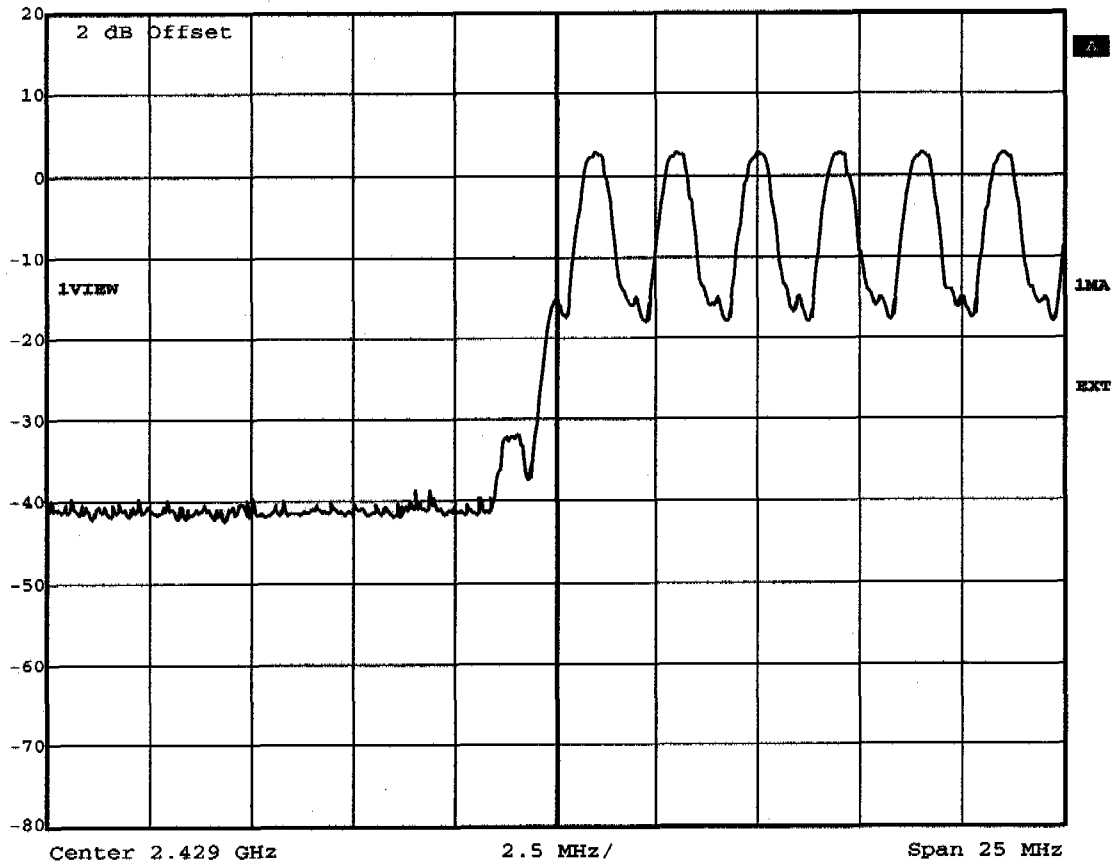


Title: Number of Hopping Frequencies (Master Inquiry Mode)
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 10:37:03



Ref Lvl
20 dBm

RBW 300 kHz RF Att 40 dB
VBW 300 kHz
SWT 5 ms Unit dBm

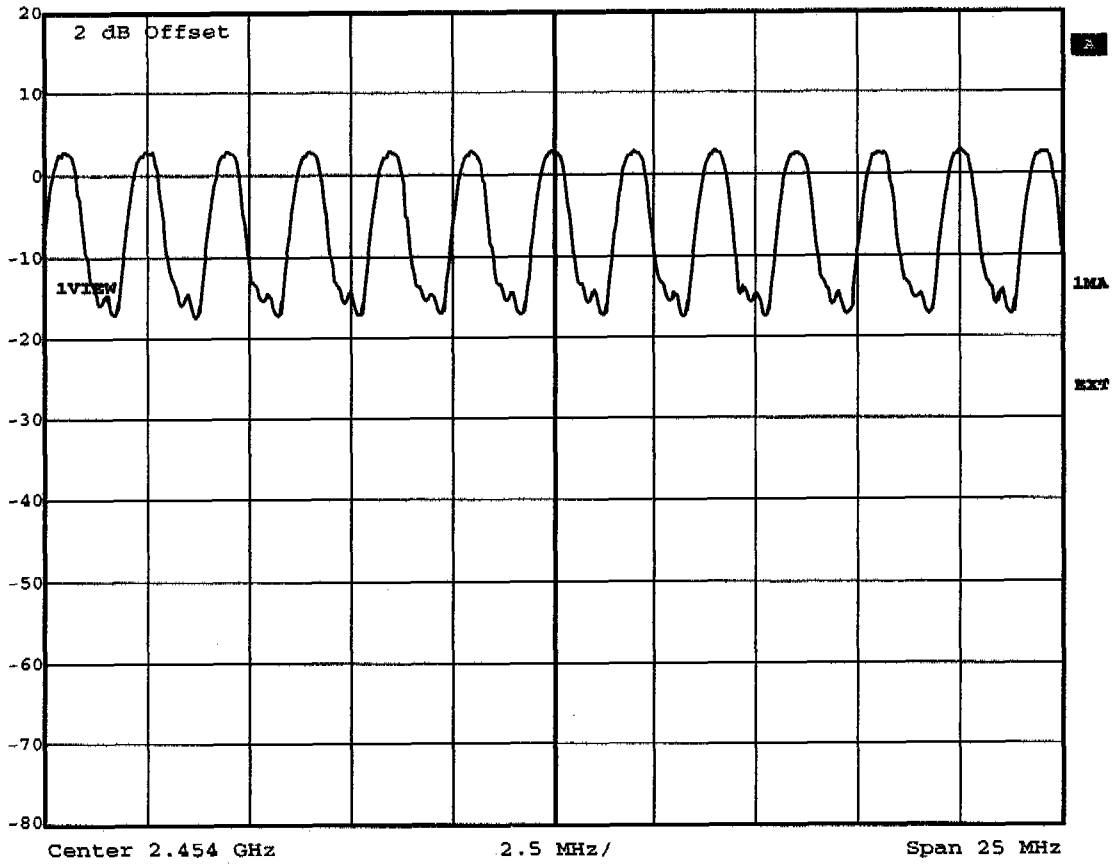


Title: Number of Hopping Frequencies (Master Inquiry Mode)
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 10:45:56



Ref Lvl
20 dBm

REW 300 kHz RF Att 40 dB
VBW 300 kHz
SWT 5 ms Unit dBm



Title: Number of Hopping Frequencies (Master Inquiry Mode)

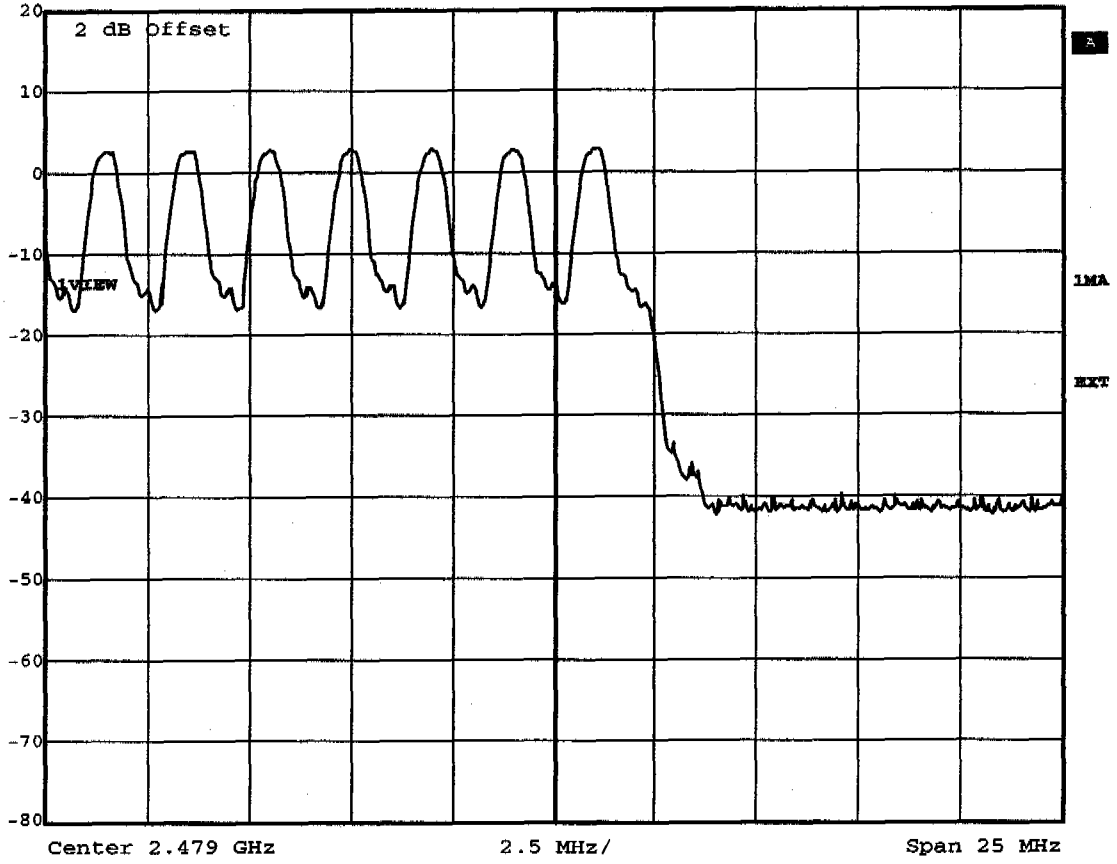
Comment A: Samsung WEP 150 DBE

Date: 23.SEP.2004 10:50:04



Ref Lvl
20 dBm

RBW 300 kHz RF Att 40 dB
VBW 300 kHz
SWT 5 ms Unit dBm



Title: Number of Hopping Frequencies (Master Inquiry Mode)
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 10:54:02

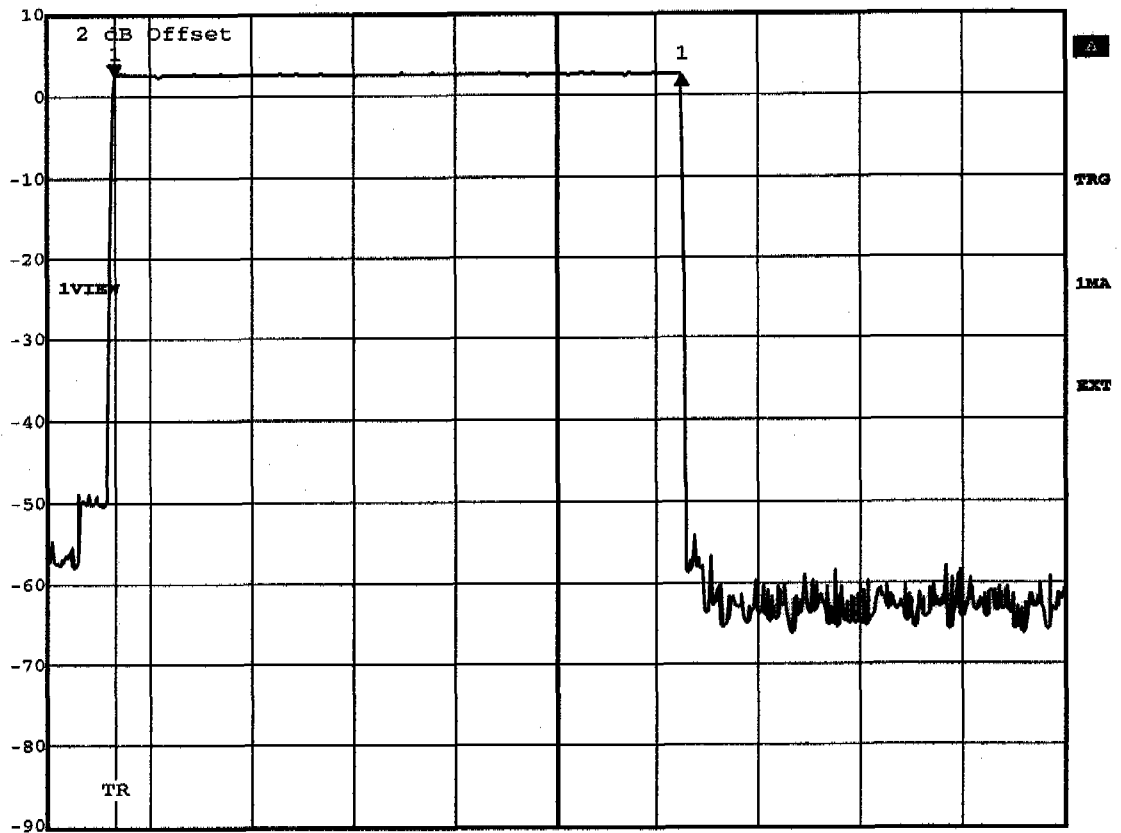


Appendix G

Time of Occupancy (Dwell Time)



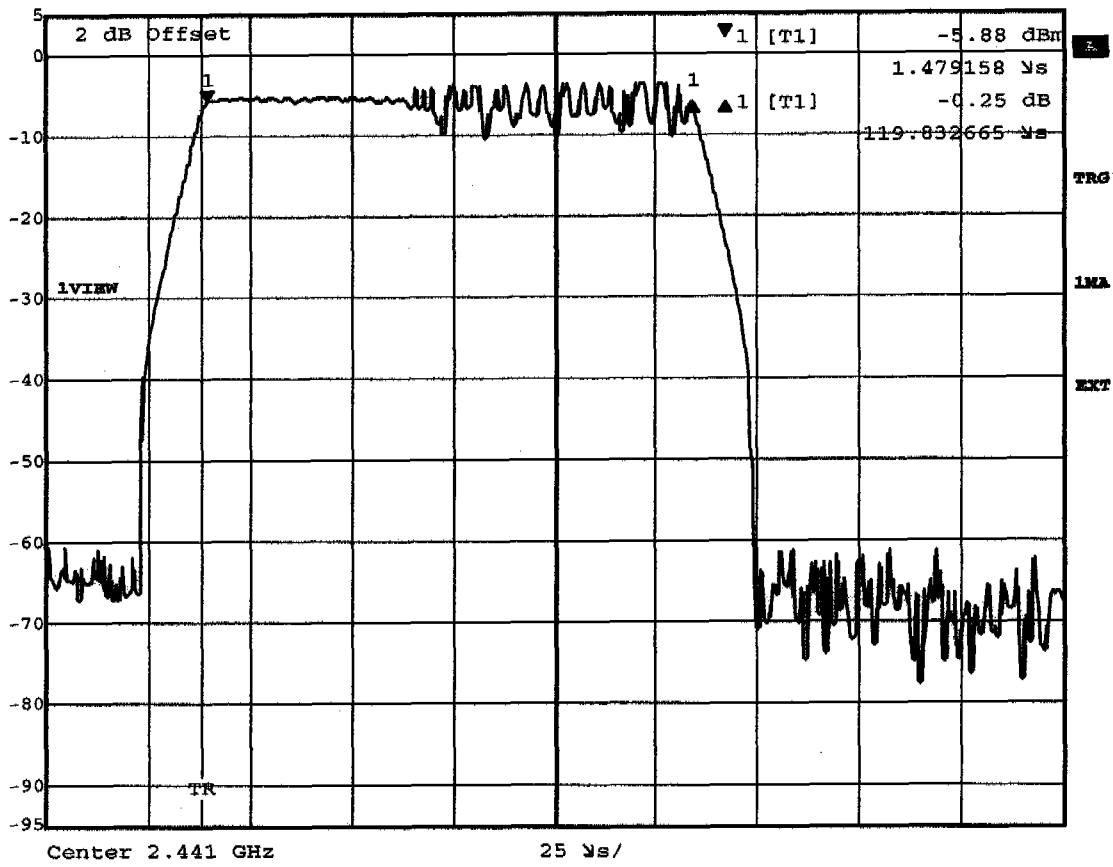
Delta 1 [T1] RBW 1 MHz RF Att 20 dB
Ref Lvl -0.41 dB VBW 1 MHz
10 dBm 1.678461 ms SWT 3 ms Unit dBm



Center 2.441 GHz 300 ns/
Title: Time of occupancy (Hopping DH3) 107 events * 1.68ms=179.76ms
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 10:25:01



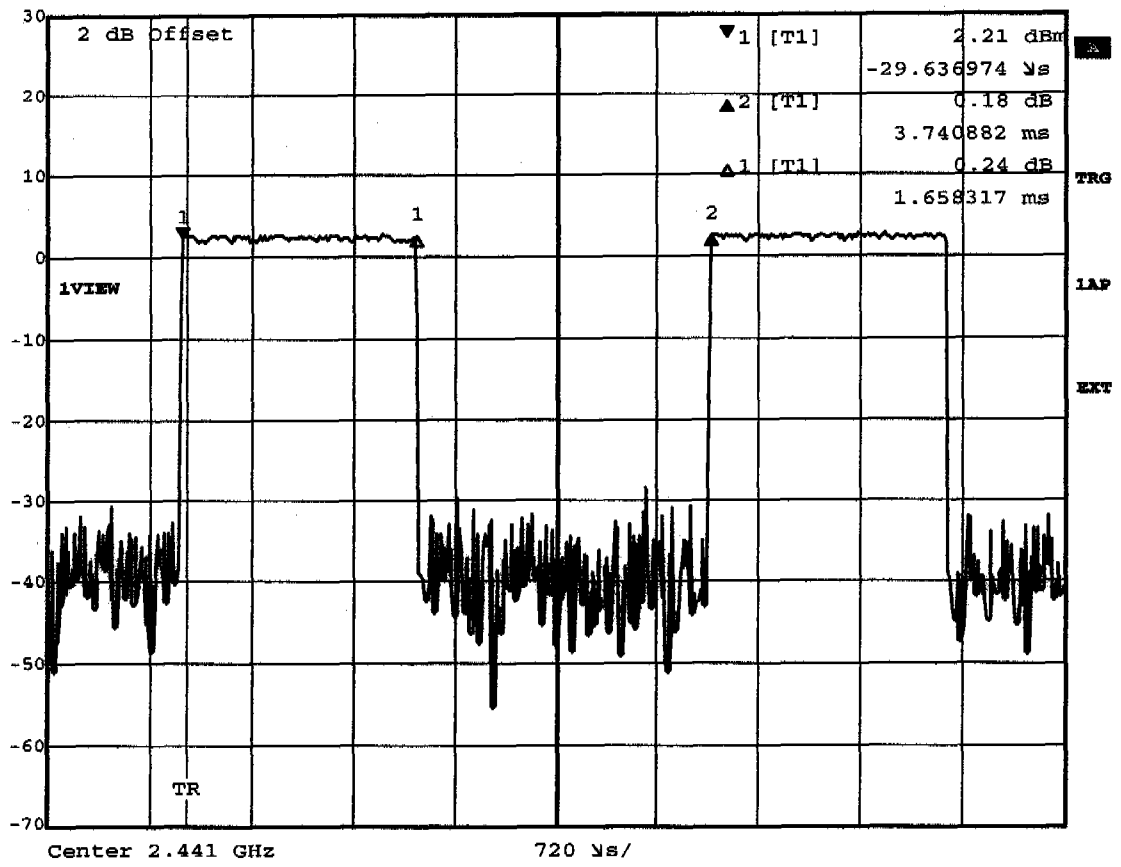
Delta 1 [T1] RBW 1 MHz RF Att 20 dB
 Ref Lvl -0.25 dB VBW 1 MHz
 5 dBm 119.832665 μ s SWT 250 μ s Unit dBm



Title: Time of occupancy (Inquiry mode) 646 events * 0.12ms=77.52ms
 Comment A: Samsung WEP 150 DBE
 Date: 23.SEP.2004 11:13:52



Delta 2 [T1] RBW 1 MHz RF Att 50 dB
Ref Lvl 0.18 dB VBW 1 MHz
30 dBm 3.740882 ms SWT 7.2 ms Unit dBm



Title: Duty Cycle
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 08:48:30

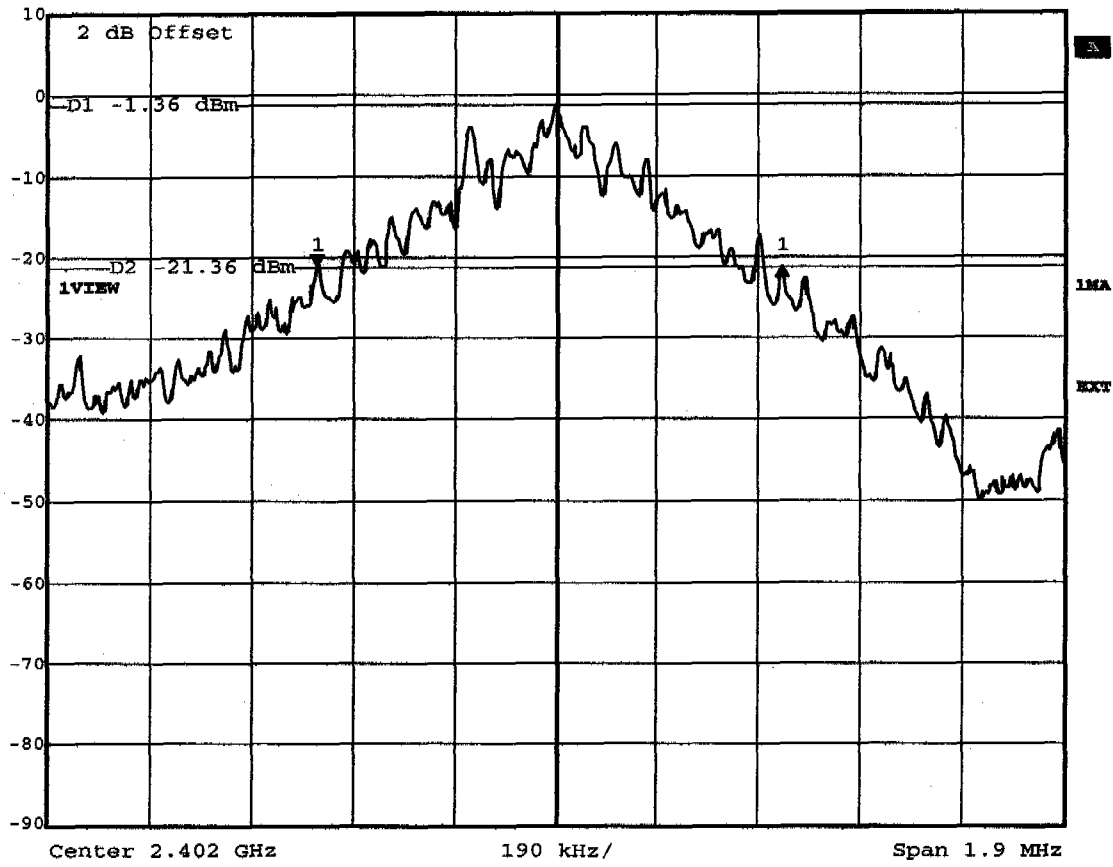


Appendix H

20dB Bandwidth



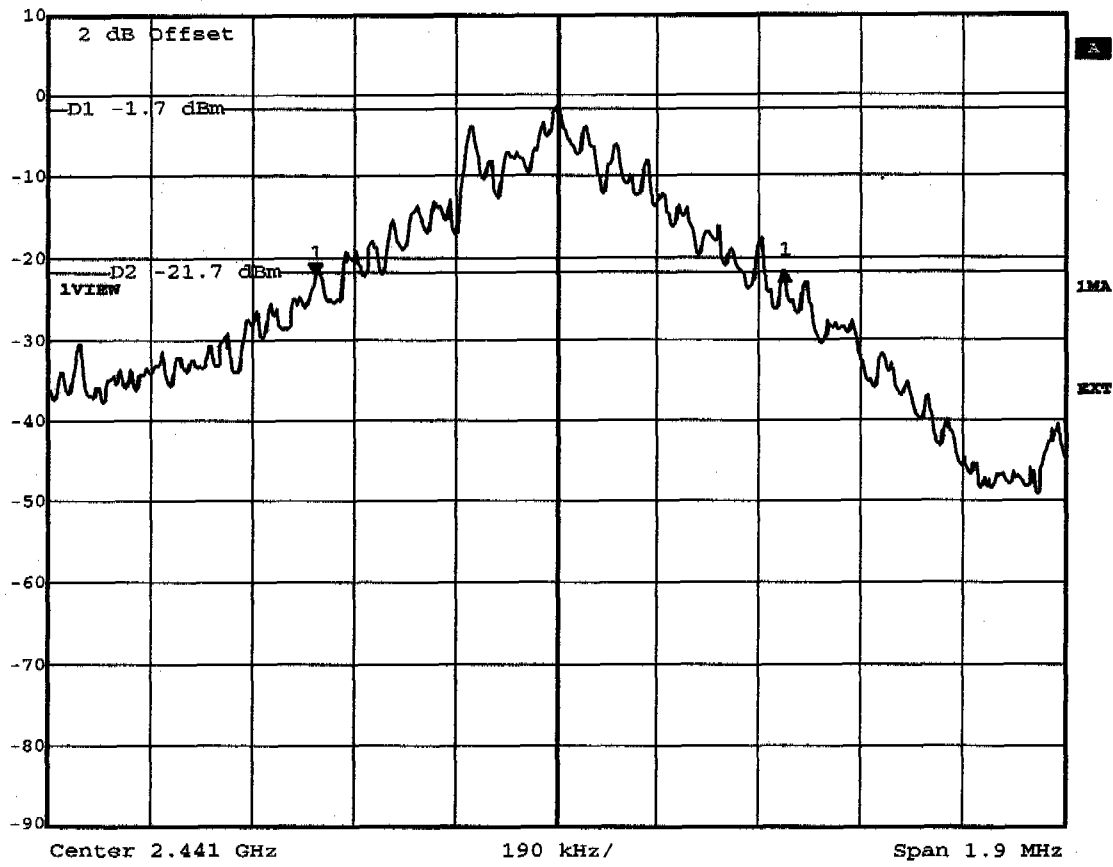
Delta 1 [T1] RBW 10 kHz RF Att 30 dB
Ref Lvl -0.31 dB VBW 10 kHz
10 dBm 871.94388777 kHz SWT 56 ms Unit dBm



Title: -20dB Bandwidth Ch.: 0
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 08:20:34



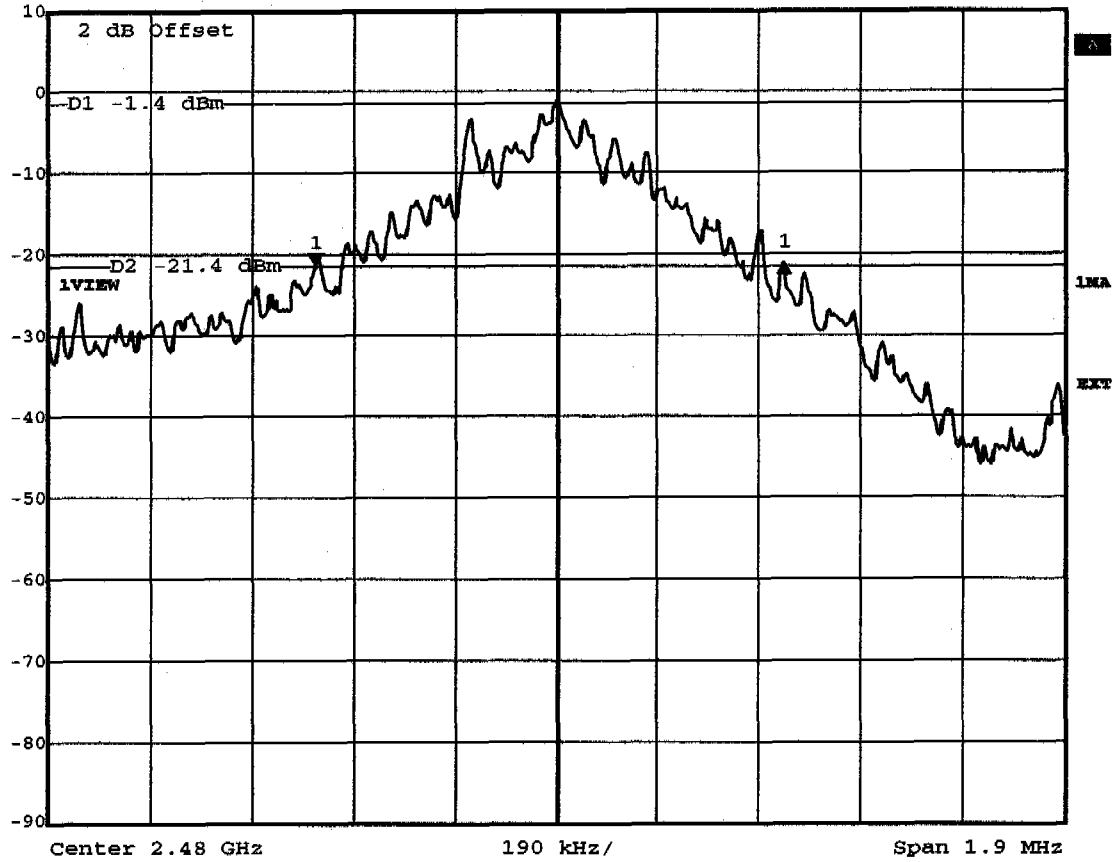
Delta 1 [T1] RBW 10 kHz RF Att 30 dB
Ref Lvl 0.13 dB VBW 10 kHz
10 dBm 879.55911824 kHz SWT 56 ms Unit dBm



Title: -20dB Bandwidth Ch.: 39
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 08:18:57



Delta 1 [T1] RBW 10 kHz RF Att 30 dB
Ref Lvl -0.01 dB VBW 10 kHz
10 dBm 879.55911824 kHz SWT 56 ms Unit dBm



Title: -20dB Bandwidth Ch.: 78
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 08:16:53

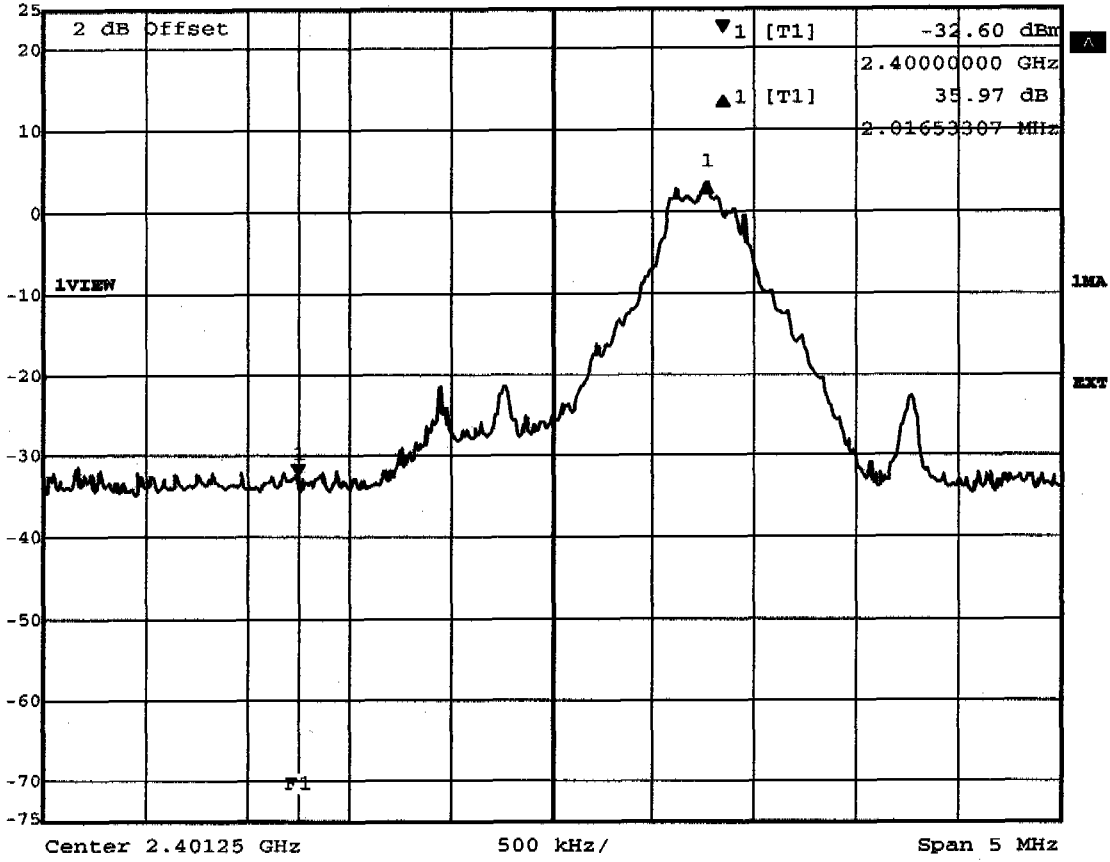


Appendix I

Band-edge Compliance of RF Emissions



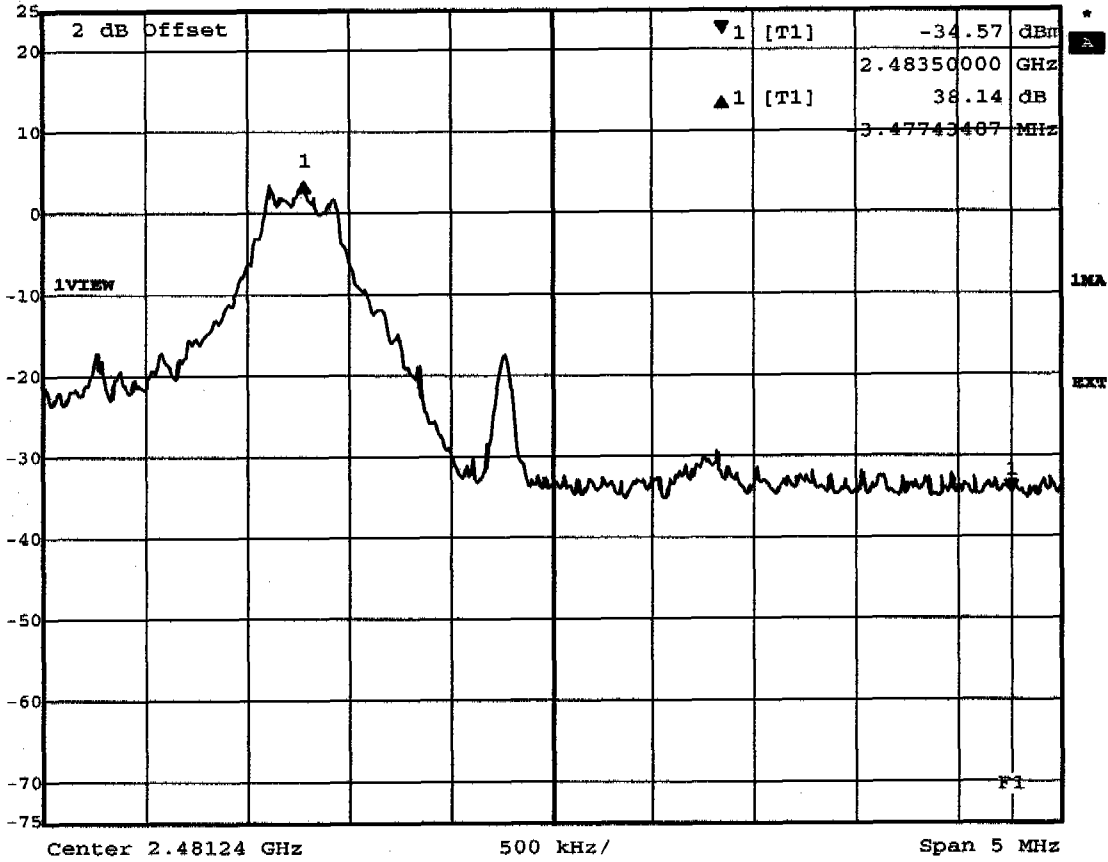
Delta 1 [T1] RBW 50 kHz RF Att 50 dB
Ref Lvl 35.97 dB VBW 50 kHz
25 dBm 2.01653307 MHz SWT 5 ms Unit dBm



Title: Band-edge Compliance (conducted, single frequency)
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 08:43:32



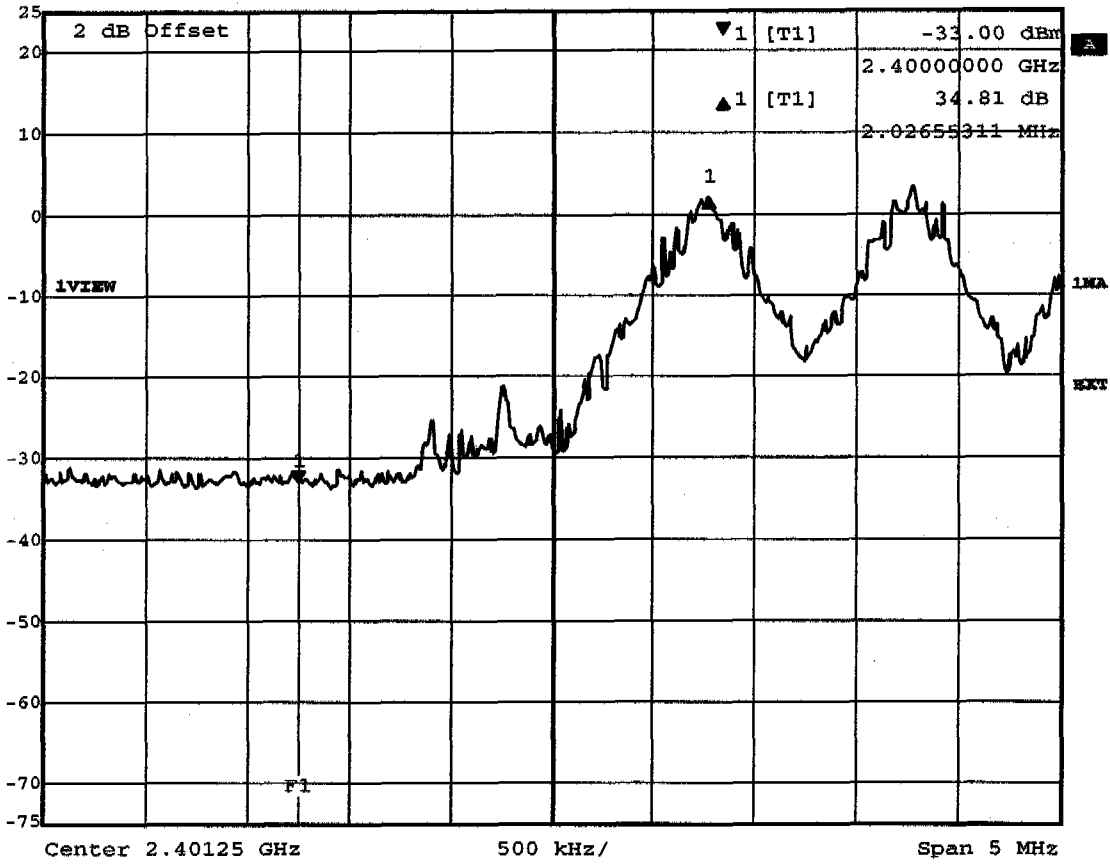
Delta 1 [T1] RBW 50 kHz RF Att 50 dB
Ref Lvl 38.14 dB VBW 50 kHz
25 dBm -3.47743487 MHz SWT 5 ms Unit dBm



Title: Band-edge Compliance (conducted, single frequency)
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 08:40:17



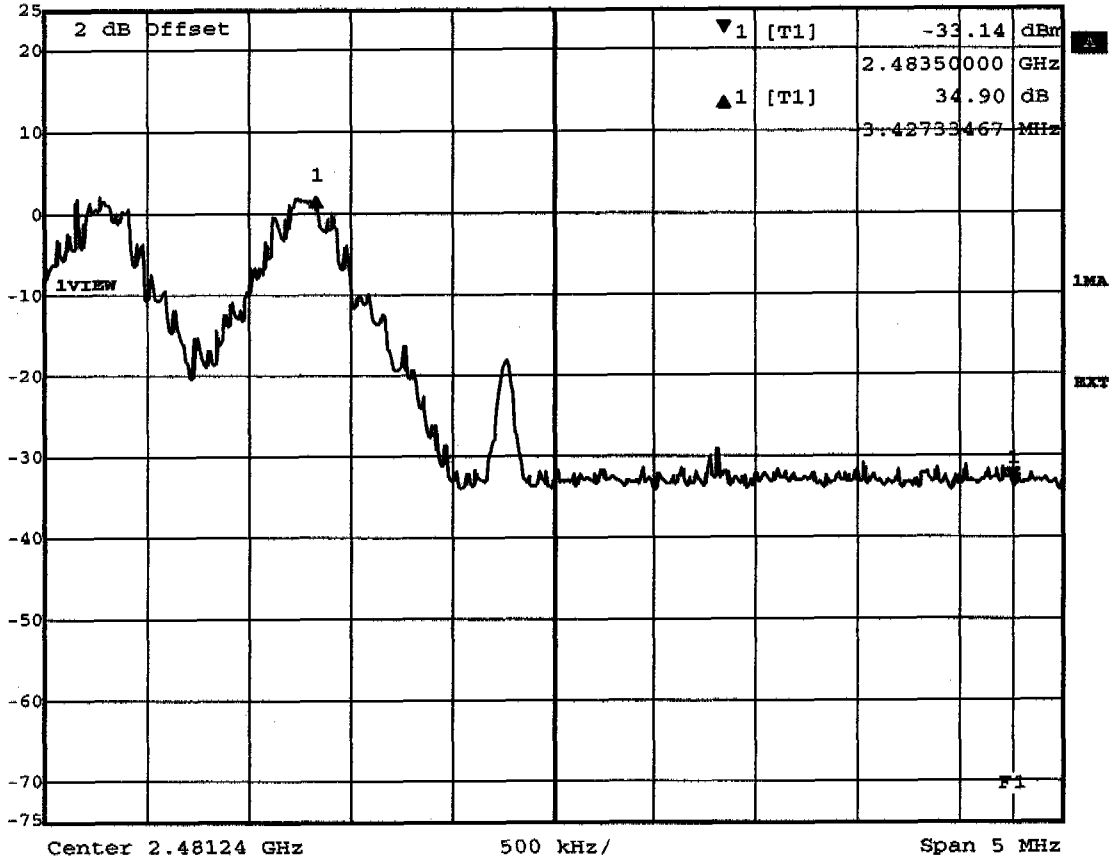
Delta 1 [T1] RBW 50 kHz RF Att 50 dB
Ref Lvl 34.81 dB VBW 50 kHz
25 dBm 2.02655311 MHz SWT 5 ms Unit dBm



Title: Band-edge Compliance (conducted, hopping mode)
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 09:04:29



Delta 1 [T1] RBW 50 kHz RF Att 50 dB
Ref Lvl 34.90 dB VBW 50 kHz
25 dBm -3.42733467 MHz SWT 5 ms Unit dBm



Title: Band-edge Compliance (conducted, hopping mode)
Comment A: Samsung WEP 150 DBE
Date: 23.SEP.2004 09:07:37

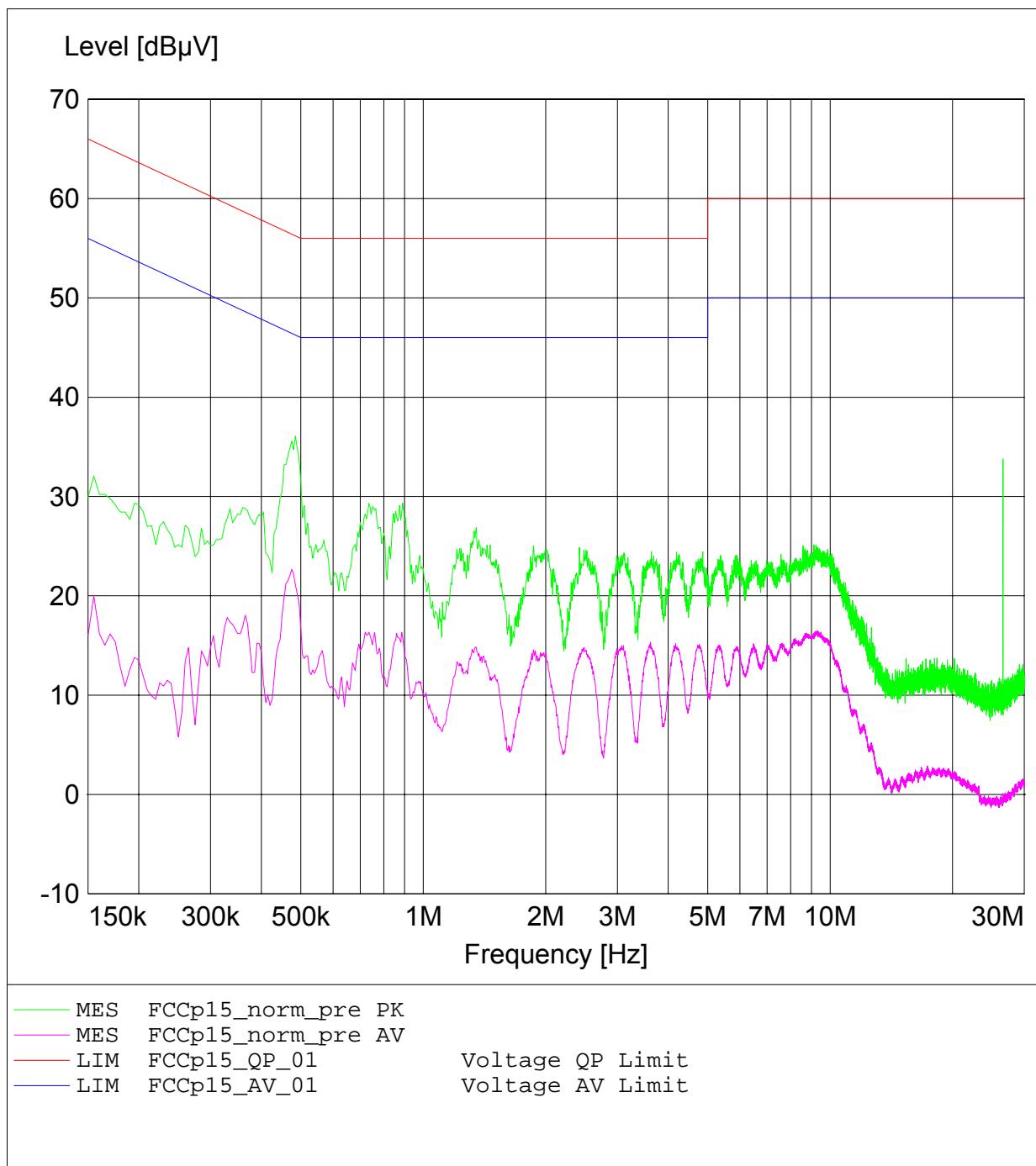


Appendix J

Conducted Measurement at (AC) Power Line

EMI voltage test in the ac-mains according to FCC part 15

EUT: Bluetooth headset
Manufacturer: GN Netcom A/S
Operating Condition: Unom: 120VAC(AC/DC-adaptor) , Tnom: 23°C
Test Site: ETS
Operator: Mr. Pflug
Test Specification: V-Network: ESH2-Z5 (L1)
Comment: model: Samsung WEP 150DBE mode: charging



EMI voltage test in the ac-mains according to FCC part 15

EUT: Bluetooth headset
Manufacturer: GN Netcom A/S
Operating Condition: Unom: 120VAC(AC/DC-adaptor) , Tnom: 23°C
Test Site: ETS
Operator: Mr. Pflug
Test Specification: V-Network: ESH2-Z5 (N)
Comment: model: Samsung WEP 150DBE mode: charging

